RL78/L1C

RENESAS MCU

R01DS0192EJ0100
Rev. 1.00
Nov 18, 2013

Integrated LCD controller/driver, 12-bit resolution A/D Converter, USB 2.0 controller (function), True Low Power Platform (as low as 112.5 μA/MHz, and 0.68 μA for RTC + LVD), 1.6 V to 3.6 V operation, 64 to 256 Kbyte Flash, 33 DMIPS at 24 MHz, for All LCD Based Applications

1. OUTLINE

1.1 Features

Ultra-Low Power Technology
- 1.6 V to 3.6 V operation from a single supply
- Stop (RAM retained): 0.25 μA, (LVD enabled): 0.31 μA
- Halt (RTC + LVD): 0.68 μA
- Supports snooze
- Operating: 112.5 μA/MHz

16-bit RL78 CPU Core
- Delivers 33 DMIPS at maximum operating frequency of 24 MHz
- Instruction Execution: 86% of instructions can be executed in 1 to 2 clock cycles
- CISC Architecture (Harvard) with 3-stage pipeline
- Multiply Signed & Unsigned: 16 × 16 to 32-bit result in 1 clock cycle
- MAC: 16 × 16 to 32-bit result in 2 clock cycles
- 16-bit barrel shifter for shift & rotate in 1 clock cycle
- 1-wire on-chip debug function

Code Flash Memory
- Density: 64 to 256 KB
- Block size: 1 KB
- On-chip single voltage flash memory with protection from block erase/writing
- Self-programming with secure boot swap function and flash shield window function

Data Flash Memory
- Data Flash with background operation
- Data flash size: 8 KB
- Erase Cycles: 1 Million (typ.)
- Erase/programming voltage: 1.8 V to 3.6 V

RAM
- 8 KB to 16 KB size options
- Supports operands or instructions
- Back-up retention in all modes

High-speed On-chip Oscillator
- 24 MHz with +/- 1% accuracy over voltage (1.8 V to 3.6 V) and temperature (-20°C to +85°C)
- Pre-configured settings: 48 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, 1 MHz (TYP.)
- 48 MHz for USB, 48 MHz for timer KB2

Reset and Supply Management
- Power-on reset (POR) monitor/generator
- Low voltage detection (LVD) with 12 setting options (Interrupt and/or reset function)

LCD Controller/Driver
- Up to 56 seg × 4 com or 52 seg × 8 com
- Supports capacitor split method, internal voltage boost method and resistance division method
- Supports waveform types A and B
- Supports LCD contrast adjustment (18 steps)
- Supports LCD blinking

USB
- Complying with USB 2.0
- Corresponding to full-speed transfer (12Mbps) and low-speed (1.5Mbps)
- Complying with Battery Charging Specification Revision 1.2
- Supports USB function controller

Data Transfer Controller (DTC)
- 33 sources & 24 different settings
- Transfer data: 8 bits/16 bits
- Normal mode and repeat mode

Event Link Controller (ELC)
- Reduce interrupt intervention
- Link 31 events to specified peripheral function

Multiple Communication Interfaces
- Up to 4 × I²C master
- Up to 1 × I²C multi-master
- Up to 4 × CSI (7-, 8-bit)
- Up to 4 × UART (7-, 8-, 9-bit)
- Up to 1 × LIN

Extended-Function Timers
- Multi-function 16-bit timer TAU: Up to 8 channels (remote control output available)
- Multi-function 16-bit timer KB2: 3 channels
- High accuracy real-time clock (RTC): 1 channel (full calendar and alarm function with watch correction function)
- 12-bit interval timer: 1 channel
- 15 kHz watchdog timer: 1 channel (window function)

Rich Analog
- ADC: Up to 13 channels, 8/12-bit resolution, 3.375 μs minimum conversion time
- Supports 1.6 V
- D/A converter: 2 channels, 8-bit resolution
- 2 × window comparators, with ELC connection
- Internal voltage reference (1.45 V)
- On-chip temperature sensor

Safety Features (IEC or UL 60730 compliance)
- Flash memory CRC calculation
- RAM parity error check
- RAM write protection
- SFR write protection
- Illegal memory access detection
- Clock stop/ frequency detection
- ADC self-test
- I/O port read back function (echo)

General Purpose I/O
- High-current (up to 20 mA per pin)
- Open-Drain, Internal Pull-up support

Operating Ambient Temperature
- T_A: -40 to +85 °C (A: Consumer applications)
- T_A: -40 to +105 °C (G: Industrial applications)

Package Type and Pin Count
- 80-pin plastic LQFP (12 × 12 mm, 0.5 mm pitch)
- 100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)

○ ROM, RAM capacities

Products with USB

Flash ROM	Data Flash	RAM	RL78/L1C	
			80 pins	100 pins
256 KB	8 KB	16 KB Note	R5F110MJ	R5F110PJ
192 KB	8 KB	16 KB Note	R5F110MH	R5F110PH
128 KB	8 KB	12 KB	R5F110MG	R5F110PG
96 KB	8 KB	10 KB	R5F110MF	R5F110PF
64 KB	8 KB	8 KB	R5F110ME	R5F110PE

Products without USB

Flash ROM	Data Flash	RAM	RL78/L1C	
			80 pins	100 pins
256 KB	8 KB	16 KB Note	R5F111MJ	R5F111PJ
192 KB	8 KB	16 KB Note	R5F111MH	R5F111PH
128 KB	8 KB	12 KB	R5F111MG	R5F111PG
96 KB	8 KB	10 KB	R5F111MF	R5F111PF
64 KB	8 KB	8 KB	R5F111ME	R5F111PE

Note This is about 15 KB when the self-programming function and data flash function are used.

1.2 Ordering Information

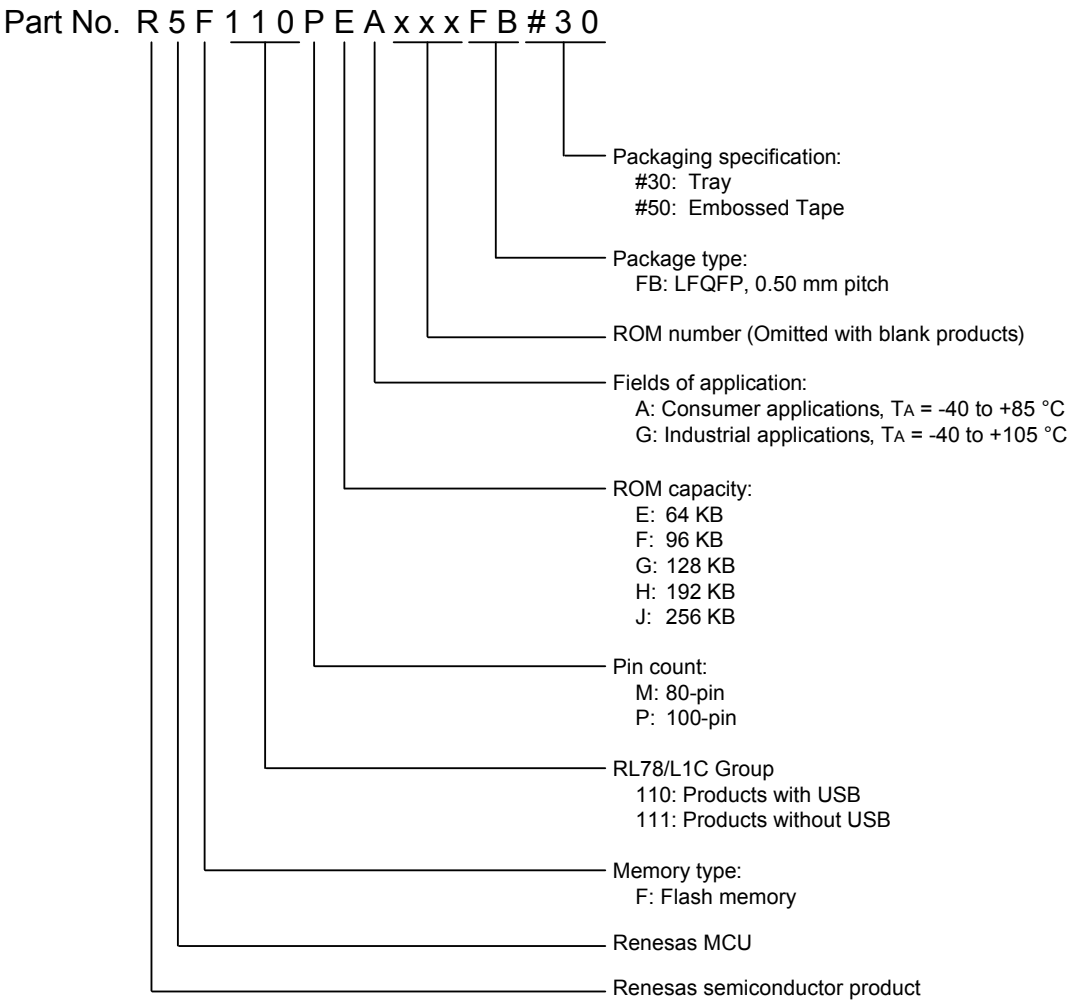
Products with USB

Pin Count	Package	Fields of Application	Orderable Part Number
80 pins	80-pin plastic LQFP (fine pitch) (12 × 12)	A	R5F110MEAFB, R5F110MFAFB, R5F110MGAFB, R5F110MHAFB, R5F110MJAFB
		G	R5F110MEGFB, R5F110MFGFB, R5F110MGGFB, R5F110MHGFB, R5F110MJGFB
100 pins	100-pin plastic LQFP (fine pitch) (14 × 14)	A	R5F110PEAFB, R5F110PFAFB, R5F110PGAFB, R5F110PHAFB, R5F110PJAFB
		G	R5F110PEGFB, R5F110PFGFB, R5F110PGGFB, R5F110PHGFB, R5F110PJGFB

Products without USB

Pin Count	Package	Fields of Application	Orderable Part Number
80 pins	80-pin plastic LQFP (fine pitch) (12 × 12)	A	R5F111MEAFB, R5F111MFAFB, R5F111MGAFB, R5F111MHAFB, R5F111MJAFB
		G	R5F111MEGFB, R5F111MFGFB, R5F111MGGFB, R5F111MHGFB, R5F111MJGFB
100 pins	100-pin plastic LQFP (fine pitch) (14 × 14)	A	R5F111PEAFB, R5F111PFAFB, R5F111PGAFB, R5F111PHAFB, R5F111PJAFB
		G	R5F111PEGFB, R5F111PFGFB, R5F111PGGFB, R5F111PHGFB, R5F111PJGFB

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/L1C

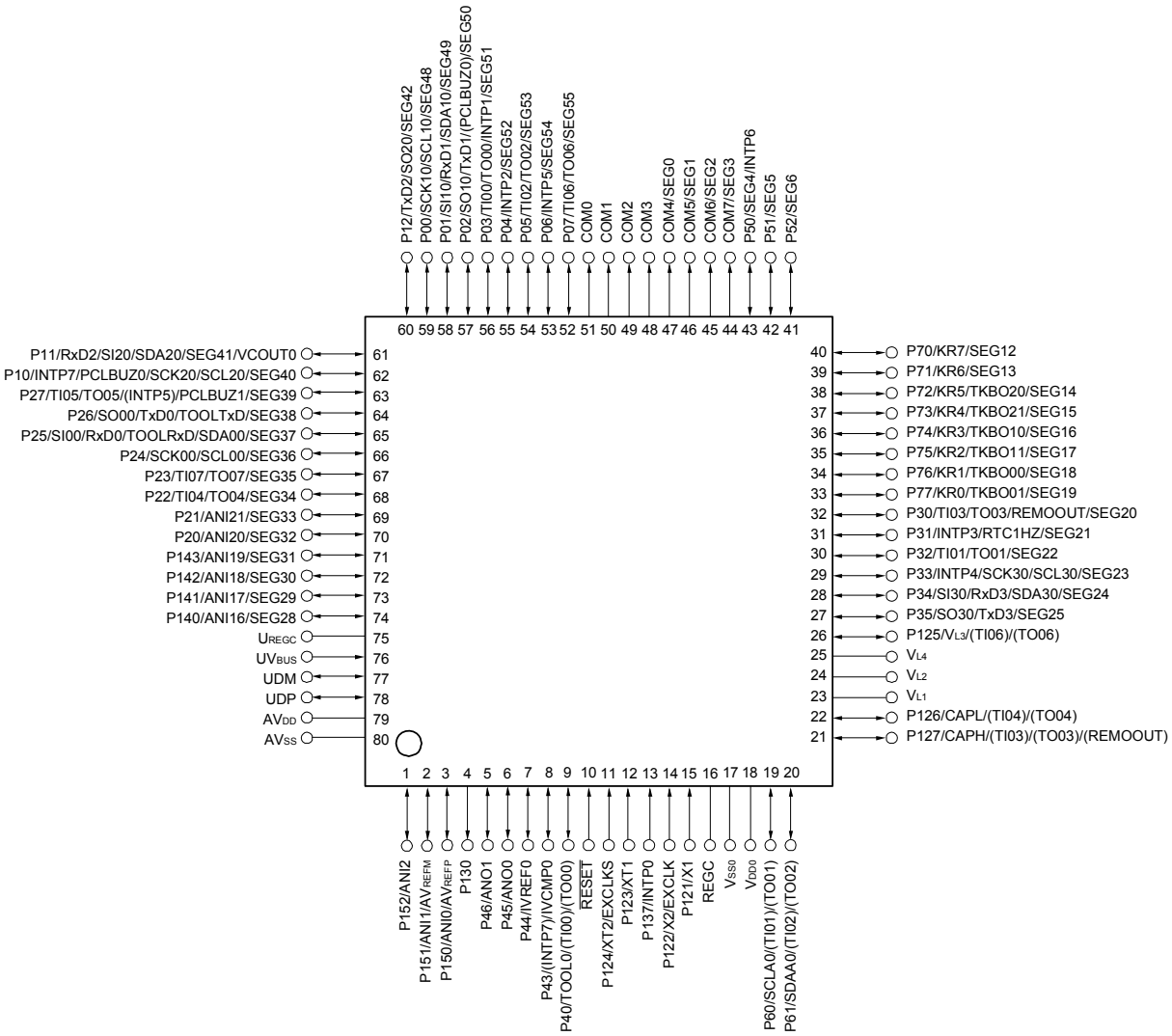


Caution Orderable part numbers are current as of when this manual was published.
Please make sure to refer to the relevant product page on the Renesas website for the latest part numbers.

1.3 Pin Configuration (Top View)

1.3.1 80-pin products (with USB)

• 80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)



Caution 1. Connect the REGC pin to VSS pin via a capacitor (0.47 to 1 μF).

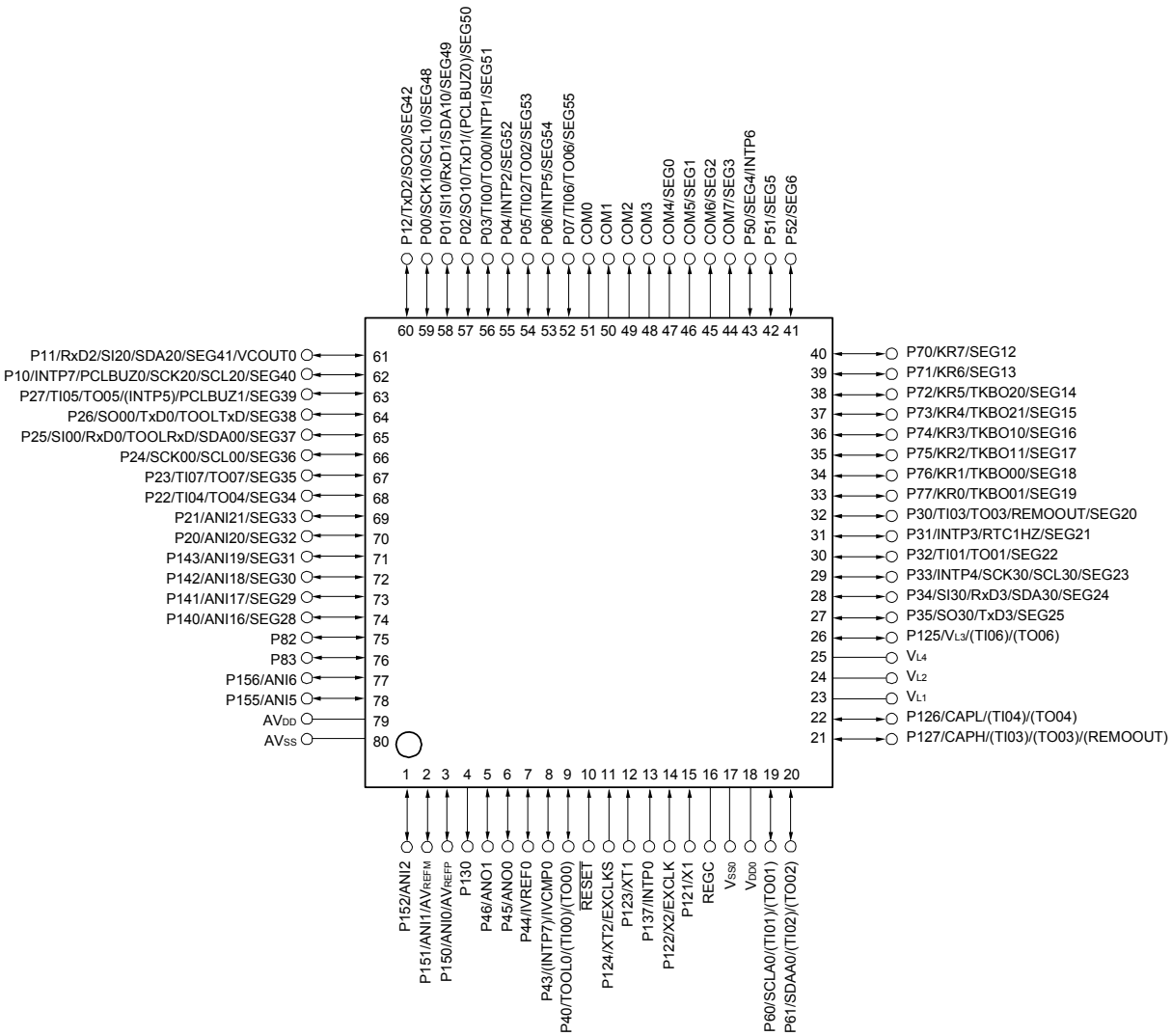
Caution 2. Connect the UREGC pin to VSS pin via a capacitor (0.33 μF).

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.3.2 80-pin products (without USB)

• 80-pin plastic LFQFP (fine pitch) (12 × 12 mm, 0.5 mm pitch)



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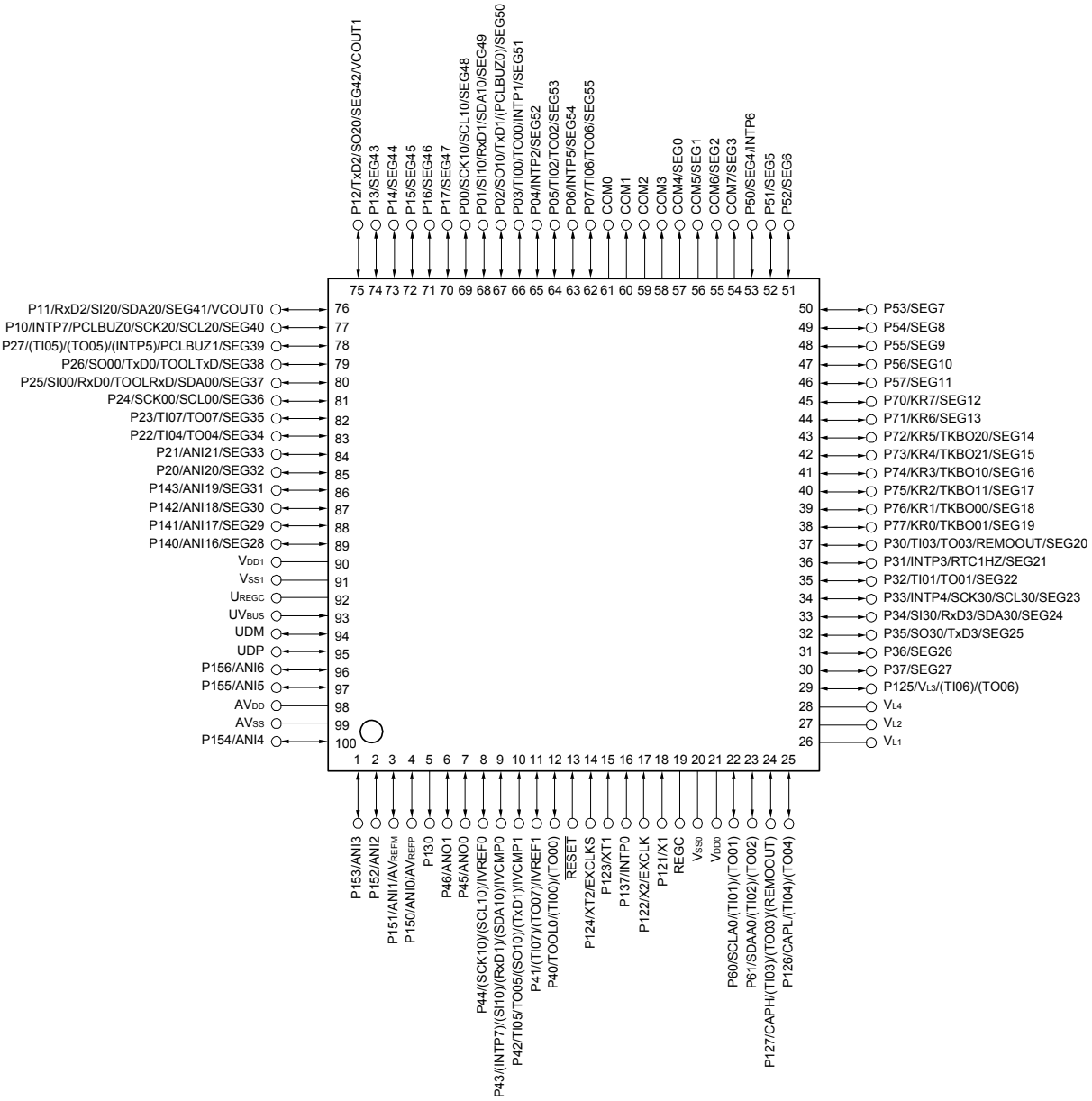
1.3.3 100-pin products (with USB)

• 100-pin plastic LFQFP (fine pitch) (14 × 14 mm, 0.5 mm pitch)



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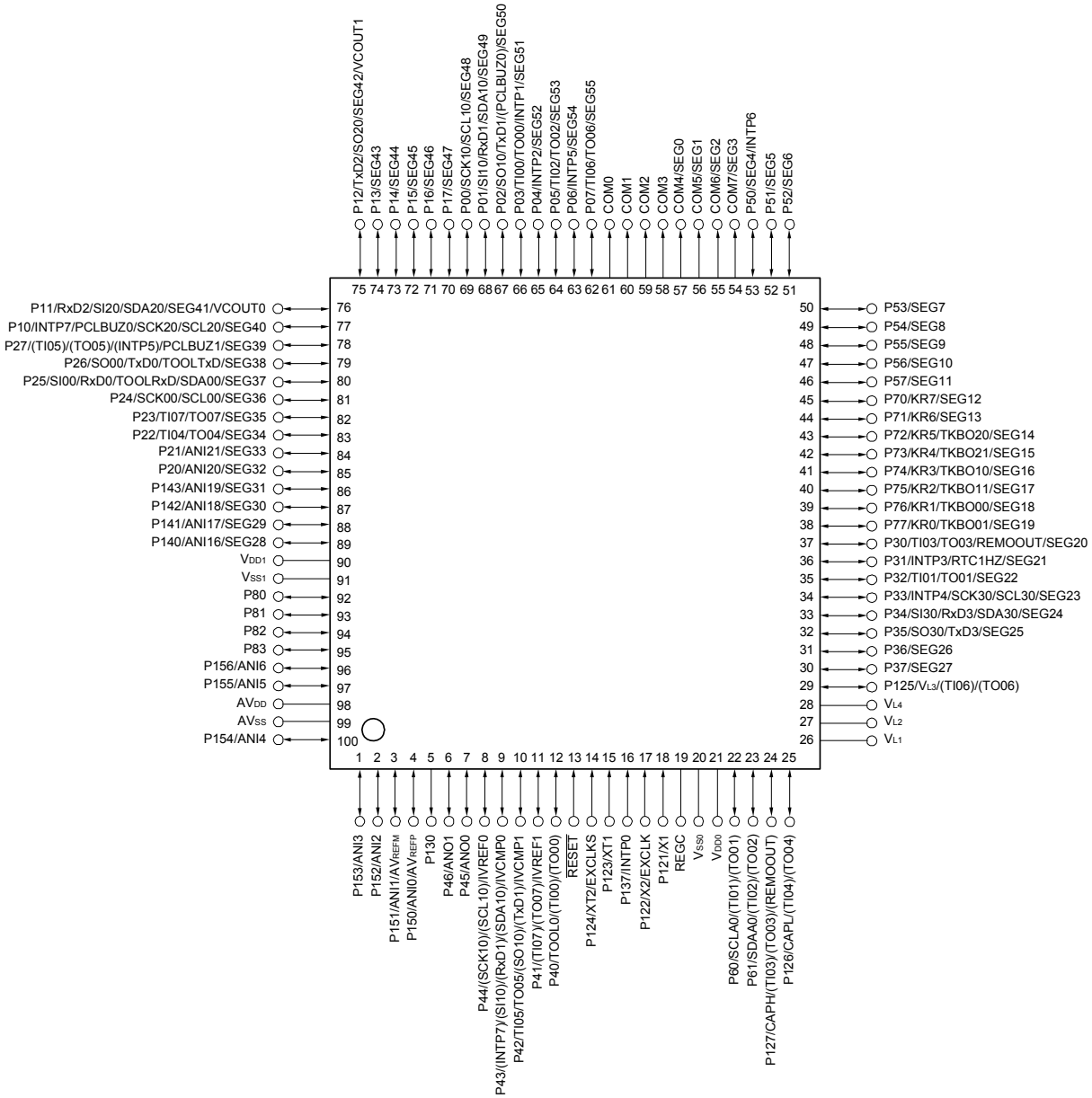
• 100-pin plastic LFQFP (fine pitch) (14 × 14 mm, 0.5 mm pitch)



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Remark 1. For pin identification, see **1.4 Pin Identification**.

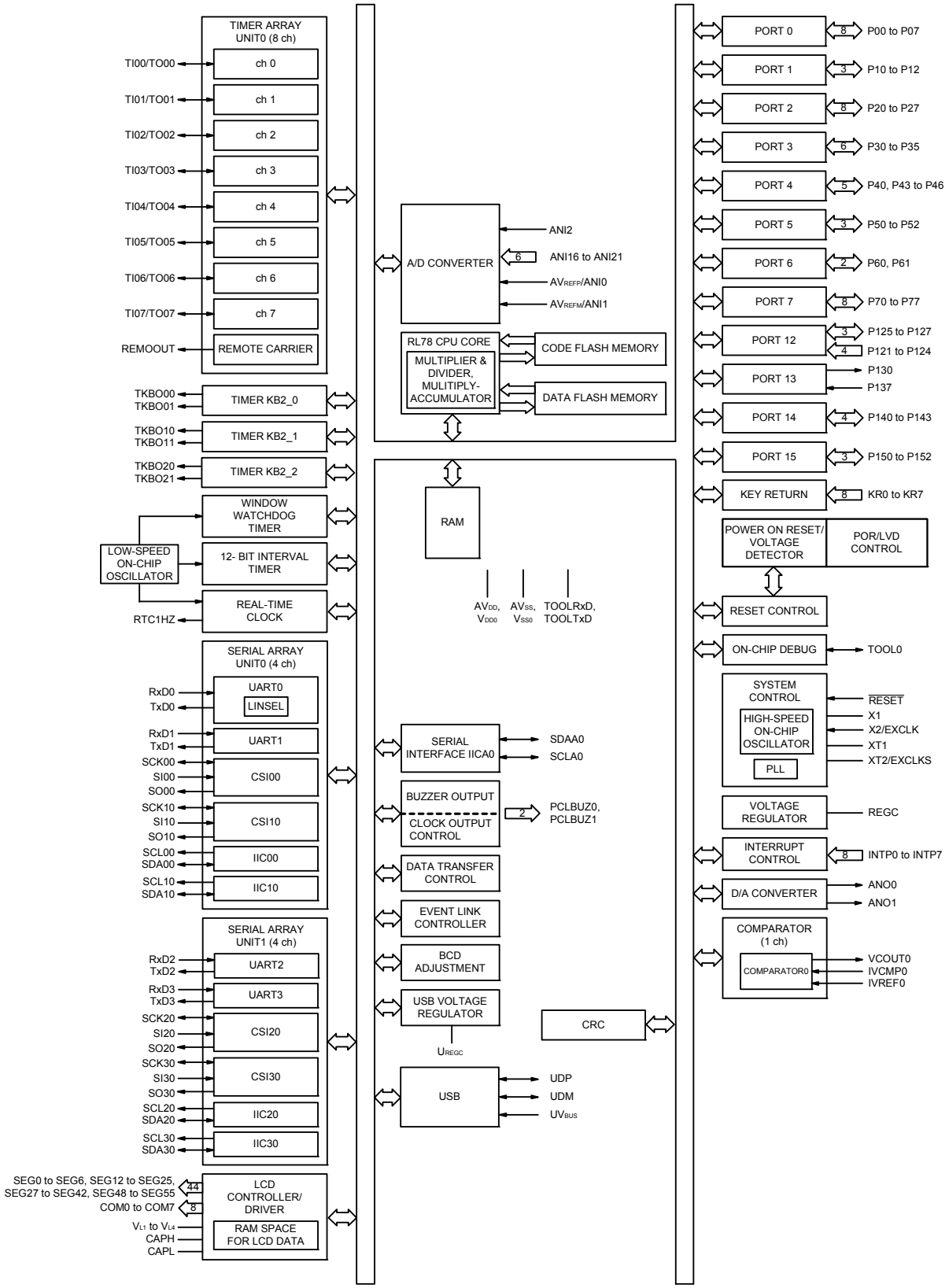
Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR).

1.4 Pin Identification

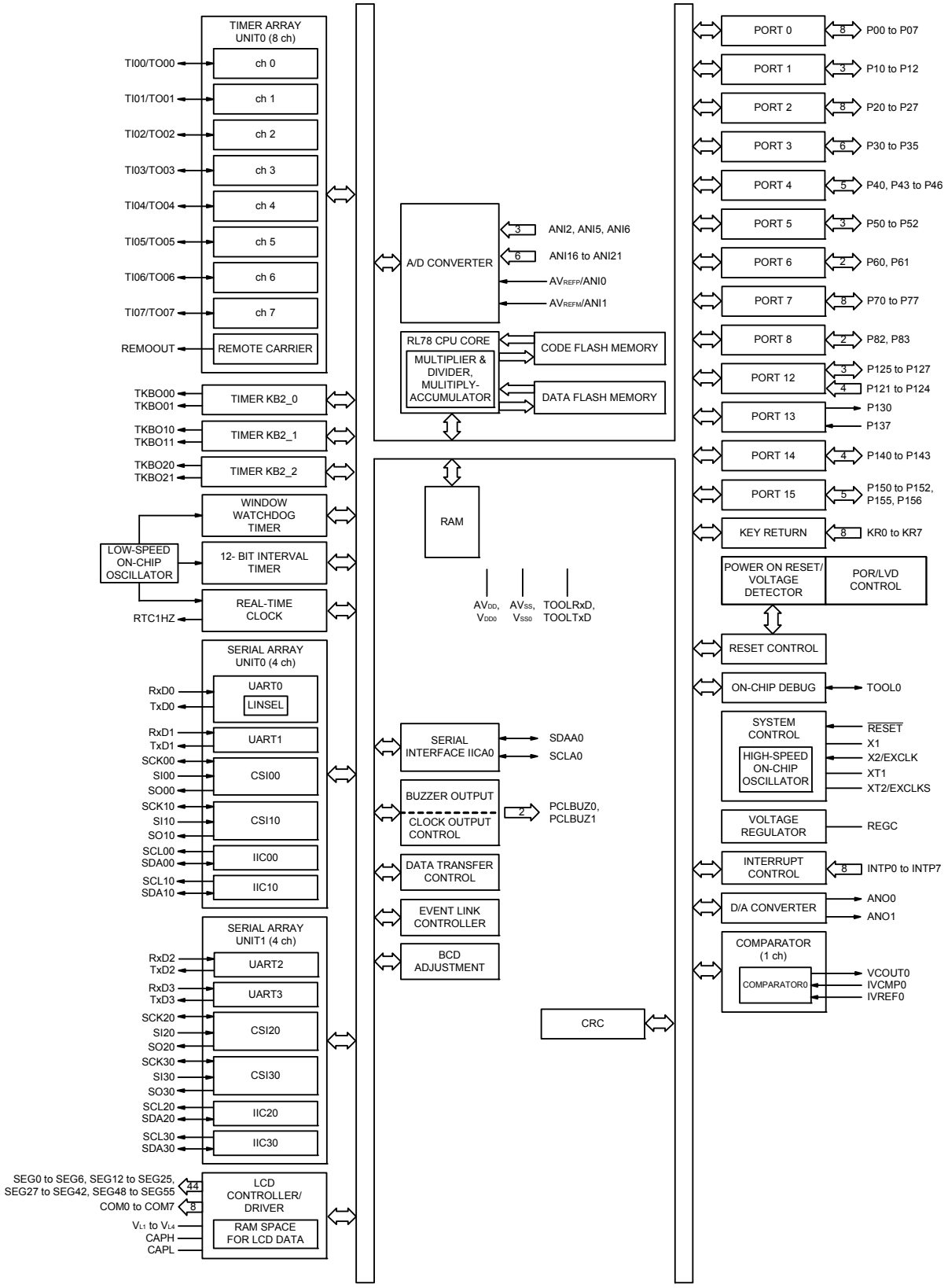
ANI0 to ANI6, ANI16 to ANI21 : Analog Input
ANO0, ANO1 : Analog Output
AV_{DD} : Analog Power Supply
AV_{REFM} : Analog Reference Voltage Minus
AV_{REFP} : Analog Reference Voltage Plus
AV_{SS} : Analog Ground
CAPH, CAPL : Capacitor for LCD
COM0 to COM7 : LCD Common Output
EXCLK : External Clock Input (Main System Clock)
EXCLKS : External Clock Input (Subsystem Clock)
INTP0 to INTP7 : External Interrupt Input
IVCMP0, IVCMP1 : Comparator Input
IVREF0, IVREF1 : Comparator Reference Input
KR0 to KR7 : Key Return
P00 to P07 : Port 0
P10 to P17 : Port 1
P20 to P27 : Port 2
P30 to P37 : Port 3
P40 to P46 : Port 4
P50 to P57 : Port 5
P60 to P62 : Port 6
P70 to P77 : Port 7
P80 to P83 : Port 8
P121 to P127 : Port 12
P130, P137 : Port 13
P140 to P143 : Port 14
P150 to P156 : Port 15
PCLBUZ0, PCLBUZ1 : Programmable Clock Output/ Buzzer Output
REGC : Regulator Capacitance
REMOOUT : Remote Control Output
$\overline{\text{RESET}}$: Reset
RTC1HZ : Real-time Clock Correction Clock (1 Hz) Output
RxD0 to RxD3 : Receive Data
SCK00, SCK10, SCK20, SCK30 : Serial Clock Input/Output
SCLA0 : Serial Clock Input/Output
SCL00, SCL10, SCL20, SCL30 : Serial Clock Output
SDAA0, SDA00, SDA10, SDA20, SDA30 : Serial Data Input/Output
SEG0 to SEG55 : LCD Segment Output
SI00, SI10, SI20, SI30 : Serial Data Input
SO00, SO10, SO20, SO30 : Serial Data Output
TI00 to TI07 : Timer Input
TO00 to TO07 : Timer Output
TKBO00, TKBO01, TKBO10, TKBO11, TKBO20, TKBO21
TOOL0 : Data Input/Output for Tool
TOOLRxD, TOOLTxD : Data Input/Output for External Device
UDM, UDP : USB Input/Output
U_{REGC} : USB Regulator Capacitance
UV_{BUS} : USB Input/USB Power Supply
TxD0 to TxD3 : Transmit Data
VCOUT0, VCOUT1 : Comparator Output
V_{DD0}, V_{DD1} : Power Supply
V_{L1} to V_{L4} : LCD Power Supply
V_{SS0}, V_{SS1} : Ground
X1, X2 : Crystal Oscillator (Main System Clock)
XT1, XT2 : Crystal Oscillator (Subsystem Clock)

1.5 Block Diagram

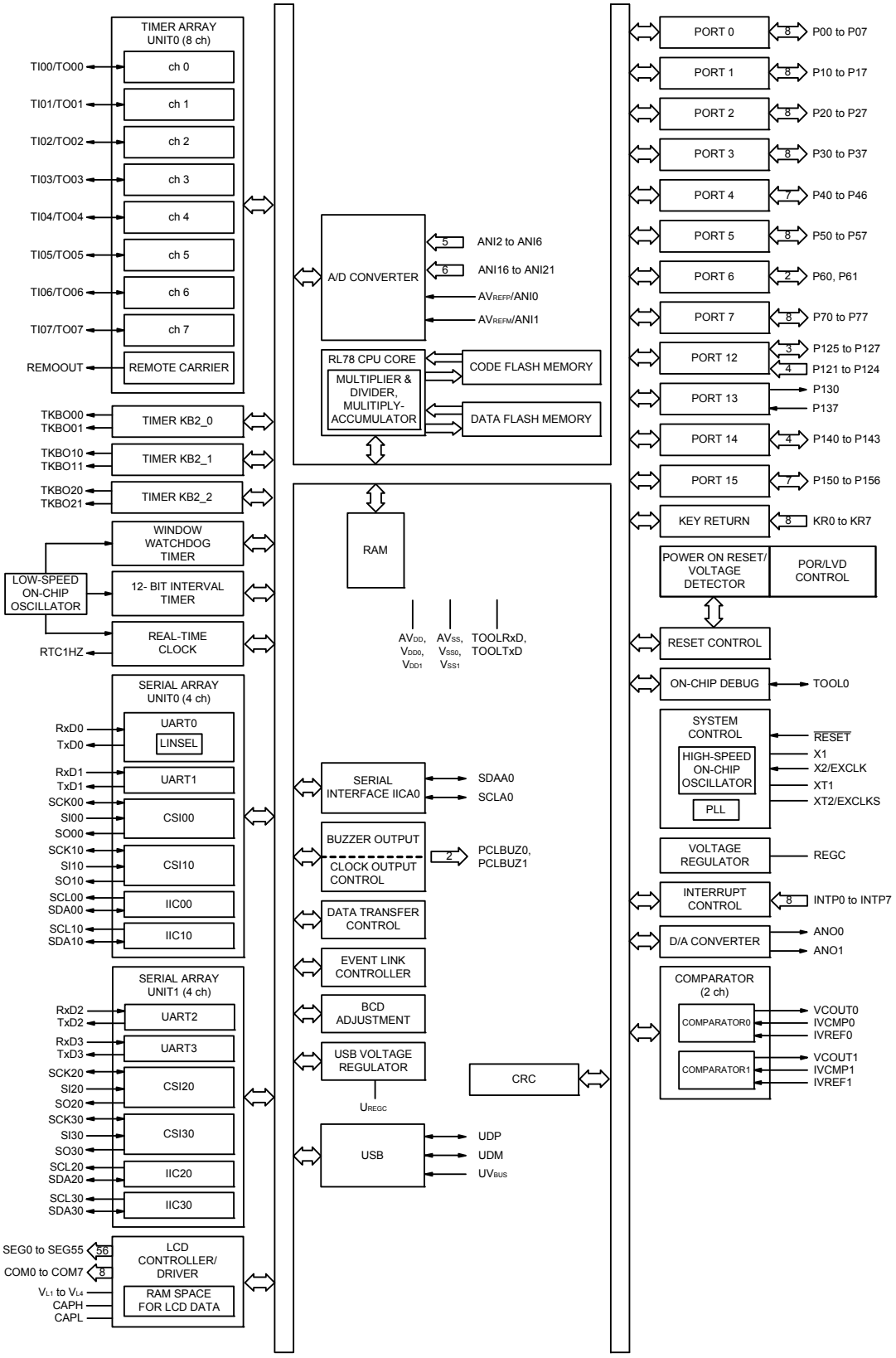
1.5.1 80-pin products (with USB)



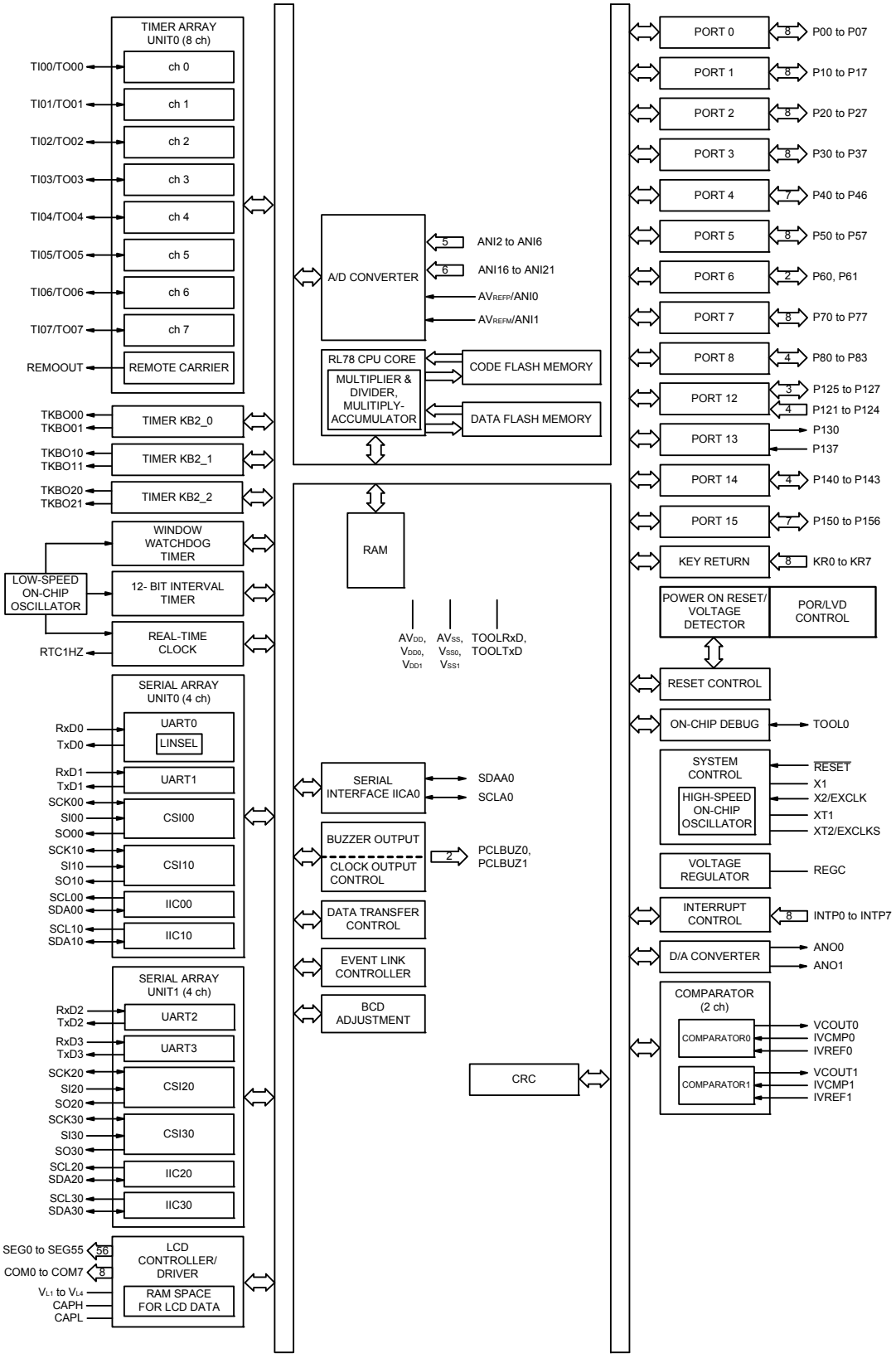
1.5.2 80-pin products (without USB)



1.5.3 100-pin products (with USB)



1.5.4 100-pin products (without USB)



1.6 Outline of Functions

[80-pin, 100-pin products (with USB)] **(1/2)**

Item		80-pin	100-pin
		R5F110Mx (x = E to H, J)	R5F110Px (x = E to H, J)
Code flash memory (KB)		64 to 256	64 to 256
Data flash memory (KB)		8	8
RAM (KB)		8 to 16 Note 1	8 to 16 Note 1
Memory space		1 MB	
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) 1 to 20 MHz: V_{DD} = 2.7 to 3.6 V, 1 to 8 MHz: V_{DD} = 1.8 to 2.7 V, 1 to 4 MHz: V_{DD} = 1.6 to 1.8 V	
	High-speed on-chip oscillator clock	HS (high-speed main) operation mode: 1 to 24 MHz (V_{DD} = 2.7 to 3.6 V), HS (high-speed main) operation mode: 1 to 16 MHz (V_{DD} = 2.4 to 3.6 V), LS (low-speed main) operation mode: 1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), LV (low-voltage main) operation mode: 1 to 4 MHz (V_{DD} = 1.6 to 3.6 V)	
	PLL clock	6, 12, 24 MHz Note 2: V_{DD} = 2.4 to 3.6 V	
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz (TYP.): V_{DD} = 1.6 to 3.6 V	
Low-speed on-chip oscillator clock		15 kHz (TYP.): V_{DD} = 1.6 to 3.6 V	
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)	
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator clock: f_{HOCO} = f_{IH} = 24 MHz operation)	
		0.04167 μs (PLL clock: f_{PLL} = 48 MHz/f_{IH} = 24 MHz Note 2 operation)	
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)	
		30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.	
I/O port	Total	59	77
	CMOS I/O	51	69
	CMOS input	5	5
	CMOS output	1	1
	N-ch open-drain I/O (6 V tolerance)	2	2
Timer	16-bit timer TAU	8 channels (with 1 channel remote control output function) (Timer outputs: 8, PWM outputs: 7 Note 3)	
	16-bit timer KB2	3 channels (PWM outputs: 6)	
	Watchdog timer	1 channel	
	12-bit interval timer	1 channel	
	High accuracy real-time clock	1 channel	
	RTC output	1 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)	

Note 1. In the case of the 16 KB, this is about 15 KB when the self-programming function and data flash function are used.

Note 2. In the PLL clock 48 MHz operation, the system clock is 2/4/8 dividing ratio.

Note 3. The number of outputs varies, depending on the setting of channels in use and the number of the master.

(2/2)

Item			80-pin	100-pin
			R5F110Mx (x = E to H, J)	R5F110Px (x = E to H, J)
Clock output/buzzer output			2	2
			• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
8/12-bit resolution A/D converter			9 channels	13 channels
D/A converter			2 channels	2 channels
Comparator			1 channel	2 channels
Serial interface			• CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel	
	I^2C bus		1 channel	1 channel
USB	Function		1 channel	
LCD controller/driver			Internal voltage boosting method, capacitor split method, and external resistance division method are switchable.	
	Segment signal output		44 (40) Note 1	56 (52) Note 1
	Common signal output		4 (8) Note 1	
Data transfer controller (DTC)			32 sources	33 sources
Event link controller (ELC)			Event input: 30, Event trigger output: 22	Event input: 31, Event trigger output: 22
Vectored interrupt sources	Internal		36	37
	External		9	9
Key interrupt			8	8
Reset			• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note 2 • Internal reset by RAM parity error • Internal reset by illegal-memory access	
Power-on-reset circuit			• Power-on-reset: 1.51 ± 0.03 V • Power-down-reset: 1.50 ± 0.03 V	
Voltage detector			• Rising edge: 1.67 V to 3.13 V (12 stages) • Falling edge: 1.63 V to 3.06 V (12 stages)	
On-chip debug function			Provided	
Power supply voltage			V_{DD} = 1.6 to 3.6 V	
Operating ambient temperature			T_A = -40 to +85 °C (A: Consumer applications), T_A = -40 to +105 °C (G: Industrial applications)	

Note 1. The number in parentheses indicates the number of signal outputs when 8 coms are used.

Note 2. The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

[80-pin, 100-pin products (without USB)] **(1/2)**

Item		80-pin	100-pin
		R5F111Mx (x = E to H, J)	R5F111Px (x = E to H, J)
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	High-speed on-chip oscillator clock	HS (high-speed main) operation mode: 1 to 24 MHz (V_{DD} = 2.7 to 3.6 V), HS (high-speed main) operation mode: 1 to 16 MHz (V_{DD} = 2.4 to 3.6 V, LS (low-speed main) operation mode: 1 to 8 MHz (V_{DD} = 1.8 to 3.6 V), LV (low-voltage main) operation mode: 1 to 4 MHz (V_{DD} = 1.6 to 3.6 V)	
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz (TYP.): V_{DD} = 1.6 to 3.6 V	
Low-speed on-chip oscillator clock		15 kHz (TYP.): V_{DD} = 1.6 to 3.6 V	
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)	
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator clock: f_{HOCO} = f_{IH} = 24 MHz operation)	
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I/O port	Total	63	81
	CMOS I/O	55	73
	CMOS input	5	5
	CMOS output	1	1
	N-ch open-drain I/O (6 V tolerance)	2	2
Timer	16-bit timer TAU	8 channels (with 1 channel remote control output function) (Timer outputs: 8, PWM outputs: 7 Note 2)	
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8/12-bit resolution A/D converter			11 channels	13 channels
D/A converter			2 channels	2 channels
Comparator			1 channel	2 channels
Serial interface			• CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel	
	I^2C bus		1 channel	1 channel
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	Segment signal output		44 (40) Note 1	56 (52) Note 1
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Vectored interrupt sources		Internal	32	33
		External	9	9
Key interrupt			8	8
Reset			• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note 2 • Internal reset by RAM parity error • Internal reset by illegal-memory access	
Power-on-reset circuit			• Power-on-reset: 1.51 ± 0.03 V • Power-down-reset: 1.50 ± 0.03 V	
Voltage detector			• Rising edge: 1.67 V to 3.13 V (12 stages) • Falling edge: 1.63 V to 3.06 V (12 stages)	
On-chip debug function			Provided	
Power supply voltage			V_{DD} = 1.6 to 3.6 V	
Operating ambient temperature			T_A = -40 to +85 °C (A: Consumer applications), T_A = -40 to +105 °C (G: Industrial applications)	

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Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS (A: TA = -40 to +85 °C)

This chapter describes the electrical specifications for the products A: Consumer applications (TA = -40 to +85 °C) and G: Industrial applications (when used in the range of TA = -40 to +85 °C).

Caution 1. The RL78 microcontroller has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. The pins mounted depend on the product. Refer to 1.3.1 80-pin products (with USB) to 1.3.4 100-pin products (without USB).

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) **(1/3)**

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V_{DD}		-0.5 to + 6.5	V
	UV_{BUS}		-0.5 to + 6.5	V
	AV_{DD}	$AV_{DD} \leq V_{DD}$	-0.5 to + 4.6	V
REGC pin input voltage	V_{IREGC}	REGC	-0.3 to + 2.8 and -0.3 to V_{DD} + 0.3 Note 1	V
U_{REGC} pin input voltage	V_{IUREGC}	U_{REGC}	-0.3 to UV_{BUS} + 0.3 Note 2	V
Input voltage	V_{I1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, EXCLK, EXCLKS, $\overline{\text{RESET}}$	-0.3 to V_{DD} + 0.3 Note 3	V
	V_{I2}	P60, P61 (N-ch open-drain)	-0.3 to + 6.5	V
	V_{I3}	UDP, UDM	-0.3 to + 6.5	V
	V_{I4}	P150 to P156	-0.3 to AV_{DD} + 0.3 Note 4	V
Output voltage	V_{O1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143	-0.3 to V_{DD} + 0.3 Note 3	V
	V_{O2}	P130, P150 to P156	-0.3 to AV_{DD} + 0.3 Note 3	V
	V_{O3}	UDP, UDM	-0.3 to + 3.8	V
Analog input voltage	V_{AI1}	ANI16 to ANI21	-0.3 to V_{DD} + 0.3 and $AV_{REF(+)}$ + 0.3 Notes 3, 5	V
	V_{AI2}	ANI0 to ANI6	-0.3 to AV_{DD} + 0.3 and $AV_{REF(+)}$ + 0.3 Notes 3, 5	V

Note 1. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Connect the U_{REGC} pin to Vss via a capacitor (0.33 μF). This value regulates the absolute maximum rating of the U_{REGC} pin. Do not use this pin with voltage applied to it.

Note 3. Must be 6.5 V or lower.

Note 4. Must be 4.6 V or lower.

Note 5. Do not exceed $AV_{REF(+)}$ + 0.3 V in case of A/D conversion target pin.

Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. $AV_{REF(+)}$: + side reference voltage of the A/D converter.

Remark 3. V_{SS}: Reference voltage

Absolute Maximum Ratings (T_A = 25°C) **(2/3)**

Parameter	Symbols	Conditions		Ratings	Unit
LCD voltage	V_{LI1}	V_{L1} input voltage Note 1		-0.3 to +2.8	V
	V_{LI2}	V_{L2} input voltage Note 1		-0.3 to +6.5	V
	V_{LI3}	V_{L3} input voltage Note 1		-0.3 to +6.5	V
	V_{LI4}	V_{L4} input voltage Note 1		-0.3 to +6.5	V
	V_{LI5}	CAPL, CAPH input voltage Note 1		-0.3 to +6.5	V
	V_{LO1}	V_{L1} output voltage		-0.3 to +2.8	V
	V_{LO2}	V_{L2} output voltage		-0.3 to +6.5	V
	V_{LO3}	V_{L3} output voltage		-0.3 to +6.5	V
	V_{LO4}	V_{L4} output voltage		-0.3 to +6.5	V
	V_{LO5}	CAPL, CAPH output voltage		-0.3 to +6.5	V
	V_{LO6}	COM0 to COM7 SEG0 to SEG55 output voltage	External resistance division method	-0.3 to V_{DD} + 0.3 Note 2	V
			Capacitor split method	-0.3 to V_{DD} + 0.3 Note 2	V
			Internal voltage boosting method	-0.3 to V_{LI4} + 0.3 Note 2	V

Note 1. This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to V_{SS} via a capacitor (0.47 ± 30%) and connect a capacitor (0.47 ± 30%) between the CAPL and CAPH pins.

Note 2. Must be 6.5 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Absolute Maximum Ratings (T_A = 25°C) **(3/3)**

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	-40	mA
		Total of all pins -170 mA	P40 to P46	-70	mA
			P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	-100	mA
	I_{OH2}	Per pin	P130, P150 to P156	-0.1	mA
		Total of all pins		-0.8	mA
	I_{OH3}	Per pin	UDP, UDM	-3	mA
Output current, low	I_{OL1}	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143	40	mA
		Total of all pins 170 mA	P40 to P46	70	mA
			P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	100	mA
	I_{OL2}	Per pin	P130, P150 to P156	0.4	mA
		Total of all pins		3.2	mA
	I_{OL3}	Per pin	UDP, UDM	3	mA
Operating ambient temperature	T_A	In normal operation mode		-40 to +85	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.2 Oscillator Characteristics

2.2.1 X1 and XT1 oscillator characteristics

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X) Note	Ceramic resonator/crystal resonator	2.7 V ≤ V_{DD} ≤ 3.6 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		16.0	
		1.8 V ≤ V_{DD} < 2.4 V	1.0		8.0	
		1.6 V ≤ V_{DD} < 1.8 V	1.0		4.0	
XT1 clock oscillation frequency (f_{XT}) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution **Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.**

Remark When using the X1 and XT1 oscillator, refer to **5.4 System Clock Oscillator in the RL78/L1C User's Manual Hardware**.

2.2.2 On-chip oscillator characteristics

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f_{HOCO}			1		48	MHz
High-speed on-chip oscillator clock frequency accuracy		-20 to +85°C	1.8 V ≤ V_{DD} ≤ 3.6 V	-1.0		+1.0	%
			1.6 V ≤ V_{DD} ≤ 1.8 V	-5.0		+5.0	%
		-40 to -20°C	1.8 V ≤ V_{DD} < 3.6 V	-1.5		+1.5	%
			1.6 V ≤ V_{DD} ≤ 1.8 V	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to **AC Characteristics** for instruction execution time.

2.2.3 PLL oscillator characteristics

(T_A = -40 to +85 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
PLL input frequency Note	f_{PLLIN}	High-speed system clock	6.00		16.00	MHz
PLL output frequency Note	f_{PLL}			48.00		MHz

Note Indicates only oscillator characteristics. Refer to **AC Characteristics** for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = -40 to +85 °C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143				-10.0 Note 2	mA
		Total of P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143 (When duty = 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			-15.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			-7.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			-3	mA
	I_{OH2}	Per pin for P130, P150 to P156	1.6 V ≤ V_{DD} ≤ 3.6 V			-0.1 Note 2	mA
		Total of all pins	1.6 V ≤ V_{DD} ≤ 3.6 V			-0.8	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

Note 2. However, do not exceed the total current value.

Note 3. Specification under conditions where the duty factor is 70%.
The output current value that has changed the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 50% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(50 × 0.01) = -14.0 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85 °C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	I_{OL1}	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143				20.0 Note 2	mA
		Per pin for P60 and P61				15.0 Note 2	mA
		Total of P40 to P46 (When duty = 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			15.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			9.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			4.5	mA
		Total of P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143 (When duty = 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			35.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			20.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			10.0	mA
		Total of all pins (When duty = 70% Note 3)				50.0	mA
	I_{OL2}	Per pin for P130, P150 to P156				0.4 Note 2	mA
		Total of all pins	1.6 V ≤ V_{DD} ≤ 3.6 V			3.2	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

Note 2. However, do not exceed the total current value.

Note 3. Specification under conditions where the duty factor is 70%.
The output current value that has changed the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 50% and I_{OL} = 10.0 mA
Total output current of pins = (10.0 × 0.7)/(50 × 0.01) = 14.0 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85 °C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0.8 V_{DD}		V_{DD}	V
	V_{IH2}	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	2.0		V_{DD}	V
			TTL input buffer 1.6 V ≤ V_{DD} < 3.3 V	1.50		V_{DD}	V
	V_{IH3}	P150 to P156		0.7 AV_{DD}		AV_{DD}	V
	V_{IH4}	P60, P61		0.7 V_{DD}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0.8 V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0		0.2 V_{DD}	V
	V_{IL2}	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	0		0.5	V
			TTL input buffer 1.6 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P150 to P156		0		0.3 AV_{DD}	V
	V_{IL4}	P60, P61		0		0.3 V_{DD}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		0.2 V_{DD}	V

Caution The maximum value of V_{IH} of pins P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 is V_{DD}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85 °C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH1} = -2.0 mA	V_{DD} - 0.6			V
			1.8 V ≤ V_{DD} ≤ 3.6 V, I_{OH1} = -1.5 mA	V_{DD} - 0.5			V
			1.6 V ≤ V_{DD} < 3.6 V, I_{OH1} = -1.0 mA	V_{DD} - 0.5			V
	V_{OH2}	P130, P150 to P156	1.6 V ≤ V_{DD} ≤ 3.6 V, I_{OH2} = -100 μA	AV_{DD} - 0.5			V
Output voltage, low	V_{OL1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL1} = 1.5 mA			0.4	V
			1.8 V ≤ V_{DD} ≤ 3.6 V, I_{OL1} = 0.6 mA			0.4	V
			1.6 V ≤ V_{DD} < 1.8 V, I_{OL1} = 0.3 mA			0.4	V
	V_{OL2}	P130, P150 to P156	1.6 V ≤ V_{DD} ≤ 3.6 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60, P61	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL3} = 3.0 mA			0.4	V
			1.8 V ≤ V_{DD} ≤ 3.6 V, I_{OL3} = 2.0 mA			0.4	V
			1.6 V ≤ V_{DD} ≤ 1.8 V, I_{OL3} = 1.0 mA			0.4	V

Caution P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85 °C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, $\overline{RESET}$	$V_I = V_{DD}$				1	μA
	I_{LIH2}	P20, P21, P140 to P143	$V_I = V_{DD}$				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	$V_I = V_{DD}$	In input port or external clock input			1	μA
				In resonator connection			10	μA
	I_{LIH4}	P150 to P156	$V_I = AV_{DD}$				1	μA
Input leakage current, low	I_{LIL1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, $\overline{RESET}$	$V_I = V_{SS}$				-1	μA
	I_{LIL2}	P20, P21, P140 to P143	$V_I = V_{SS}$				-1	μA
	I_{LIL3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	$V_I = V_{SS}$	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
	I_{LIL4}	P150 to P156	$V_I = AV_{SS}$				-1	μA
On-chip pull-up resistance	R_{U1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P140 to P143, P125 to P127	$V_I = V_{SS}$	2.4 V ≤ V_{DD} ≤ 3.6 V	10	20	100	kΩ
				1.6 V ≤ V_{DD} ≤ 2.4 V	10	30	100	
	R_{U2}	P40 to P46, P80 to P83	$V_I = V_{SS}$		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	f_{HOCO} = 48 MHz Note 3, f_{IH} = 24 MHz Note 3	Basic operation	V_{DD} = 3.6 V		2.2	2.8	mA
						V_{DD} = 3.0 V		2.2	2.8	
					Normal operation	V_{DD} = 3.6 V		4.4	8.5	
						V_{DD} = 3.0 V		4.4	8.5	
				f_{HOCO} = 24 MHz Note 3, f_{IH} = 24 MHz Note 3	Basic operation	V_{DD} = 3.6 V		2.0	2.6	
						V_{DD} = 3.0 V		2.0	2.6	
					Normal operation	V_{DD} = 3.6 V		4.2	6.8	
						V_{DD} = 3.0 V		4.2	6.8	
				f_{HOCO} = 16 MHz Note 3, f_{IH} = 16 MHz Note 3	Normal operation	V_{DD} = 3.6 V		3.1	4.9	
						V_{DD} = 3.0 V		3.1	4.9	
			LS (low-speed main) mode Note 5	f_{HOCO} = 8 MHz Note 3, f_{IH} = 8 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.4	2.2	mA
						V_{DD} = 2.0 V		1.4	2.2	
			LV (low-voltage main) mode Note 5	f_{HOCO} = 4 MHz Note 3, f_{IH} = 4 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.3	1.8	mA
						V_{DD} = 2.0 V		1.3	1.8	
			HS (high-speed main) mode Note 5	f_{MX} = 20 MHz Note 2, V_{DD} = 3.6 V	Normal operation	Square wave input		3.5	5.5	mA
						Resonator connection		3.6	5.7	
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		3.5	5.5	
						Resonator connection		3.6	5.7	
				f_{MX} = 16 MHz Note 2, V_{DD} = 3.6 V	Normal operation	Square wave input		2.9	4.5	
						Resonator connection		3.1	4.6	
				f_{MX} = 16 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.9	4.5	
						Resonator connection		3.1	4.6	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.6 V	Normal operation	Square wave input		2.1	3.2	
						Resonator connection		2.2	3.2	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.1	3.2	
						Resonator connection		2.2	3.2	
			LS (low-speed main) mode Note 5	f_{MX} = 8 MHz Note 2, V_{DD} = 3.6 V	Normal operation	Square wave input		1.2	2.0	mA
						Resonator connection		1.3	2.0	
				f_{MX} = 8 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.2	2.1	
						Resonator connection		1.3	2.2	
			HS (High-speed main) mode (PLL operation)	f_{PLL} = 48 MHz, f_{CLK} = 24 MHz Note 2	Normal operation	V_{DD} = 3.6 V		4.7	7.5	mA
						V_{DD} = 3.0 V		4.7	7.5	
				f_{PLL} = 48 MHz, f_{CLK} = 12 MHz Note 2	Normal operation	V_{DD} = 3.6 V		3.1	5.1	
						V_{DD} = 3.0 V		3.1	5.1	
				f_{PLL} = 48 MHz, f_{CLK} = 6 MHz Note 2	Normal operation	V_{DD} = 3.6 V		2.3	3.9	
						V_{DD} = 3.0 V		2.3	3.9	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 4 T_A = -40°C	Normal operation	Square wave input		4.6	6.9	µA
						Resonator connection		4.7	6.9	
				f_{SUB} = 32.768 kHz Note 4 T_A = +25°C	Normal operation	Square wave input		4.9	7.0	
						Resonator connection		5.0	7.2	
				f_{SUB} = 32.768 kHz Note 4 T_A = +50°C	Normal operation	Square wave input		5.2	7.6	
						Resonator connection		5.2	7.7	
				f_{SUB} = 32.768 kHz Note 4 T_A = +70°C	Normal operation	Square wave input		5.5	9.3	
						Resonator connection		5.6	9.4	
				f_{SUB} = 32.768 kHz Note 4 T_A = +85°C	Normal operation	Square wave input		6.2	13.3	
						Resonator connection		6.2	13.4	

(Notes and Remarks are listed on the next page.)

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the high accuracy RTC, 12-bit interval timer, and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	2.7 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 24 MHz
	2.4 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 16 MHz
LS (low-speed main) mode:	1.8 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 8 MHz
LV (low-voltage main) mode	1.6 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 4 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

Remark 3. f_{IH}: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 48 MHz Note 4, f_{IH} = 24 MHz Note 4	V_{DD} = 3.6 V		0.77	2.70	mA
					V_{DD} = 3.0 V		0.77	2.70	
				f_{HOCO} = 24 MHz Note 4, f_{IH} = 24 MHz Note 4	V_{DD} = 3.6 V		0.55	1.91	
					V_{DD} = 3.0 V		0.55	1.90	
				f_{HOCO} = 16 MHz Note 4, f_{IH} = 16 MHz Note 4	V_{DD} = 3.6 V		0.48	1.41	
					V_{DD} = 3.0 V		0.47	1.41	
			LS (low-speed main) mode Note 7	f_{HOCO} = 8 MHz Note 4, f_{IH} = 8 MHz Note 4	V_{DD} = 3.0 V		300	770	μA
					V_{DD} = 2.0 V		300	770	
			LV (low-voltage main) mode Note 7	f_{HOCO} = 4 MHz Note 4, f_{IH} = 4 MHz Note 4	V_{DD} = 3.0 V		440	770	μA
					V_{DD} = 2.0 V		440	770	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 3.6 V	Square wave input		0.35	1.63	mA
					Resonator connection		0.51	1.68	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.34	1.63	
					Resonator connection		0.51	1.68	
				f_{MX} = 16 MHz Note 3, V_{DD} = 3.6 V	Square wave input		0.30	1.22	
					Resonator connection		0.45	1.39	
				f_{MX} = 16 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.29	1.20	
					Resonator connection		0.45	1.38	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.6 V	Square wave input		0.23	0.82	
					Resonator connection		0.30	0.90	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.22	0.81	
					Resonator connection		0.30	0.89	
			LS (low-speed main) mode Note 7	f_{MX} = 8 MHz Note 3, V_{DD} = 3.0 V	Square wave input		120	510	μA
					Resonator connection		170	560	
				f_{MX} = 8 MHz Note 3, V_{DD} = 2.0 V	Square wave input		130	520	
					Resonator connection		170	570	
			HS (High-speed main) mode (PLL operation)	f_{MX} = 48 MHz, f_{CLK} = 24 MHz Note 3	V_{DD} = 3.6 V		0.99	2.89	mA
					V_{DD} = 3.0 V		0.99	2.88	
				f_{MX} = 48 MHz, f_{CLK} = 12 MHz Note 3	V_{DD} = 3.6 V		0.89	2.48	
					V_{DD} = 3.0 V		0.89	2.47	
				f_{MX} = 48 MHz, f_{CLK} = 6 MHz Note 3	V_{DD} = 3.6 V		0.84	2.27	
					V_{DD} = 3.0 V		0.84	2.27	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5 T_A = -40°C	Square wave input		0.32	0.61	μA
					Resonator connection		0.51	0.80	
				f_{SUB} = 32.768 kHz Note 5 T_A = +25°C	Square wave input		0.41	0.74	
					Resonator connection		0.62	0.91	
				f_{SUB} = 32.768 kHz Note 5 T_A = +50°C	Square wave input		0.52	2.30	
					Resonator connection		0.75	2.49	
				f_{SUB} = 32.768 kHz Note 5 T_A = +70°C	Square wave input		0.82	4.03	
					Resonator connection		1.08	4.22	
				f_{SUB} = 32.768 kHz Note 5 T_A = +85°C	Square wave input		1.38	8.04	
					Resonator connection		1.62	8.23	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.18	0.52	μA
			T_A = +25°C				0.25	0.52	
			T_A = +50°C				0.34	2.21	
			T_A = +70°C				0.64	3.94	
			T_A = +85°C				1.18	7.95	

(Notes and Remarks are listed on the next page.)

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. During HALT instruction execution by flash memory.

Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 4. When high-speed system clock and subsystem clock are stopped.

Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the high accuracy RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 6. Not including the current flowing into the high accuracy RTC, 12-bit interval timer, and watchdog timer.

Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 24 MHz
2.4 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 8 MHz
LV (low-voltage main) mode 1.6 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 4 MHz

Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

Remark 3. f_{IH}: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1						0.20		μA
High-accuracy RTC operating current	I_{RTC} Notes 1, 3						0.02		μA
12-bit interval timer operating current	I_{TMKA} Notes 1, 2, 4						0.02		μA
Watchdog timer operating current	I_{WDT} Notes 1, 4	f_{IL} = 15 kHz					0.22		μA
A/D converter operating current	I_{ADC} Notes 6, 7	AV_{DD} = 3.0 V, when conversion at maximum speed					422	720	μA
$AV_{REF(+)}$ current	I_{AVREF} Note 8	AV_{DD} = 3.0 V, ADREFP1 = 0, ADREFP0 = 0 Note 7					14.0	25.0	μA
		AV_{REFP} = 3.0 V, ADREFP1 = 0, ADREFP0 = 1 Note 10					14.0	25.0	
		ADREFP1 = 1, ADREFP0 = 0 Note 1					14.0	25.0	
A/D converter reference voltage current	I_{ADREF} Notes 1, 9	V_{DD} = 3.0 V					75.0		μA
Temperature sensor operating current	I_{TMPS} Note 1						78		μA
D/A converter operating current	I_{DAC} Notes 1, 11	Per D/A converter channel					0.53	1.5	mA
Comparator operating current	I_{CMP} Notes 1, 12	V_{DD} = 3.6 V, Regulator output voltage = 2.1 V	Window mode				12.5		μA
			Comparator high-speed mode				4.5		μA
			Comparator low-speed mode				1.2		μA
		V_{DD} = 3.6 V, Regulator output voltage = 1.8 V	Window mode				7.05		μA
			Comparator high-speed mode				2.2		μA
			Comparator low-speed mode				0.9		μA
LVD operating current	I_{LVI} Notes 1, 13						0.06		μA
Self-programming operating current	I_{FSP} Notes 1, 14						2.50	12.20	mA
BGO operating current	I_{BGO} Notes 1, 15						1.68	12.20	mA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation	The mode is performed Note 16				0.34	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V				0.53	2.04	
		CSI/UART operation					0.70	1.54	mA
LCD operating current	I_{LCD1} Notes 17, 18	External resistance division method	f_{LCD} = f_{SUB} LCD clock = 128 Hz	1/3 bias 4-time slice	V_{DD} = 3.6 V, L_{V4} = 3.6 V		0.14		μA
	I_{LCD2} Note 17	Internal voltage boosting method	f_{LCD} = f_{SUB} LCD clock = 128 Hz	1/3 bias 4-time slice	V_{DD} = 3.0 V, L_{V4} = 3.0 V (VLCD = 04H)		0.61		μA
	I_{LCD3} Note 17	Capacitor split method	f_{LCD} = f_{SUB} LCD clock = 128 Hz	1/3 bias 4-time slice	V_{DD} = 3.0 V, L_{V4} = 3.0 V		0.12		μA
USB current Note 19	I_{USB} Note 20	Operating current during USB communication					4.88		mA
	I_{USB} Note 21	Operating current in the USB suspended state					0.04		mA

(Notes and Remarks are listed on the next page.)

Note 1. Current flowing to V_{DD}.

Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.

Note 3. Current flowing only to the high accuracy real-time clock (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the high accuracy real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the high accuracy real-time clock.

Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{TMKA}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the 12-bit interval timer.

Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates in STOP mode.

Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC}, I_{AVREF}, I_{ADREF} when the A/D converter operates in an operation mode or the HALT mode.

Note 7. Current flowing to the AV_{DD}.

Note 8. Current flowing from the reference voltage source of A/D converter.

Note 9. Operation current flowing to the internal reference voltage.

Note 10. Current flowing to the AV_{REFP}.

Note 11. Current flowing only to the D/A converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{DA} when the D/A converter operates in an operation mode or the HALT mode.

Note 12. Current flowing only to the comparator circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{CMP} when the comparator circuit operates in the Operating, HALT or STOP mode.

Note 13. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVI} when the LVD circuit operates in the Operating, HALT or STOP mode.

Note 14. Current flowing only during self-programming.

Note 15. Current flowing only during data flash rewrite.

Note 16. For shift time to the SNOOZE mode, see **23.3.3 SNOOZE mode in the RL78/L1C User's Manual Hardware**.

Note 17. Current flowing only to the LCD controller/driver (V_{DD} pin). The current value of the RL78 microcontrollers is the sum of the LCD operating current (I_{LCD1}, I_{LCD2} or I_{LCD3}) to the supply current (I_{DD1}, or I_{DD2}) when the LCD controller/driver operates in an operation mode or HALT mode. Not including the current that flows through the LCD panel.

Note 18. Not including the current that flows through the external divider resistor divider resistor.

Note 19. Current flowing to the UV_{BUS}.

Note 20. Including the operating current when f_{PLL} = 48 MHz.

Note 21. Including the current supplied from the pull-up resistor of the UDP pin to the pull-down resistor of the host device, in addition to the current consumed by this MCU during the suspended state.

Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency

Remark 4. Temperature condition of the TYP. value is T_A = 25°C

2.4 AC Characteristics

2.4.1 Basic operation

(T_A = -40 to +85 °C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(1/2)**

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ V_{DD} ≤ 3.6 V	0.25		1	μs
		Subsystem clock (f_{SUB}) operation		1.8 V ≤ V_{DD} ≤ 3.6 V	28.5	30.5	31.3	μs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V	0.25		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 3.6 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
		1.8 V ≤ V_{DD} < 2.4 V			1.0		8.0	MHz
		1.6 V ≤ V_{DD} < 1.8 V			1.0		4.0	MHz
	f_{EXT}				32		35	kHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 3.6 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
		1.8 V ≤ V_{DD} < 2.4 V			60			ns
		1.6 V ≤ V_{DD} < 1.8 V			120			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns

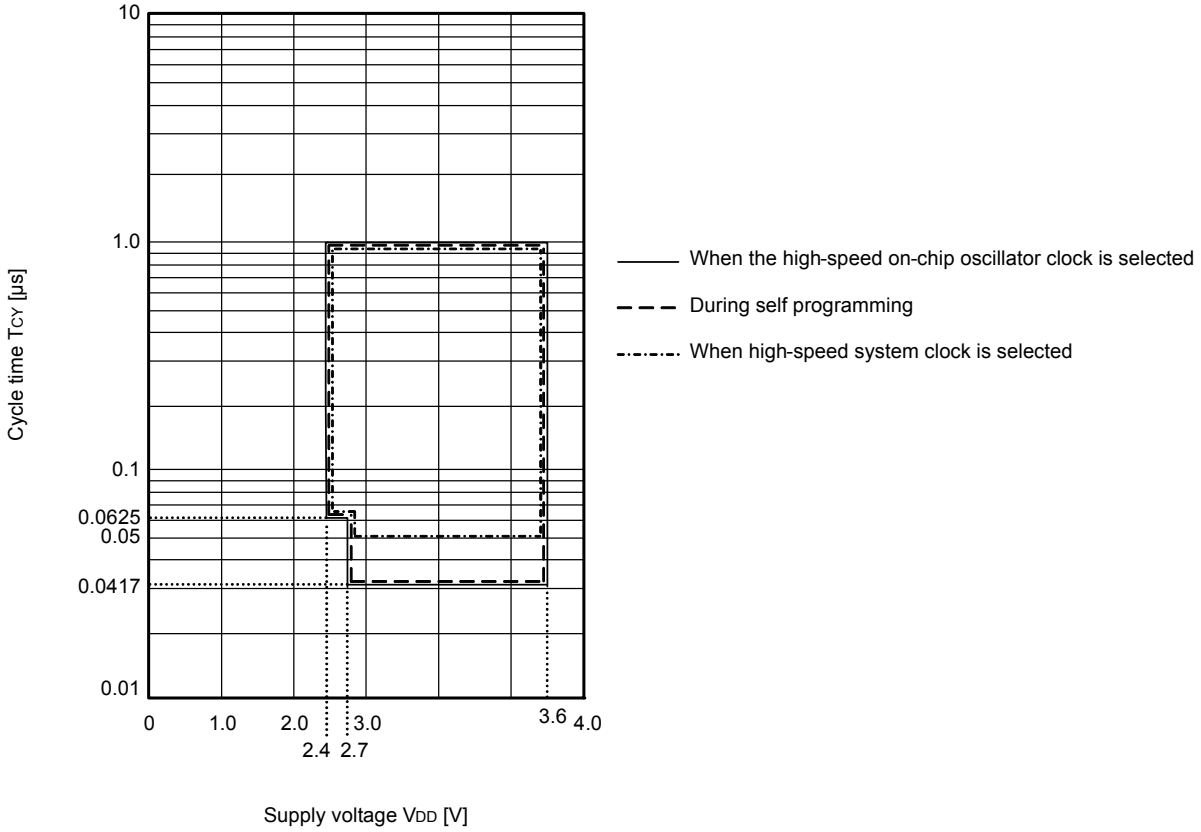
Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 7))

(T_A = -40 to +85 °C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(2/2)**

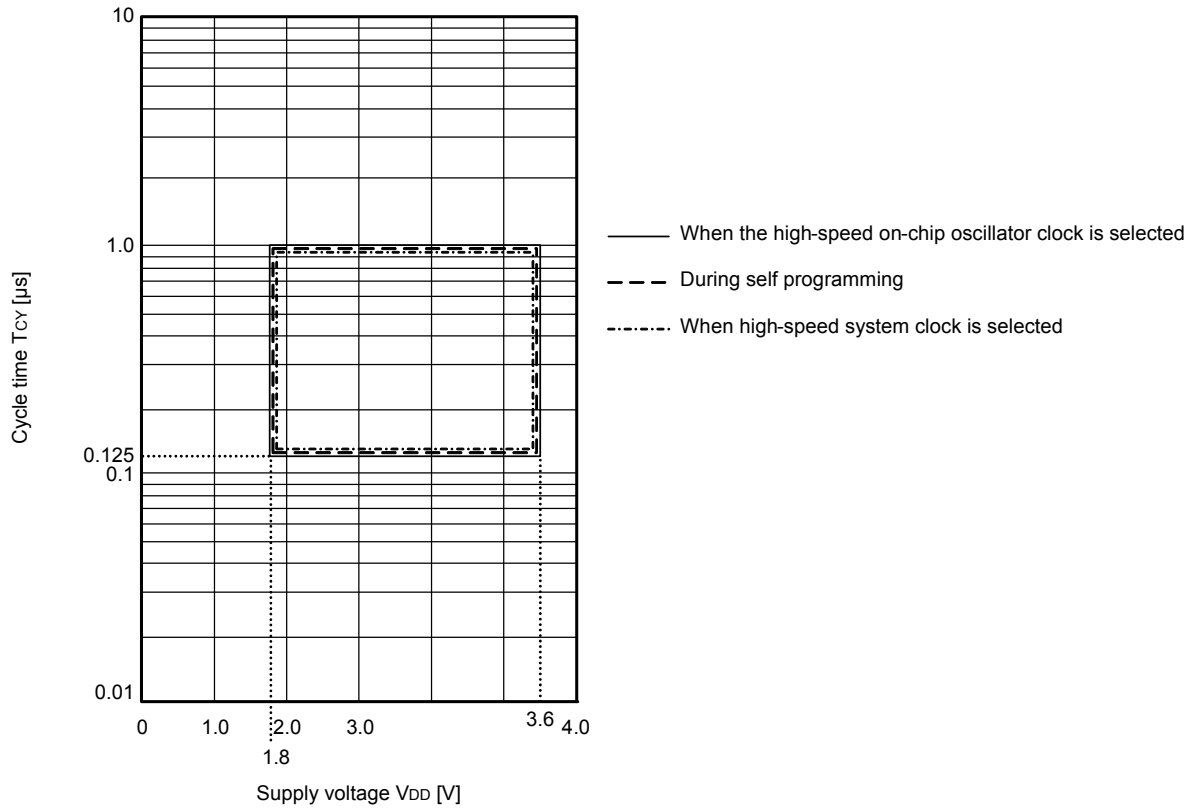
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
TO00 to TO07, TKBO00, TKBO01, TKBO10, TKBO11, TKBO20, TKBO21 output frequency	f_{TO}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			8	MHz
		LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			4	MHz
		LV (low-voltage main) mode	1.6 V ≤ V_{DD} ≤ 3.6 V			2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			8	MHz
		LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			4	MHz
		LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 3.6 V			2	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0 to INTP7	1.6 V ≤ V_{DD} ≤ 3.6 V	1			µs
Key interrupt input low-level width	t_{KR}	1.8 V ≤ V_{DD} ≤ 3.6 V		250			ns
		1.6 V ≤ V_{DD} < 1.8 V		1			µs
TMKB2 forced output stop input high-level width	t_{IHR}	INTP0 to INTP7	f_{CLK} > 16 MHz	125			ns
			f_{CLK} ≤ 16 MHz	2			f_{CLK}
$\overline{\text{RESET}}$ low-level width	t_{RSL}			10			µs

Minimum Instruction Execution Time during Main System Clock Operation

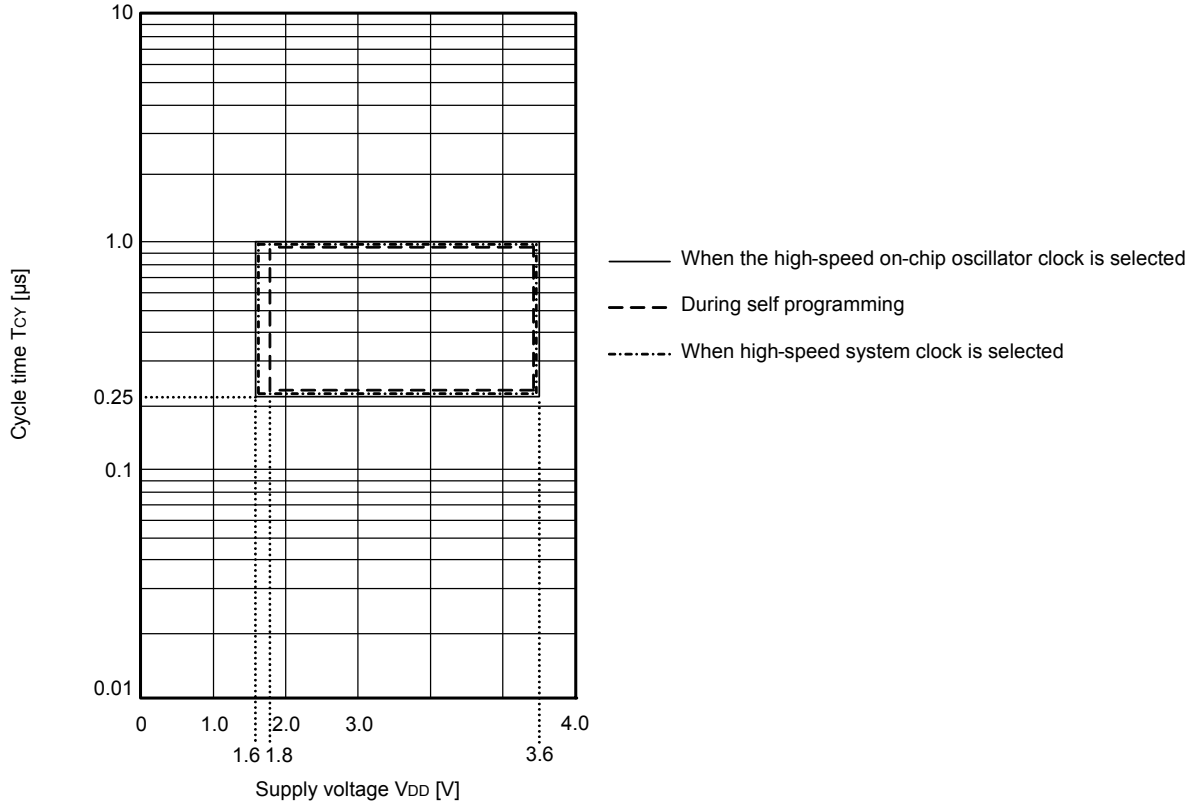
TCY vs VDD (HS (high-speed main) mode)



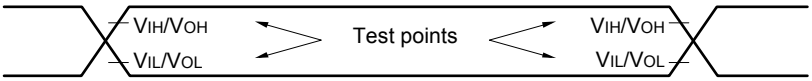
TCY vs VDD (LS (low-speed main) mode)



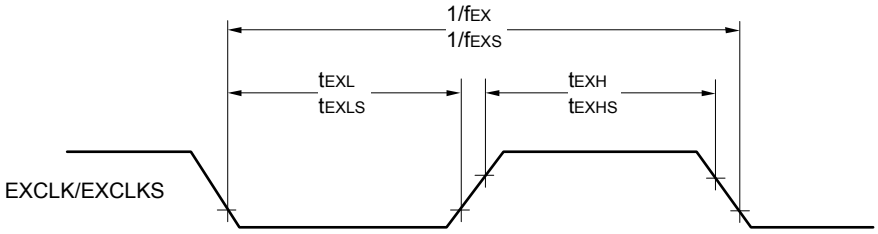
TCY vs VDD (LV (low-voltage main) mode)



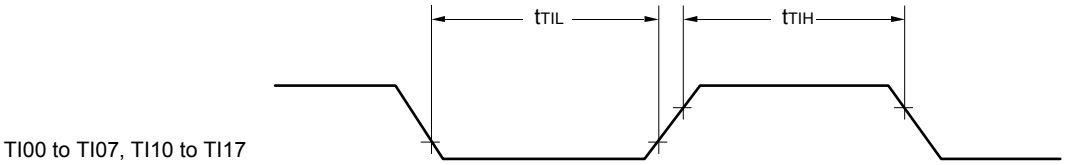
AC Timing Test Points

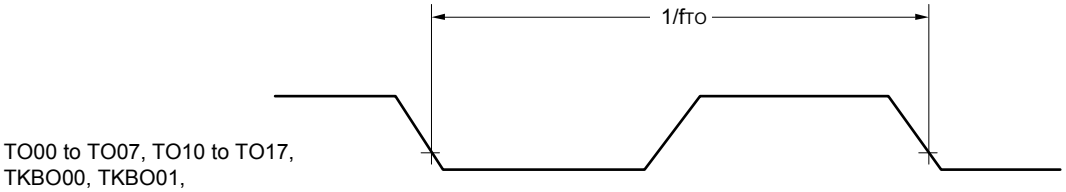


External System Clock Timing

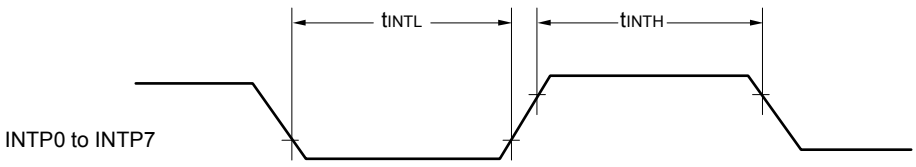


TI/TO Timing

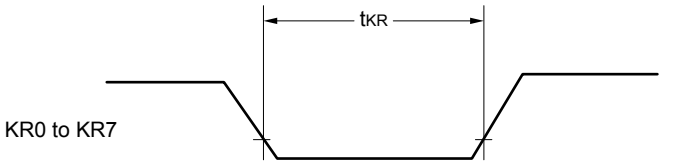




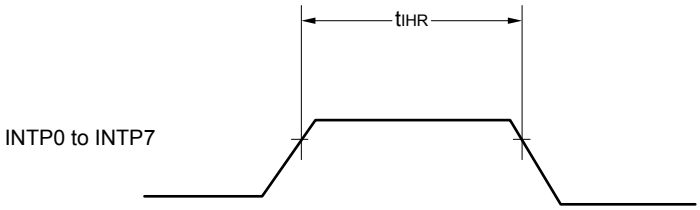
Interrupt Request Input Timing



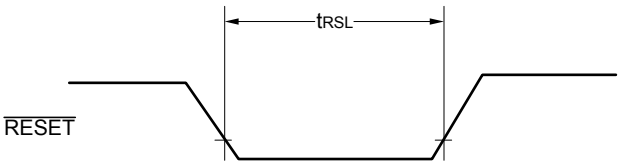
Key Interrupt Input Timing



Timer KB2 Input Timing

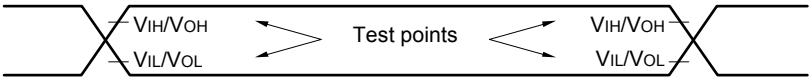


$\overline{\text{RESET}}$ Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +85 °C, 1.6 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.7 V ≤ VDD ≤ 3.6 V		fMCK/6 Note 2		fMCK/6		fMCK/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3		0.6	Mbps
		2.4 V ≤ VDD ≤ 3.6 V		fMCK/6 Note 2		fMCK/6		fMCK/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.6		1.3		0.6	Mbps
		1.8 V ≤ VDD ≤ 3.6 V		—		fMCK/6 Note 2		fMCK/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		—		1.3		0.6	Mbps
		1.6 V ≤ VDD ≤ 3.6 V		—		—		fMCK/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		—		—		0.6	Mbps

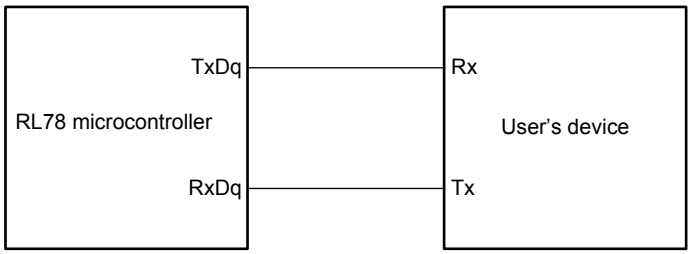
Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The following conditions are required for low voltage interface.
2.4 V ≤ VDD < 2.7 V: MAX. 2.6 Mbps
1.8 V ≤ VDD < 2.4 V: MAX. 1.3 Mbps
1.6 V ≤ VDD < 1.8 V: MAX. 0.6 Mbps

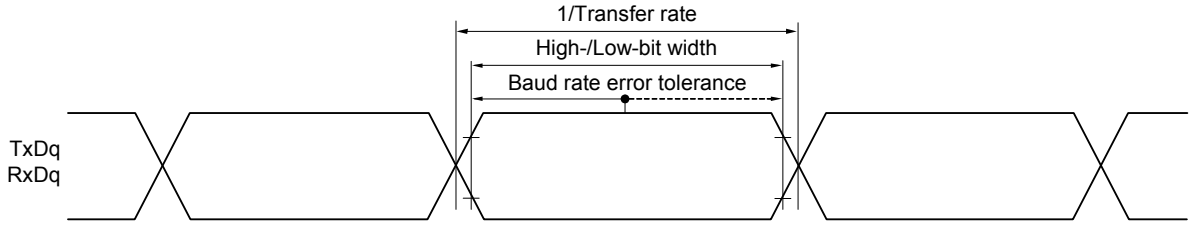
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fCLK) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ VDD ≤ 3.6 V)
16 MHz (2.4 V ≤ VDD ≤ 3.6 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ VDD ≤ 3.6 V)
LV (low-voltage main) mode: 4 MHz (1.6 V ≤ VDD ≤ 3.6 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 2. fMCK: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85 °C, 2.7 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/2$ 2.7 V ≤ V_{DD} ≤ 3.6 V	167		250		500		ns
SCKp high-/low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V	$t_{KCY1}/2$ - 10		$t_{KCY1}/2$ - 50		$t_{KCY1}/2$ - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V	33		110		110		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 20 pF Note 4		10		10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 2)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7 V ≤ V_{DD} ≤ 3.6 V	167		500		1000		ns
			2.4 V ≤ V_{DD} ≤ 3.6 V	250		500		1000		ns
			1.8 V ≤ V_{DD} ≤ 3.6 V	—		500		1000		ns
			1.6 V ≤ V_{DD} ≤ 3.6 V	—		—		1000		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 18		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 38		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		t_{KCY1}/2 - 100		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V		44		110		110		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		75		110		110		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		110		110		ns
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		220		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}	2.4 V ≤ V_{DD} ≤ 3.6 V		19		19		19		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		19		19		ns
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		19		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 3.6 V		25		50		50	ns
			2.4 V ≤ V_{DD} ≤ 3.6 V		25		50		50	ns
			1.8 V ≤ V_{DD} ≤ 3.6 V		—		50		50	ns
			1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)

Remark 2. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	2.7 V ≤ V_{DD} < 3.6 V	f_{MCK} > 16 MHz	8/f_{MCK}		—		—		ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 3.6 V		6/f_{MCK} and 500		6/f_{MCK} and 500		6/f_{MCK} and 500		ns
		1.8 V ≤ V_{DD} < 3.6 V		—		6/f_{MCK} and 750		6/f_{MCK} and 750		ns
		1.6 V ≤ V_{DD} < 3.6 V		—		—		6/f_{MCK} and 1500		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		t_{KCY2}/2 - 8		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		t_{KCY2}/2 - 18		t_{KCY2}/2 - 18		ns
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		t_{KCY1}/2 - 66		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V ≤ V_{DD} < 3.6 V		—		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.6 V ≤ V_{DD} < 3.6 V		—		—		1/f_{MCK} + 40		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}	2.4 V ≤ V_{DD} < 3.6 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ V_{DD} < 3.6 V		—		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.6 V ≤ V_{DD} < 3.6 V		—		—		1/f_{MCK} + 250		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 44		2/f_{MCK} + 110		2/f_{MCK} + 110	ns
			2.4 V ≤ V_{DD} < 3.6 V		2/f_{MCK} + 75		2/f_{MCK} + 110		2/f_{MCK} + 110	ns
			1.8 V ≤ V_{DD} < 3.6 V		—		2/f_{MCK} + 110		2/f_{MCK} + 110	ns
			1.6 V ≤ V_{DD} < 3.6 V		—		—		2/f_{MCK} + 220	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

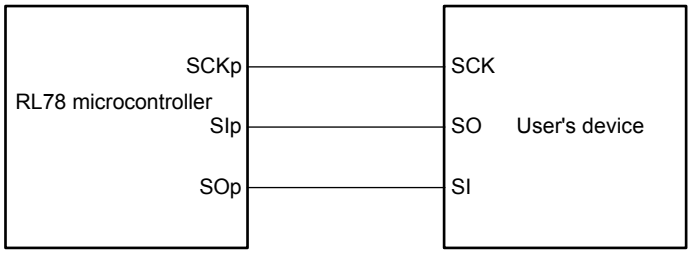
Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

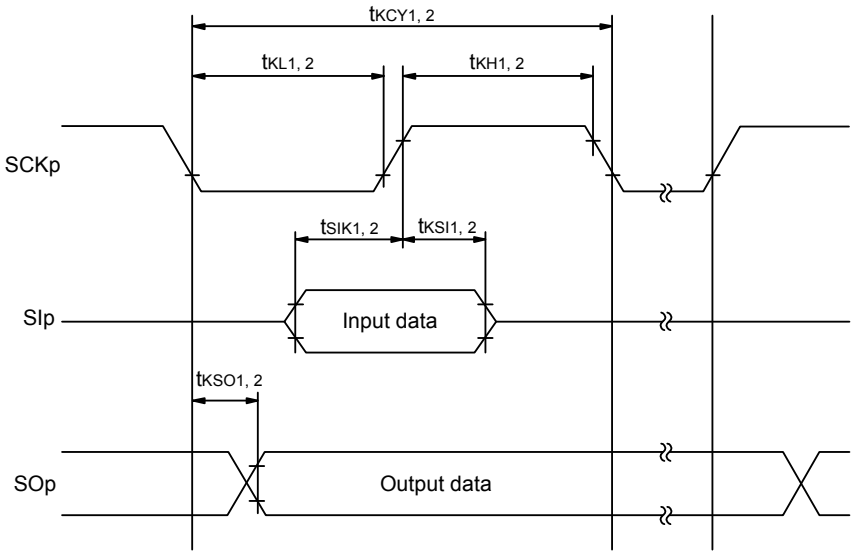
CSI mode connection diagram (during communication at same potential)



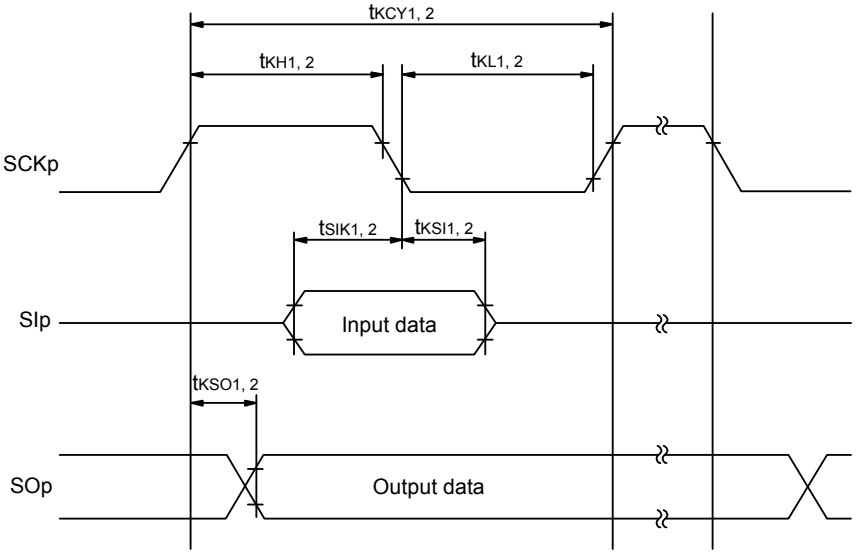
Remark 1. p: CSI number (p = 00, 10, 20, 30)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 10, 20, 30)
Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(5) During communication at same potential (simplified I^2C mode)

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

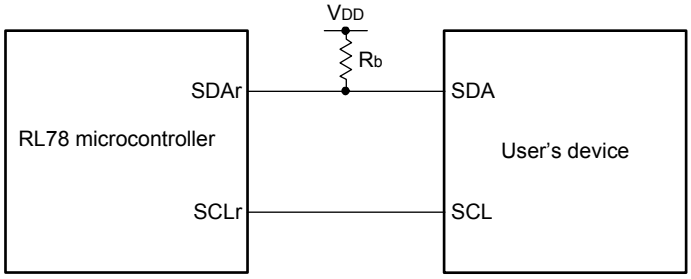
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ		—		—		250	kHz
Hold time when SCLr = “L”	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		1850		ns
Hold time when SCLr = “H”	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		1850		ns
Data setup time (reception)	t_{SU}: DAT	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 85 Note 2		1/f_{MCK} + 145 Note 2		1/f_{MCK} + 145 Note 2		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 145 Note 2		1/f_{MCK} + 145 Note 2		1/f_{MCK} + 145 Note 2		ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1/f_{MCK} + 230 Note 2		1/f_{MCK} + 230 Note 2		1/f_{MCK} + 230 Note 2		ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		1/f_{MCK} + 290 Note 2		ns
Data hold time (transmission)	t_{HD}: DAT	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		1.8 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	—		—		0	405	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

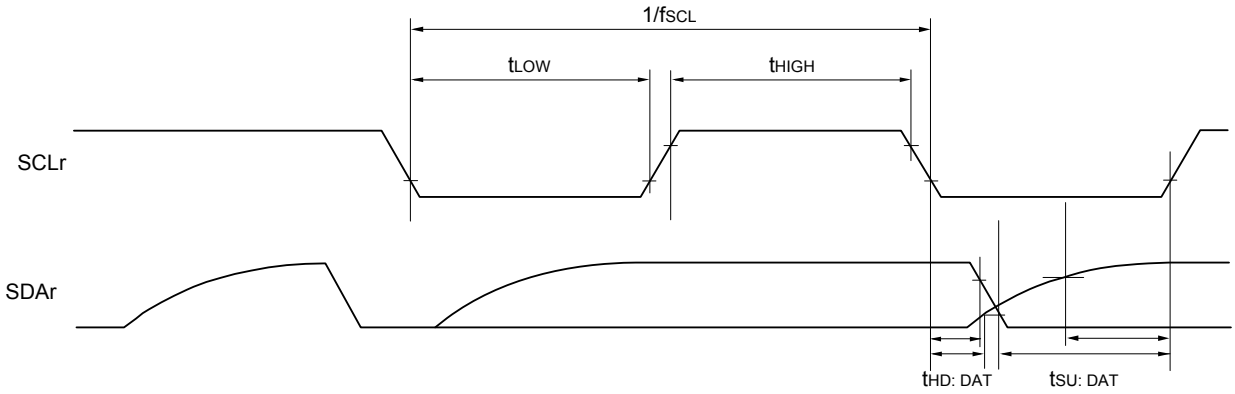
Note 2. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remark 1. Rb[Ω]: Communication line (SDAr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM number (g = 0 to 3),
h: POM number (h = 0 to 3)

Remark 3. fMCK: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),
n: Channel number (n = 0, 2), mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5 V) (UART mode) (dedicated baud rate generator output)

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Notes 1, 2		reception	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 4		4.0		1.3		0.6	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		f_{MCK}/6 Notes 1, 2, 3		f_{MCK}/6 Notes 1, 2, 3		f_{MCK}/6 Notes 1, 2, 3	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 4		4.0		1.3		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.

Note 2. Use it with V_{DD} ≥ Vb.

Note 3. The following conditions are required for low voltage interface.

2.4 V ≤ V_{DD} < 2.7 V: MAX. 2.6 Mbps

1.8 V ≤ V_{DD} < 2.4 V: MAX. 1.3 Mbps

1.6 V ≤ V_{DD} < 1.8 V: MAX. 0.6 Mbps

Note 4. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 3.6 V)

16 MHz (2.4 V ≤ V_{DD} ≤ 3.6 V)

LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 3.6 V)

LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 3.6 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5V) (UART mode) (dedicated baud rate generator output)

(T_A = -40 to +85 °C, 1.8 ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 2		transmission	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 2		1.2 Note 2		1.2 Note 2	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Notes 3, 4		Notes 3, 4		Notes 3, 4	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 5		0.43 Note 5		0.43 Note 5	Mbps

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} < 3.6 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. Use it with $V_{DD} \geq V_b$.

Note 4. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 1.8 V ≤ V_{DD} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

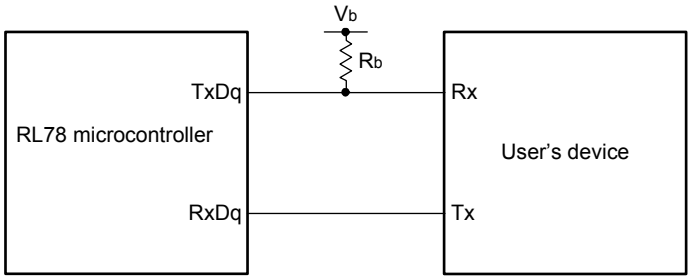
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

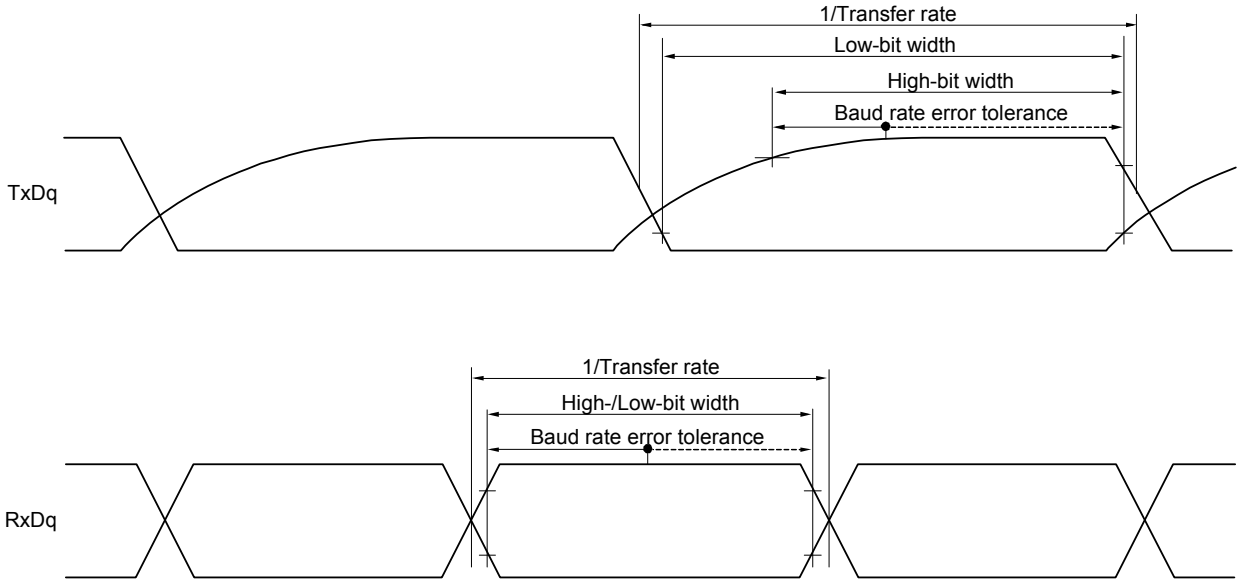
Note 5. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Remark 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(7) Communication at different potential (2.5 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85 °C, 2.7 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/2$	2.7V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1150		1150		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 10		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 1.4 kΩ			130		130		130	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			10		10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0),
n: Channel number (n = 0), g: PIM and POM number (g = 2)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00))

(8) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7V ≤ V_{DD} < 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500 Note		1150		1150		ns
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 1.8 V, C_b = 30 pF, R_b = 5.5 kΩ	1150 Note		1150		1150		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 18		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns

Note Use it with $V_{DD} \geq V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	177		479		479		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	479		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		195		195		195	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		483		483		483	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	44		110		110		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	110		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25		25	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		25		25		25	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

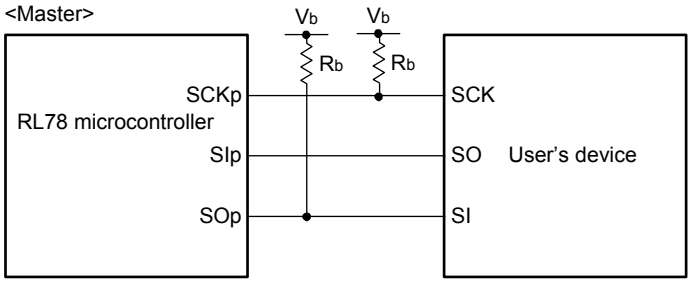
Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. Use it with V_{DD} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

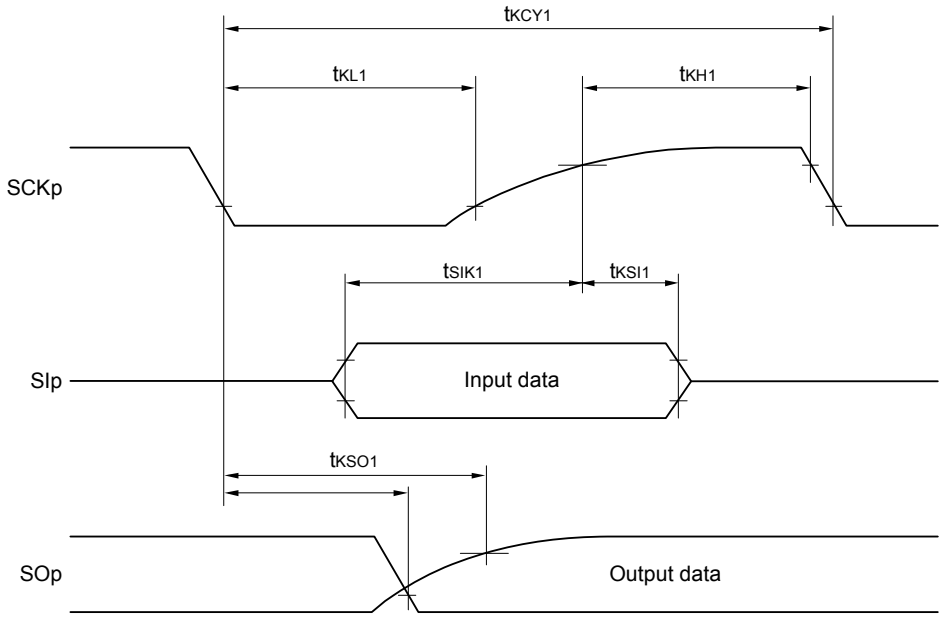


Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

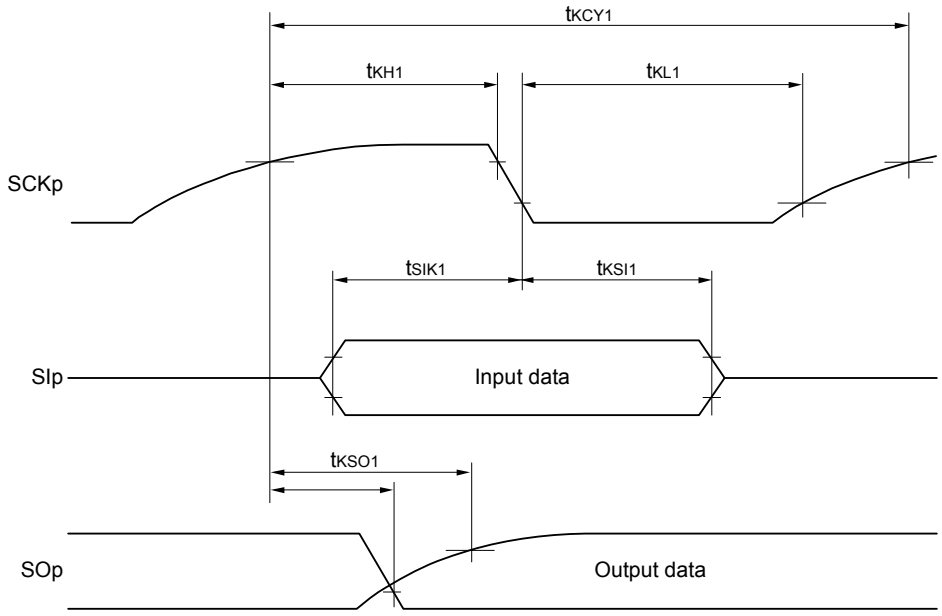
Remark 2. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM number (g = 0 to 3)

(9) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	16/f_{MCK}		—		—		ns
			16 MHz < f_{MCK} ≤ 20 MHz	14/f_{MCK}		—		—		ns
			8 MHz < f_{MCK} ≤ 16 MHz	12/f_{MCK}		—		—		ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}		—		ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	20 MHz < f_{MCK} ≤ 24 MHz	36/f_{MCK}		—		—		ns
			16 MHz < f_{MCK} ≤ 20 MHz	32/f_{MCK}		—		—		ns
			8 MHz < f_{MCK} ≤ 16 MHz	26/f_{MCK}		—		—		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		16/f_{MCK}		—		ns
			f_{MCK} ≤ 4 MHz	10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 - 18		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		t_{KCY2}/2 - 50		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V ≤ V_{DD} < 3.3 V		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}			1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
Delay time from SCKp↓ to SOp output Note 5	t_{KSO2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 214		2/f_{MCK} + 573		2/f_{MCK} + 573	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2 C_b = 30 pF, R_b = 5.5 kΩ			2/f_{MCK} + 573		2/f_{MCK} + 573		2/f_{MCK} + 573	ns

(Notes and Caution are listed on the next page. Remarks are listed on the page after the next page.)

Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Note 2. Use it with $V_{DD} \geq V_b$.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

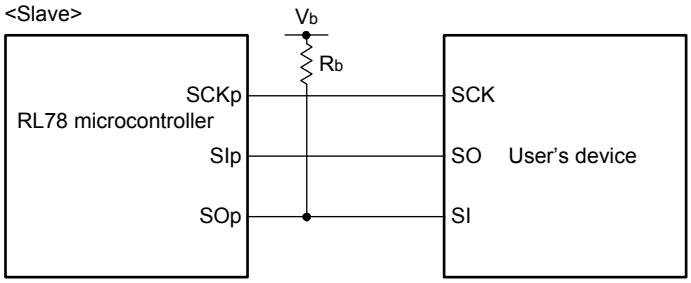
Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

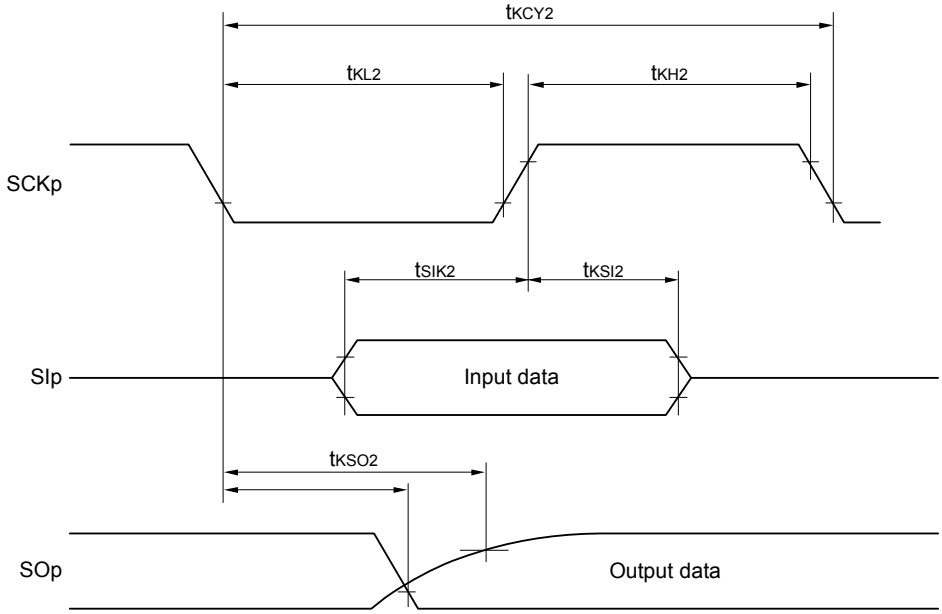


Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

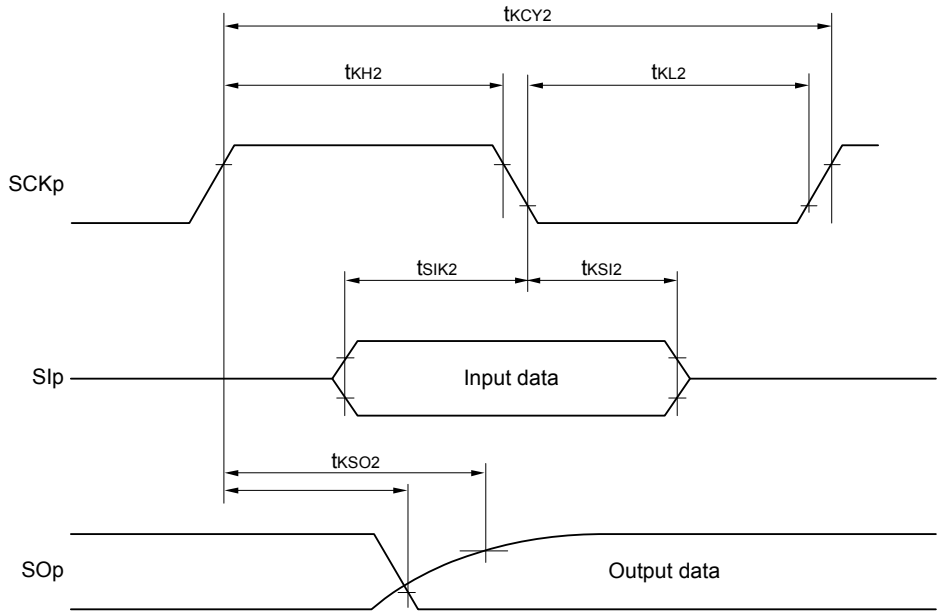
Remark 2. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02, 10, 12))

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

(10) Communication at different potential (1.8 V, 2.5 V) (simplified I²C mode)

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b <2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = “L”	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1550		1550		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b <2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1150		1550		1550		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1550		1550		1550		ns
Hold time when SCLr = “H”	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	200		610		610		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	600		610		610		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	610		610		610		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 135 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	0	405	0	405	0	405	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

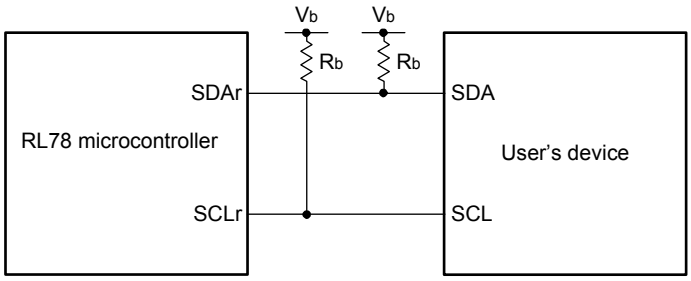
Note 2. Use it with $V_{DD} \geq V_b$.

Note 3. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

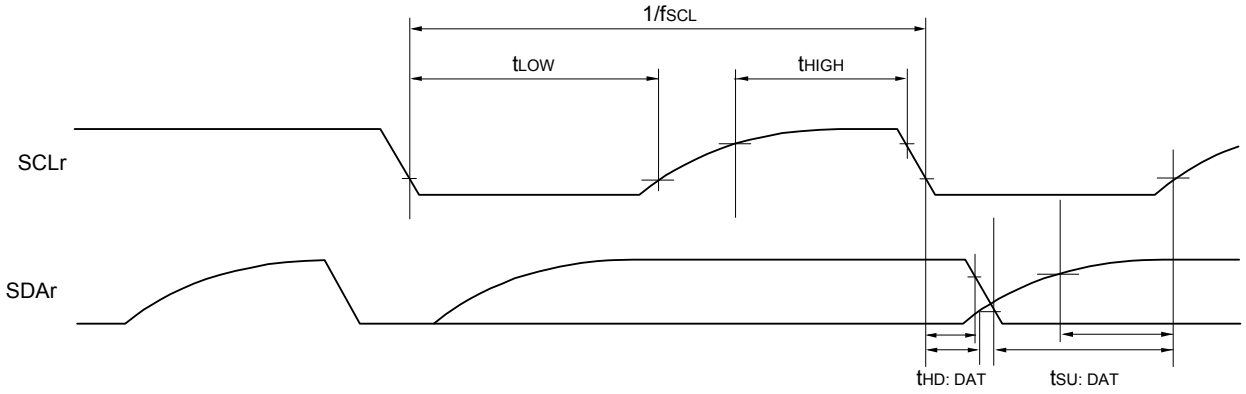
Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM, POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 02, 10, 12)

2.5.2 Serial interface IICA

(1) I²C standard mode

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Standard mode: f_{CLK} ≥ 1 MHz	2.7 V ≤ V_{DD} ≤ 3.6 V	0	100	0	100	0	100	kHz
			1.8 V ≤ V_{DD} ≤ 3.6 V	—	—	0	100	0	100	kHz
			1.6 V ≤ V_{DD} ≤ 3.6 V	—	—	—	—	0	100	kHz
Setup time of restart condition	$t_{SU: STA}$	2.7 V ≤ V_{DD} ≤ 3.6 V		4.7		4.7		4.7		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		4.7		4.7		µs
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		4.7		µs
Hold time Note 1	$t_{HD: STA}$	2.7 V ≤ V_{DD} ≤ 3.6 V		4.0		4.0		4.0		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		4.0		4.0		µs
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		4.0		µs
Hold time when SCLA0 = “L”	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V		4.7		4.7		4.7		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		4.7		4.7		µs
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		4.7		µs
Hold time when SCLA0 = “H”	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V		4.0		4.0		4.0		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		4.0		4.0		µs
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		4.0		µs
Data setup time (reception)	$t_{SU: DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V		250		250		250		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		250		250		ns
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		250		ns
Data hold time (transmission) Note 2	$t_{HD: DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V		0	3.45	0	3.45	0	3.45	µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		—	—	0	3.45	0	3.45	µs
		1.6 V ≤ V_{DD} ≤ 3.6 V		—	—	—	—	0	3.45	µs
Setup time of stop condition	$t_{SU: STO}$	2.7 V ≤ V_{DD} ≤ 3.6 V		4.0		4.0		4.0		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		4.0		4.0		µs
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		4.0		µs
Bus-free time	t_{BUF}	2.7 V ≤ V_{DD} ≤ 3.6 V		4.7		4.7		4.7		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		—		4.7		4.7		µs
		1.6 V ≤ V_{DD} ≤ 3.6 V		—		—		4.7		µs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.
Standard mode: C_b = 400 pF, R_b = 2.7 kΩ

(2) I^2C fast mode

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: f_{CLK} ≥ 3.5 MHz	2.7 V ≤ V_{DD} ≤ 3.6 V	0	400	0	400	0	400	kHz
			1.8 V ≤ V_{DD} ≤ 3.6 V	0	400	0	400	0	400	kHz
Setup time of restart condition	$t_{SU: STA}$	2.7 V ≤ V_{DD} ≤ 3.6 V		0.6		0.6		0.6		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		0.6		0.6		0.6		µs
Hold time Note 1	$t_{HD: STA}$	2.7 V ≤ V_{DD} ≤ 3.6 V		0.6		0.6		0.6		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		0.6		0.6		0.6		µs
Hold time when SCLA0 = “L”	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V		1.3		1.3		1.3		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		1.3		1.3		1.3		µs
Hold time when SCLA0 = “H”	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V		0.6		0.6		0.6		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		0.6		0.6		0.6		µs
Data setup time (reception)	$t_{SU: DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V		100		100		100		ns
		1.8 V ≤ V_{DD} ≤ 3.6 V		100		100		100		ns
Data hold time (transmission) Note 2	$t_{HD: DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V		0	0.9	0	0.9	0	0.9	µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		0	0.9	0	0.9	0	0.9	µs
Setup time of stop condition	$t_{SU: STO}$	2.7 V ≤ V_{DD} ≤ 3.6 V		0.6		0.6		0.6		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		0.6		0.6		0.6		µs
Bus-free time	t_{BUF}	2.7 V ≤ V_{DD} ≤ 3.6 V		1.3		1.3		1.3		µs
		1.8 V ≤ V_{DD} ≤ 3.6 V		1.3		1.3		1.3		µs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of $t_{HD: DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.
Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

(3) I^2C fast mode plus

(T_A = -40 to +85 °C, 2.7 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

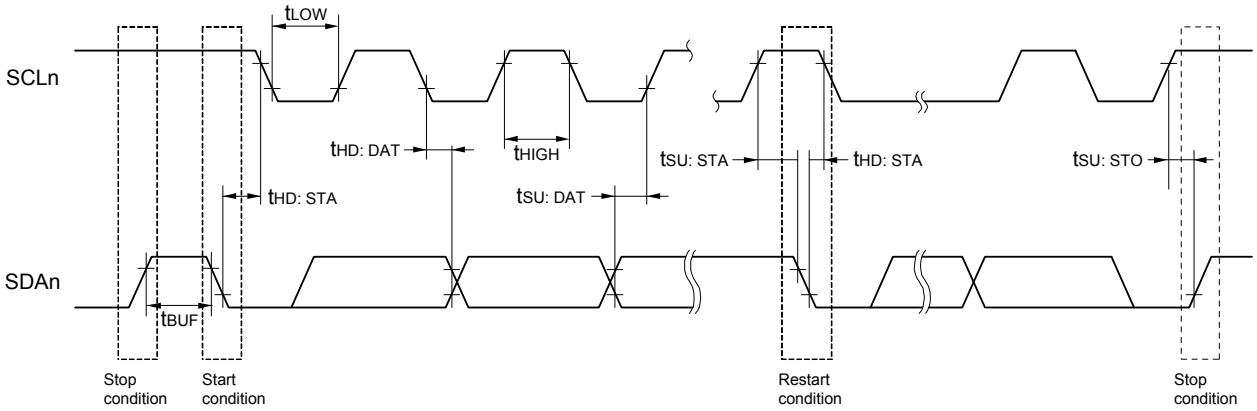
Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode plus: f_{CLK} ≥ 10 MHz	2.7 V ≤ V_{DD} ≤ 3.6 V	0	1000	—		—		kHz
Setup time of restart condition	$t_{SU: STA}$	2.7 V ≤ V_{DD} ≤ 3.6 V		0.26		—		—		µs
Hold time Note 1	$t_{HD: STA}$	2.7 V ≤ V_{DD} ≤ 3.6 V		0.26		—		—		µs
Hold time when SCLA0 = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V		0.5		—		—		µs
Hold time when SCLA0 = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V		0.26		—		—		µs
Data setup time (reception)	$t_{SU: DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V		50		—		—		ns
Data hold time (transmission) Note 2	$t_{HD: DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V		0	0.45	—		—		µs
Setup time of stop condition	$t_{SU: STO}$	2.7 V ≤ V_{DD} ≤ 3.6 V		0.26		—		—		µs
Bus-free time	t_{BUF}	2.7 V ≤ V_{DD} ≤ 3.6 V		0.5		—		—		µs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of $t_{HD: DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.
Fast mode plus: C_b = 120 pF, R_b = 1.1 kΩ

IICA serial transfer timing



2.5.3 USB

(1) Electrical specifications

(T_A = -40 to +85 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, HS (High-speed main) mode only)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
U_{REGC}	U_{REGC} output voltage characteristic	U_{REGC}	UV_{BUS} = 4.0 to 5.5 V, PXXCON = VDDUSBE = 1	3.0	3.3	3.6	V
UV_{BUS}	UV_{BUS} input voltage characteristic	UV_{BUS}	Function	4.35 (4.02 Note)	5.00	5.25	V

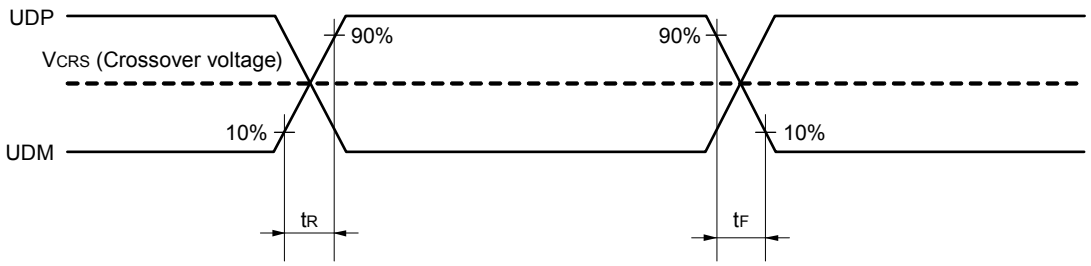
Note Value of instantaneous voltage

(T_A = -40 to +85 °C, 4.35 V ≤ UV_{BUS} ≤ 5.25 V, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, HS (High-speed main) mode only)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input characteristic (FS/LS receiver)	Input voltage		V_{IH}		2.0			V
			V_{IL}				0.8	V
	Difference input sensitivity		V_{DI}	| UDP voltage - UDM voltage |	0.2			V
	Difference common mode range		V_{CM}		0.8		2.5	V
Output characteristic (FS driver)	Output voltage		V_{OH}	I_{OH} = -200 μA	2.8		3.6	V
			V_{OL}	I_{OL} = 2 mA	0		0.3	V
	Transition time	Rising	t_{FR}	Rising: From 10% to 90% of amplitude, Falling: From 90% to 10% of amplitude, CL = 50 pF	4		20	ns
		Falling	t_{FF}		4		20	ns
	Matching (TFR/TFF)		V_{FRFM}		90		111.1	%
	Crossover voltage		V_{FCRS}		1.3		2.0	V
	Output Impedance		Z_{DRV}	U_{REGC} voltage = 3.3 V, Pin voltage = 1.65 V	28		44	Ω
Output characteristic (LS driver)	Output voltage		V_{OH}		2.8		3.6	V
			V_{OL}		0		0.3	V
	Transition time	Rising	t_{LR}	Rising: From 10% to 90% of amplitude, Falling: From 90% to 10% of amplitude, CL = 250 pF to 750 pF The UDP and UDM pins are individually pulled down via 15 kΩ	75		300	ns
		Falling	t_{LF}		75		300	ns
	Matching (TFR/TFF) Note		V_{LTFM}		80		125	%
	Crossover voltage Note		V_{LCRS}		1.3		2.0	V
Pull-up, Pull-down	Pull-down resistor		R_{PD}		14.25		24.80	kΩ
	Pull-up resistor	Idle	R_{PUI}		0.9		1.575	kΩ
		Reception	R_{PUA}		1.425		3.09	kΩ
UV_{BUS}	UV_{BUS} pull-down resistor		R_{VBUS}	UV_{BUS} voltage = 5.5 V		1000		kΩ
	UV_{BUS} input voltage		V_{IH}		3.20			V
			V_{IL}				0.8	V

Note Excludes the first signal transition from the idle state.

Timing of UDP and UDM



(2) BC standard

(TA = -40 to +85 °C, 4.35 V ≤ UVBUS ≤ 5.25 V, 2.4 V ≤ VDD ≤ 3.6 V, VSS = 0 V, HS (High-speed main) mode only)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB standard BC1.2	UDP sink current	IDP_SINK		25	100	175	μA
	UDM sink current	IDM_SINK		25	100	175	μA
	DCD source current	IDP_SRC		7	10	13	μA
	Data detection voltage	VDAT_REF		0.25	0.325	0.4	V
	UDP source voltage	VDP_SRC	Output current 250 μA	0.5	0.6	0.7	V
	UDM source voltage	VDM_SRC	Output current 250 μA	0.5	0.6	0.7	V

(3) BC option standard

(T_A = -40 to +85 °C, 4.35 V ≤ UV_{BUS} ≤ 5.25 V, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, HS (High-speed main) mode only)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDP/UDM input reference voltage (UV_{BUS} divider ratio) (Function)	VDSELi [3: 0] (i = 0, 1)	0000	V_{DDET0}		27	32	37	%UVBUS
		0001	V_{DDET1}		29	34	39	%UVBUS
		0010	V_{DDET2}		32	37	42	%UVBUS
		0011	V_{DDET3}		35	40	45	%UVBUS
		0100	V_{DDET4}		38	43	48	%UVBUS
		0101	V_{DDET5}		41	46	51	%UVBUS
		0110	V_{DDET6}		44	49	54	%UVBUS
		0111	V_{DDET7}		47	52	57	%UVBUS
		1000	V_{DDET8}		51	56	61	%UVBUS
		1001	V_{DDET9}		55	60	65	%UVBUS
		1010	V_{DDET10}		59	64	69	%UVBUS
		1011	V_{DDET11}		63	68	73	%UVBUS
		1100	V_{DDET12}		67	72	73	%UVBUS
		1101	V_{DDET13}		71	76	81	%UVBUS
		1110	V_{DDET14}		75	80	85	%UVBUS
		1111	V_{DDET15}		79	84	89	%UVBUS

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage / Input Channel	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = AV_{DD} Reference voltage (-) = AV_{SS}	Reference voltage (+) = Internal reference voltage Reference voltage (-) = AV_{SS}
High-accuracy channel; ANI0 to ANI6 (input buffer power supply: AV_{DD})	Refer to **2.6.1 (1)**. Refer to **2.6.1 (2)**.	Refer to **2.6.1 (3)**.	Refer to **2.6.1 (6)**.
Standard channel; ANI16 to ANI21 (input buffer power supply: V_{DD})	Refer to **2.6.1 (4)**.	Refer to **2.6.1 (5)**.	
Internal reference voltage, Temperature sensor output voltage	Refer to **2.6.1 (4)**.	Refer to **2.6.1 (5)**.	—

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target for conversion: ANI2 to ANI6

(T_A = -40 to +85 °C, 2.7 V ≤ AV_{REFP} ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, reference voltage (+) = AV_{REFP}, reference voltage (-) = AV_{REFM} = 0 V, HALT mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES				12	bit
Overall error Notes 1, 2, 3	AINL	12-bit resolution		±1.7	±3.3	LSB
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	3.375			μs
Zero-scale error Notes 1, 2, 3	E_{ZS}	12-bit resolution		±1.3	±3.2	LSB
Full-scale error Notes 1, 2, 3	E_{FS}	12-bit resolution		±0.7	±2.9	LSB
Integral linearity error Notes 1, 2, 3	ILE	12-bit resolution		±1.0	±1.4	LSB
Differential linearity error Notes 1, 2, 3	DLE	12-bit resolution		±0.9	±1.2	LSB
Analog input voltage	V_{AIN}		0		AV_{REFP}	V

Note 1. TYP. Value is the average value at AV_{DD} = AV_{REFP} = 3 V and T_A = 25 °C. MAX. value is the average value ±3σ at normalized distribution.

Note 2. These values are the results of characteristic evaluation and are not checked for shipment.

Note 3. Excludes quantization error (±1/2 LSB).

Caution 1. Route the wiring so that noise will not be superimposed on each power line and ground line, and insert a capacitor to suppress noise.
In addition, separate the reference voltage line of AV_{REFP} from the other power lines to keep it free from the influences of noise.

Caution 2. During A/D conversion, keep a pulse, such as a digital signal, that abruptly changes its level from being input to or output from the pins adjacent to the converter pins and P150 to P156.

(2) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), conversion target: ANI2 to ANI6

(T_A = -40 to +85 °C, 1.6 V ≤ AV_{REFP} ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		12	bit
			1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.5	
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	3.375			µs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	6.75			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	13.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	2.5625			
			1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	5.125			
			1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	10.25			
Zero-scale error Note 3	E_{ZS}	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	
Full-scale error Note 3	E_{FS}	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.0	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.0	
Analog input voltage	V_{AIN}			0		AV_{REFP}	V

Note 1. Cannot be used for lower 2 bit of ADCR register

Note 2. Cannot be used for lower 4 bit of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(3) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AV_{SS} (ADREFM = 0), conversion target: ANI0 to ANI6

(T_A = -40 to +85 °C, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (-) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
			1.8 V ≤ AV_{DD} ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AV_{DD} ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±7.5	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±3.0	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	3.375			µs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AV_{DD} ≤ 3.6 V	6.75			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AV_{DD} ≤ 3.6 V	13.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	2.5625			
			1.8 V ≤ AV_{DD} ≤ 3.6 V	5.125			
			1.6 V ≤ AV_{DD} ≤ 3.6 V	10.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±1.5	
Analog input voltage	VAIN	ANI0 to ANI6		0		AV_{DD}	V

Note 1. Cannot be used for lower 2 bit of ADCR register

Note 2. Cannot be used for lower 4 bit of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(4) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, 1.6 V ≤ AV_{REFP} ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		12	bit
			1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±7.0	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±3.0	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	4.125			µs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	57.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	3.3125			
			1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	7.875			
			1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	54.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.5	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±5.0	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±5.0	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.5	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±3.0	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
		10-bit resolution	1.8 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	
		8-bit resolution	1.6 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	
Analog input voltage	VAIN			0		AV_{REFP}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{BGR} Note 4			
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{TMP25} Note 4			

Note 1. Cannot be used for lower 2 bits of ADCR register

Note 2. Cannot be used for lower 4 bits of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Note 4. Refer to **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(5) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AV_{SS} (ADREFM = 0), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, 1.6 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (-) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
			1.8 V ≤ AV_{DD} ≤ 3.6 V	8		10 Note 1	
			1.6 V ≤ AV_{DD} ≤ 3.6 V	8 Note 2			
Overall error Note 3	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.5	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±6.0	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±3.5	
Conversion time	tCONV	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	4.125			µs
		ADTYP = 0, 10-bit resolution Note 1	1.8 V ≤ AV_{DD} ≤ 3.6 V	9.5			
		ADTYP = 0, 8-bit resolution Note 2	1.6 V ≤ AV_{DD} ≤ 3.6 V	57.5			
		ADTYP = 1, 8-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	3.3125			
			1.8 V ≤ AV_{DD} ≤ 3.6 V	7.875			
			1.6 V ≤ AV_{DD} ≤ 3.6 V	54.25			
Zero-scale error Note 3	EZS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±3.0	
Full-scale error Note 3	EFS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±5.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±3.0	
Integral linearity error Note 3	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.5	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±1.5	
Differential linearity error Note 3	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.5	LSB
		10-bit resolution	1.8 V ≤ AV_{DD} ≤ 3.6 V			±2.5	
		8-bit resolution	1.6 V ≤ AV_{DD} ≤ 3.6 V			±2.0	
Analog input voltage	VAIN			0		AV_{DD}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{BGR} Note 4			
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{TMP25} Note 4			

Note 1. Cannot be used for lower 2 bits of ADCR register

Note 2. Cannot be used for lower 4 bits of ADCR register

Note 3. Excludes quantization error (±1/2 LSB).

Note 4. Refer to **2.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(6) When reference voltage (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI6, ANI16 to ANI21

(T_A = -40 to +85 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, 1.6 V ≤ V_{DD}, 1.6 V ≤ AV_{DD} = V_{DD}, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = internal reference voltage, Reference voltage (-) = AV_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tCONV	8-bit resolution	16			μs
Zero-scale error Note	EZS	8-bit resolution			±4.0	LSB
Integral linearity error Note	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note	DLE	8-bit resolution			±2.5	LSB
Reference voltage (+)	$AV_{REF(+)}$	= Internal reference voltage (V_{BGR})	1.38	1.45	1.5	V
Analog input voltage	VAIN		0		V_{BGR}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

2.6.2 Temperature sensor, internal reference voltage output characteristics

(T_A = -40 to +85 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V (HS (high-speed main) mode))

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tAMP		10			μs

2.6.3 D/A converter characteristics

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	1.8 V ≤ V_{DD} ≤ 3.6 V			±2.5	LSB
		Rload = 8 MΩ	1.8 V ≤ V_{DD} ≤ 3.6 V			±2.5	LSB
Settling time	tSET	Cload = 20 pF	2.7 V ≤ V_{DD} ≤ 3.6 V			3	μs
			1.6 V ≤ V_{DD} < 2.7 V			6	μs

2.6.4 Comparator

(T_A = -40 to +85 °C, 1.6 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		V_{DD} - 1.4	V
	Ivcmp			-0.3		V_{DD} + 0.3	V
Output delay	td	V_{DD} = 3.0 V Input slew rate > 50 mV/µs	High-speed comparator mode, standard mode			1.2	µs
			High-speed comparator mode, window mode			2.0	µs
			Low-speed comparator mode, standard mode		3	5.0	µs
High-electric-potential judgment voltage	VTW+	High-speed comparator mode, window mode			0.76 V_{DD}		V
Low-electric-potential judgment voltage	VTW-	High-speed comparator mode, window mode			0.24 V_{DD}		V
Operation stabilization wait time	t_{CMP}			100			µs
Internal reference voltage Note	V_{BGR}			1.38	1.45	1.50	V

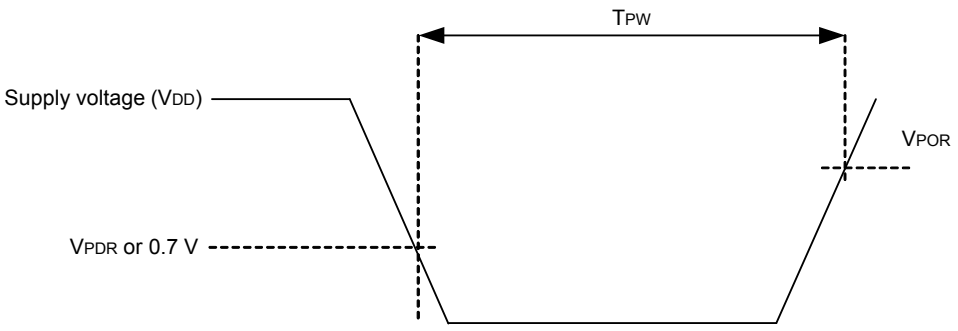
Note Not usable in LS (low-speed main) mode, LV (low-voltage main) mode, sub-clock operation, or STOP mode.

2.6.5 POR circuit characteristics

(T_A = -40 to +85 °C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.47	1.51	1.55	V
	V_{PDR}	Power supply fall time Note	1.46	1.50	1.54	V
Minimum pulse width	T_{PW}		300			µs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.6 LVD circuit characteristics

(T_A = -40 to +85 °C, $V_{PDR} \leq V_{DD} \leq 3.6$ V $\leq V_{SS}$ = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD2}	Power supply rise time	3.07	3.13	3.19	V
			Power supply fall time	3.00	3.06	3.12	V
		V_{LVD3}	Power supply rise time	2.96	3.02	3.08	V
			Power supply fall time	2.90	2.96	3.02	V
		V_{LVD4}	Power supply rise time	2.86	2.92	2.97	V
			Power supply fall time	2.80	2.86	2.91	V
		V_{LVD5}	Power supply rise time	2.76	2.81	2.87	V
			Power supply fall time	2.70	2.75	2.81	V
		V_{LVD6}	Power supply rise time	2.66	2.71	2.76	V
			Power supply fall time	2.60	2.65	2.70	V
		V_{LVD7}	Power supply rise time	2.56	2.61	2.66	V
			Power supply fall time	2.50	2.55	2.60	V
		V_{LVD8}	Power supply rise time	2.45	2.50	2.55	V
			Power supply fall time	2.40	2.45	2.50	V
		V_{LVD9}	Power supply rise time	2.05	2.09	2.13	V
			Power supply fall time	2.00	2.04	2.08	V
		V_{LVD10}	Power supply rise time	1.94	1.98	2.02	V
			Power supply fall time	1.90	1.94	1.98	V
		V_{LVD11}	Power supply rise time	1.84	1.88	1.91	V
			Power supply fall time	1.80	1.84	1.87	V
		V_{LVD12}	Power supply rise time	1.74	1.77	1.81	V
			Power supply fall time	1.70	1.73	1.77	V
		V_{LVD13}	Power supply rise time	1.64	1.67	1.70	V
			Power supply fall time	1.60	1.63	1.66	V
Minimum pulse width		t_{LW}		300			µs
Detection delay time						300	µs

Caution Set the detection voltage (V_{LVD}) to be within the operating voltage range. The operating voltage range depends on the setting of the user option byte (000C2H/010C2H). The following shows the operating voltage range.

HS (high-speed main) mode: V_{DD} = 2.7 to 3.6 V at 1 MHz to 24 MHz
V_{DD} = 2.4 to 3.6 V at 1 MHz to 16 MHz
LS (low-speed main) mode: V_{DD} = 1.8 to 3.6 V at 1 MHz to 8 MHz
LV (low-voltage main) mode: V_{DD} = 1.6 to 3.6 V at 1 MHz to 4 MHz

LVD Detection Voltage of Interrupt & Reset Mode

(T_A = -40 to +85 °C, $V_{PDR} \le V_{DD} \le$ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDA0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 0, 0, falling reset voltage: 1.6 V			1.60	1.63	1.66	V
	V_{LVDA1}	LVIS0, LVIS1 = 1, 0		Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	V_{LVDA2}	LVIS0, LVIS1 = 0, 1		Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	V_{LVDA3}	LVIS0, LVIS1 = 0, 0		Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDB0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 0, 1, falling reset voltage: 1.8 V			1.80	1.84	1.87	V
	V_{LVDB1}	LVIS0, LVIS1 = 1, 0		Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	V_{LVDB2}	LVIS0, LVIS1 = 0, 1		Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	V_{LVDB3}	LVIS0, LVIS1 = 0, 0		Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	V_{LVDC0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 0, falling reset voltage: 2.4 V			2.40	2.45	2.50	V
	V_{LVDC1}	LVIS0, LVIS1 = 1, 0		Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	V_{LVDC2}	LVIS0, LVIS1 = 0, 1		Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	V_{LVDD0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 1, falling reset voltage: 2.7 V			2.70	2.75	2.81	V
	V_{LVDD1}	LVIS0, LVIS1 = 1, 0		Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVDD2}	LVIS0, LVIS1 = 0, 1		Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V

2.7 Power supply voltage rising slope characteristics

(T_A = -40 to +85 °C, V_{SS} = 0 V)

Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SV_{DD}			54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.8 LCD Characteristics

2.8.1 Resistance division method

(1) Static display mode

(T_A = -40 to +85 °C, V_{L4} (MIN.) ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.0		V_{DD}	V

(2) 1/2 bias method, 1/4 bias method

(T_A = -40 to +85 °C, V_{L4} (MIN.) ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.7		V_{DD}	V

(3) 1/3 bias method

(T_A = -40 to +85 °C, V_{L4} (MIN.) ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.5		V_{DD}	V

2.8.2 Internal voltage boosting method

(1) 1/3 bias method

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V_{L1}	C1 to C4 Note 1 = 0.47 μF Note 2	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	V_{L2}	C1 to C4 Note 1 = 0.47 μF		2 V_{L1} - 0.1	2 V_{L1}	2 V_{L1}	V
Tripler output voltage	V_{L3}	C1 to C4 Note 1 = 0.47 μF		3 V_{L1} - 0.15	3 V_{L1}	3 V_{L1}	V
Reference voltage setup time Note 2	t_{VWAIT1}			5			ms
Voltage boost wait time Note 3	t_{VWAIT2}	C1 to C4 Note 1 = 0.47μF		500			ms

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L3} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

(2) 1/4 bias method

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V_{L1}	C1 to C4 Note 1 = 0.47 μF Note 2	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	V_{L2}	C1 to C4 Note 1 = 0.47 μF		2 V_{L1} - 0.08	2 V_{L1}	2 V_{L1}	V
Tripler output voltage	V_{L3}	C1 to C4 Note 1 = 0.47 μF		3 V_{L1} - 0.12	3 V_{L1}	3 V_{L1}	V
Quadruply output voltage	V_{L4}	C1 to C5 Note 1 = 0.47 μF		4 V_{L1} - 0.16	4 V_{L1}	4 V_{L1}	V
Reference voltage setup time Note 2	t_{VWAIT1}			5			ms
Voltage boost wait time Note 3	t_{VWAIT2}	C1 to C5 Note 1 = 0.47μF		500			ms

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L3} and GND
C5: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

2.8.3 Capacitor split method

(1) 1/3 bias method

(T_A = -40 to +85 °C, 2.2 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V_{L4} voltage	V_{L4}	C1 to C4 = 0.47 μF Note 2		V_{DD}		V
V_{L2} voltage	V_{L2}	C1 to C4 = 0.47 μF Note 2	2/3 V_{L4} - 0.1	2/3 V_{L4}	2/3 V_{L4} + 0.1	V
V_{L1} voltage	V_{L1}	C1 to C4 = 0.47 μF Note 2	1/3 V_{L4} - 0.1	1/3 V_{L4}	1/3 V_{L4} + 0.1	V
Capacitor split wait time Note 1	t_{VWAIT}		100			ms

Note 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

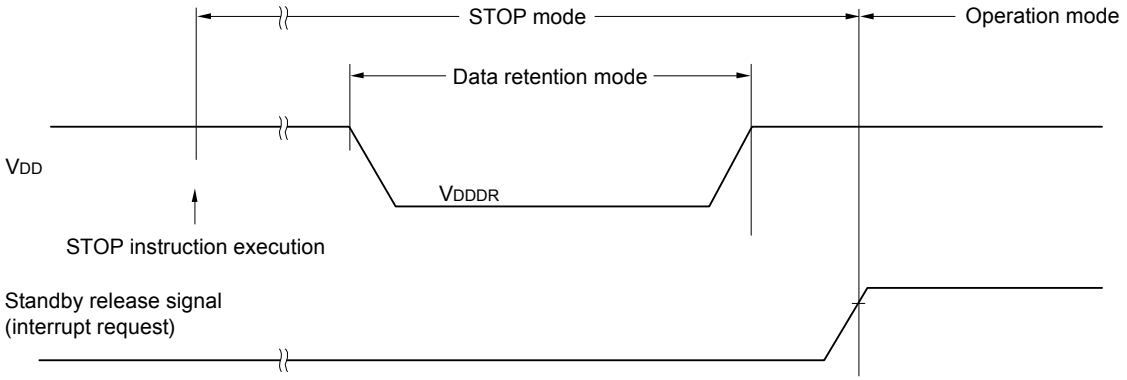
Note 2. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

2.9 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

(TA = -40 to +85 °C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 Note		3.6	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



2.10 Flash Memory Programming Characteristics

(TA = -40 to +85 °C, 1.8 V ≤ VDD ≤ 3.6 V, Vss = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fCLK	2.4 V ≤ VDD ≤ 3.6 V		1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years	TA = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year	TA = 25°C		1,000,000		
		Retained for 5 years	TA = 85°C	100,000			
		Retained for 20 years	TA = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.11 Dedicated Flash Memory Programmer Communication (UART)

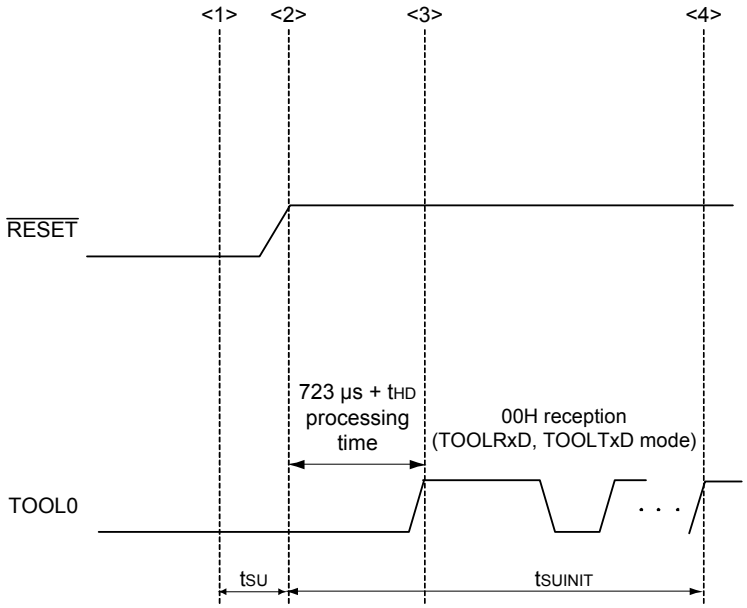
(TA = -40 to +85 °C, 1.8 V ≤ VDD ≤ 3.6 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.12 Timing Specs for Switching Modes

(T_A = -40 to +85 °C, 1.8 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	t_{SUINIT}	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	t_{SU}	POR and LVD reset must end before the external reset ends.	10			μs
Time to hold the TOOL0 pin at the low level after an external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must end before the external reset ends.	1			ms



<1> The low level is input to the TOOL0 pin.
<2> The external reset ends (POR and LVD reset must end before the external reset ends.).
<3> The TOOL0 pin is set to the high level.
<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.
t_{SU}: How long from when the TOOL0 pin is placed at the low level until a external reset ends
t_{HD}: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

3. ELECTRICAL SPECIFICATIONS (G: TA = -40 to +105 °C)

This chapter describes the electrical specifications for the products “G: Industrial applications (TA = -40 to +105 °C)”.

Caution 1. The RL78 microcontroller has an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. The pins mounted depend on the product. Refer to 1.3.1 80-pin products (with USB) to 1.3.4 100-pin products (without USB).

Caution 3. Please contact Renesas Electronics sales office for derating of operation under TA = +85 ºC to +105 ºC. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When the RL78 microcontroller is used in the range of TA = -40 to +85 °C, see **2. ELECTRICAL SPECIFICATIONS (A: TA = -40 to +85 °C)**.

The following functions differ between the products “G: Industrial applications (TA = -40 to +105 °C)” and the products “A: Consumer applications and G: Industrial applications (when used in the range of TA = -40 to +85 °C)”.

Parameter	A: Consumer applications	G: Industrial applications
Operating ambient temperature	TA = -40 to +85 °C	TA = -40 to +105 °C
Operating mode Operating voltage range	HS (high-speed main) mode: 2.7 V ≤ VDD ≤ 3.6 V@1 MHz to 24 MHz 2.4 V ≤ VDD ≤ 3.6 V@1 MHz to 16 MHz LS (low-speed main) mode: 1.8 V ≤ VDD ≤ 3.6 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V ≤ VDD ≤ 3.6 V@1 MHz to 4 MHz	HS (high-speed main) mode only: 2.7 V ≤ VDD ≤ 3.6 V@1 MHz to 24 MHz 2.4 V ≤ VDD ≤ 3.6 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	1.8 V ≤ VDD ≤ 3.6 V: ±1.0% @ TA = -20 to +85 °C ±1.5% @ TA = -40 to -20 °C 1.6 V ≤ VDD ≤ 1.8 V: ±5.0% @ TA = -20 to +85 °C ±5.5% @ TA = -40 to -20 °C	2.4 V ≤ VDD ≤ 3.6 V: ±2.0% @ TA = +85 to +105 °C ±1.0% @ TA = -20 to +85 °C ±1.5% @ TA = -40 to -20 °C
Serial array unit	UART CSI: fCLK/4 Simplified I2C communication	UART CSI: fCLK/4 Simplified I2C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	• Rise detection voltage: 1.67 V to 3.13 V (12 levels) • Fall detection voltage: 1.63 V to 3.06 V (12 levels)	• Rise detection voltage: 2.61 V to 3.13 V (6 levels) • Fall detection voltage: 2.55 V to 3.06 V (6 levels)

Remark The electrical characteristics of the products G: Industrial applications (TA = -40 to +105 °C) are different from those of the products “A: Consumer applications”. For details, refer to **3.1** to **3.12**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/3)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V_{DD}		-0.5 to + 6.5	V
	UV_{BUS}		-0.5 to + 6.5	V
	AV_{DD}	$AV_{DD} \leq V_{DD}$	-0.5 to + 4.6	V
REGC pin input voltage	V_{IREGC}	REGC	-0.3 to + 2.8 and -0.3 to V_{DD} + 0.3 Note 1	V
U_{REGC} pin input voltage	V_{IUREGC}	U_{REGC}	-0.3 to UV_{BUS} + 0.3 Note 2	V
Input voltage	V_{I1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, EXCLK, EXCLKS, $\overline{\text{RESET}}$	-0.3 to V_{DD} + 0.3 Note 3	V
	V_{I2}	P60, P61 (N-ch open-drain)	-0.3 to + 6.5	V
	V_{I3}	UDP, UDM	-0.3 to + 6.5	V
	V_{I4}	P150 to P156	-0.3 to AV_{DD} + 0.3 Note 4	V
Output voltage	V_{O1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143	-0.3 to V_{DD} + 0.3 Note 3	V
	V_{O2}	P130, P150 to P156	-0.3 to AV_{DD} + 0.3 Note 3	V
	V_{O3}	UDP, UDM	-0.3 to + 3.8	V
Analog input voltage	V_{AI1}	ANI16 to ANI21	-0.3 to V_{DD} + 0.3 and $AV_{REF(+)}$ + 0.3 Notes 3, 5	V
	V_{AI2}	ANI0 to ANI6	-0.3 to AV_{DD} + 0.3 and $AV_{REF(+)}$ + 0.3 Notes 3, 5	V

Note 1. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Connect the U_{REGC} pin to Vss via a capacitor (0.33 μF). This value regulates the absolute maximum rating of the U_{REGC} pin. Do not use this pin with voltage applied to it.

Note 3. Must be 6.5 V or lower.

Note 4. Must be 4.6 V or lower.

Note 5. Do not exceed $AV_{REF(+)}$ + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. $AV_{REF(+)}$: + side reference voltage of the A/D converter.

Remark 3. V_{SS}: Reference voltage

Absolute Maximum Ratings (T_A = 25°C) **(2/3)**

Parameter	Symbols	Conditions		Ratings	Unit
LCD voltage	V_{LI1}	V_{L1} input voltage Note 1		-0.3 to +2.8	V
	V_{LI2}	V_{L2} input voltage Note 1		-0.3 to +6.5	V
	V_{LI3}	V_{L3} input voltage Note 1		-0.3 to +6.5	V
	V_{LI4}	V_{L4} input voltage Note 1		-0.3 to +6.5	V
	V_{LI5}	CAPL, CAPH input voltage Note 1		-0.3 to +6.5	V
	V_{LO1}	V_{L1} output voltage		-0.3 to +2.8	V
	V_{LO2}	V_{L2} output voltage		-0.3 to +6.5	V
	V_{LO3}	V_{L3} output voltage		-0.3 to +6.5	V
	V_{LO4}	V_{L4} output voltage		-0.3 to +6.5	V
	V_{LO5}	CAPL, CAPH output voltage		-0.3 to +6.5	V
	V_{LO6}	COM0 to COM7 SEG0 to SEG55 output voltage	External resistance division method	-0.3 to V_{DD} + 0.3 Note 2	V
			Capacitor split method	-0.3 to V_{DD} + 0.3 Note 2	V
			Internal voltage boosting method	-0.3 to V_{LI4} + 0.3 Note 2	V

Note 1. This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method or capacitance split method, connect these pins to V_{SS} via a capacitor (0.47 ± 30%) and connect a capacitor (0.47 ± 30%) between the CAPL and CAPH pins.

Note 2. Must be 6.5 V or lower.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Absolute Maximum Ratings (T_A = 25 °C) (3/3)

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	-40	mA
		Total of all pins -170 mA	P40 to P46	-70	mA
			P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	-100	mA
	I_{OH2}	Per pin	P130, P150 to P156	-0.1	mA
		Total of all pins		-0.8	mA
	I_{OH3}	Per pin	UDP, UDM	-3	mA
Output current, low	I_{OL1}	Per pin	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143	40	mA
		Total of all pins 170 mA	P40 to P46	70	mA
			P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	100	mA
	I_{OL2}	Per pin	P130, P150 to P156	0.4	mA
		Total of all pins		3.2	mA
	I_{OL3}	Per pin	UDP, UDM	3	mA
Operating ambient temperature	T_A	In normal operation mode		-40 to +105	°C
		In flash memory programming mode		-40 to +85	
Storage temperature	T_{stg}			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.2 Oscillator Characteristics

3.2.1 X1 and XT1 oscillator characteristics

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X) Note	Ceramic resonator/crystal resonator	2.7 V ≤ V_{DD} ≤ 3.6 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		16.0	
XT1 clock oscillation frequency (f_{XT}) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution **Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.**

Remark When using the X1 and XT1 oscillator, refer to **5.4 System Clock Oscillator in the RL78/L1C User's Manual Hardware**.

3.2.2 On-chip oscillator characteristics

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f_{HOCO}		1		24	MHz
High-speed on-chip oscillator clock frequency accuracy		-20 to +85 °C	-1.0		+1.0	%
		-40 to -20 °C	-1.5		+1.5	%
		+85 to +105 °C	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	f_{IL}			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to **AC Characteristics** for instruction execution time.

3.2.3 PLL oscillator characteristics

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
PLL input frequency Note	f_{PLLIN}	High-speed system clock	6.00		16.00	MHz
PLL output frequency Note	f_{PLL}			48.00		MHz

Note Indicates only oscillator characteristics. Refer to **AC Characteristics** for instruction execution time.

3.3 DC Characteristics

3.3.1 Pin characteristics

(T_A = -40 to +105 °C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143				-10.0 Note 2	mA
		Total of P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143 (When duty = 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			-15.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			-7.0	mA
	I_{OH2}	Per pin for P130, P150 to P156				-0.1 Note 2	mA
		Total of all pins	2.4 V ≤ V_{DD} ≤ 3.6 V			-0.8	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

Note 2. However, do not exceed the total current value.

Note 3. Specification under conditions where the duty factor is 70%.
The output current value that has changed the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 50% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(50 × 0.01) = -14.0 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +105 °C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	I_{OL1}	Per pin for P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143				20.0 Note 2	mA
		Per pin for P60 and P61				15.0 Note 2	mA
		Total of P40 to P46 (When duty = 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			15.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			9.0	mA
		Total of P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P140 to P143 (When duty = 70% Note 3)	2.7 V ≤ V_{DD} ≤ 3.6 V			35.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			20.0	mA
		Total of all pins (When duty = 70% Note 3)				50.0	mA
	I_{OL2}	Per pin for P130, P150 to P156				0.4 Note 2	mA
		Total of all pins	2.4 V ≤ V_{DD} ≤ 3.6 V			3.2	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

Note 2. However, do not exceed the total current value.

Note 3. Specification under conditions where the duty factor is 70%.
The output current value that has changed the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 50% and I_{OL} = 10.0 mA
Total output current of pins = (10.0 × 0.7)/(50 × 0.01) = 14.0 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +105 °C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0.8 V_{DD}		V_{DD}	V
	V_{IH2}	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	2.0		V_{DD}	V
			TTL input buffer 2.4 V ≤ V_{DD} < 3.3 V	1.50		V_{DD}	V
	V_{IH3}	P150 to P156		0.7 AV_{DD}		AV_{DD}	V
	V_{IH4}	P60, P61		0.7 V_{DD}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0.8 V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	Normal input buffer	0		0.2 V_{DD}	V
	V_{IL2}	P00, P01, P10, P11, P24, P25, P33, P34, P43, P44	TTL input buffer 3.3 V ≤ V_{DD} ≤ 3.6 V	0		0.5	V
			TTL input buffer 2.4 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P150 to P156		0		0.3 AV_{DD}	V
	V_{IL4}	P60, P61		0		0.3 V_{DD}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		0.2 V_{DD}	V

Caution The maximum value of V_{IH} of pins P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 is V_{DD}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +105 °C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH1} = -2.0 mA	V_{DD} - 0.6			V
			2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OH1} = -1.5 mA	V_{DD} - 0.5			V
	V_{OH2}	P130, P150 to P156	2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OH2} = -100 μA	AV_{DD} - 0.5			V
Output voltage, low	V_{OL1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P70 to P77, P80 to P83, P125 to P127, P140 to P143	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL1} = 3.0 mA			0.6	V
			2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OL1} = 1.5 mA			0.4	V
			2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OL1} = 0.6 mA			0.4	V
	V_{OL2}	P130, P150 to P156	2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60, P61	2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL3} = 3.0 mA			0.4	V
			2.4 V ≤ V_{DD} ≤ 3.6 V, I_{OL3} = 2.0 mA			0.4	V

Caution P00 to P02, P10 to P12, P24 to P26, P33 to P35, and P42 to P44 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +105 °C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, $\overline{RESET}$	$V_I = V_{DD}$				1	μA
	I_{LIH2}	P20, P21, P140 to P143	$V_I = V_{DD}$				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	$V_I = V_{DD}$	In input port or external clock input			1	μA
				In resonator connection			10	μA
	I_{LIH4}	P150 to P156	$V_I = AV_{DD}$				1	μA
Input leakage current, low	I_{LIL1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P40 to P46, P50 to P57, P60, P61, P70 to P77, P80 to P83, P125 to P127, P137, P140 to P143, $\overline{RESET}$	$V_I = V_{SS}$				-1	μA
	I_{LIL2}	P20, P21, P140 to P143	$V_I = V_{SS}$				-1	μA
	I_{LIL3}	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	$V_I = V_{SS}$	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
	I_{LIL4}	P150 to P156	$V_I = AV_{SS}$				-1	μA
On-chip pull-up resistance	R_{U1}	P00 to P07, P10 to P17, P20 to P27, P30 to P37, P50 to P57, P70 to P77, P140 to P143, P125 to P127	$V_I = V_{SS}$	2.4 V ≤ V_{DD} ≤ 3.6 V	10	20	100	kΩ
	R_{U2}	P40 to P46, P80 to P83	$V_I = V_{SS}$		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	f_{HOCO} = 48 MHz Note 3, f_{IH} = 24 MHz Note 3	Basic operation	V_{DD} = 3.6 V		2.2	2.9	mA
						V_{DD} = 3.0 V		2.2	2.9	
					Normal operation	V_{DD} = 3.6 V		4.4	9.2	
						V_{DD} = 3.0 V		4.4	9.2	
				f_{HOCO} = 24 MHz Note 3, f_{IH} = 24 MHz Note 3	Basic operation	V_{DD} = 3.6 V		2.0	2.6	
						V_{DD} = 3.0 V		2.0	2.6	
					Normal operation	V_{DD} = 3.6 V		4.2	7.0	
						V_{DD} = 3.0 V		4.2	7.0	
				f_{HOCO} = 16 MHz Note 3, f_{IH} = 16 MHz Note 3	Normal operation	V_{DD} = 3.6 V		3.1	5.0	
						V_{DD} = 3.0 V		3.1	5.0	
			HS (high-speed main) mode Note 5	f_{MX} = 20 MHz Note 2, V_{DD} = 3.6 V	Normal operation	Square wave input		3.5	5.9	mA
						Resonator connection		3.6	6.0	
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		3.5	5.9	
						Resonator connection		3.6	6.0	
				f_{MX} = 16 MHz Note 2, V_{DD} = 3.6 V	Normal operation	Square wave input		2.9	4.5	
						Resonator connection		3.1	4.6	
				f_{MX} = 16 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.9	4.5	
						Resonator connection		3.1	4.6	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.6 V	Normal operation	Square wave input		2.1	3.5	
						Resonator connection		2.2	3.5	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.1	3.5	
						Resonator connection		2.2	3.5	
			HS (High-speed main) mode (PLL operation)	f_{PLL} = 48 MHz, f_{CLK} = 24 MHz Note 2	Normal operation	V_{DD} = 3.6 V		4.7	7.6	mA
						V_{DD} = 3.0 V		4.7	7.6	
				f_{PLL} = 48 MHz, f_{CLK} = 12 MHz Note 2	Normal operation	V_{DD} = 3.6 V		3.1	5.2	
						V_{DD} = 3.0 V		3.1	5.1	
				f_{PLL} = 48 MHz, f_{CLK} = 6 MHz Note 2	Normal operation	V_{DD} = 3.6 V		2.3	3.9	
						V_{DD} = 3.0 V		2.3	3.9	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 4 T_A = -40°C	Normal operation	Square wave input		4.6	6.9	μA
						Resonator connection		4.7	6.9	
				f_{SUB} = 32.768 kHz Note 4 T_A = +25°C	Normal operation	Square wave input		4.9	7.0	
						Resonator connection		5.0	7.2	
				f_{SUB} = 32.768 kHz Note 4 T_A = +50°C	Normal operation	Square wave input		5.2	7.6	
						Resonator connection		5.2	7.7	
				f_{SUB} = 32.768 kHz Note 4 T_A = +70°C	Normal operation	Square wave input		5.5	9.3	
						Resonator connection		5.6	9.4	
				f_{SUB} = 32.768 kHz Note 4 T_A = +85°C	Normal operation	Square wave input		6.2	13.3	
						Resonator connection		6.2	13.4	
				f_{SUB} = 32.768 kHz Note 4 T_A = +105°C	Normal operation	Square wave input		8.3	46.0	
						Resonator connection		8.4	46.0	

(Notes and Remarks are listed on the next page.)

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the high accuracy RTC, 12-bit interval timer, and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 24 MHz

2.4 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 16 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

Remark 3. f_{IH}: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 48 MHz Note 4, f_{IH} = 24 MHz Note 4	V_{DD} = 3.6 V		0.77	3.4	mA
					V_{DD} = 3.0 V		0.77	3.4	
				f_{HOCO} = 24 MHz Note 4, f_{IH} = 24 MHz Note 4	V_{DD} = 3.6 V		0.55	2.7	
					V_{DD} = 3.0 V		0.55	2.7	
				f_{HOCO} = 16 MHz Note 4, f_{IH} = 16 MHz Note 4	V_{DD} = 3.6 V		0.48	1.9	
					V_{DD} = 3.0 V		0.47	1.9	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 3.6 V	Square wave input		0.35	2.10	mA
					Resonator connection		0.51	2.20	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.34	2.10	
					Resonator connection		0.51	2.20	
				f_{MX} = 16 MHz Note 3, V_{DD} = 3.6 V	Square wave input		0.30	1.25	
					Resonator connection		0.45	1.41	
				f_{MX} = 16 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.29	1.23	
					Resonator connection		0.45	1.41	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.6 V	Square wave input		0.23	1.10	
					Resonator connection		0.30	1.20	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.22	1.10	
					Resonator connection		0.30	1.20	
			HS (High-speed main) mode (PLL operation)	f_{MX} = 48 MHz, f_{CLK} = 24 MHz Note 3	V_{DD} = 3.6 V		0.99	2.93	mA
					V_{DD} = 3.0 V		0.99	2.92	
				f_{MX} = 48 MHz, f_{CLK} = 12 MHz Note 3	V_{DD} = 3.6 V		0.89	2.51	
					V_{DD} = 3.0 V		0.89	2.50	
				f_{MX} = 48 MHz, f_{CLK} = 6 MHz Note 3	V_{DD} = 3.6 V		0.84	2.30	
					V_{DD} = 3.0 V		0.84	2.29	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5 T_A = -40°C	Square wave input		0.32	0.61	μA
					Resonator connection		0.51	0.80	
				f_{SUB} = 32.768 kHz Note 5 T_A = +25°C	Square wave input		0.41	0.74	
					Resonator connection		0.62	0.91	
				f_{SUB} = 32.768 kHz Note 5 T_A = +50°C	Square wave input		0.52	2.30	
					Resonator connection		0.75	2.49	
				f_{SUB} = 32.768 kHz Note 5 T_A = +70°C	Square wave input		0.82	4.03	
					Resonator connection		1.08	4.22	
				f_{SUB} = 32.768 kHz Note 5 T_A = +85°C	Square wave input		1.38	8.04	
					Resonator connection		1.62	8.23	
				f_{SUB} = 32.768 kHz Note 5 T_A = +105°C	Square wave input		3.29	41.00	
					Resonator connection		3.63	41.00	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.18	0.52	μA
			T_A = +25°C				0.25	0.52	
			T_A = +50°C				0.34	2.21	
			T_A = +70°C				0.64	3.94	
			T_A = +85°C				1.18	7.95	
			T_A = +105°C				2.92	40.00	

(Notes and Remarks are listed on the next page.)

Note 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, D/A converter, comparator, LVD circuit, USB 2.0 function module, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. During HALT instruction execution by flash memory.

Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 4. When high-speed system clock and subsystem clock are stopped.

Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the high accuracy RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 6. Not including the current flowing into the high accuracy RTC, 12-bit interval timer, and watchdog timer.

Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 24 MHz

2.4 V ≤ V_{DD} ≤ 3.6 V@1 MHz to 16 MHz

Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (48 MHz max.)

Remark 3. f_{IH}: Main system clock source frequency when the high-speed on-chip oscillator clock divided 1, 2, 4, or 8, or the PLL clock divided by 2, 4, or 8 is selected (24 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1						0.20		μA
High-accuracy RTC operating current	I_{RTC} Notes 1, 3						0.02		μA
12-bit interval timer operating current	I_{TMKA} Notes 1, 2, 4						0.02		μA
Watchdog timer operating current	I_{WDT} Notes 1, 4	f_{IL} = 15 kHz					0.22		μA
A/D converter operating current	I_{ADC} Notes 6, 7	AV_{DD} = 3.0 V, when conversion at maximum speed					422	720	μA
$AV_{REF(+)}$ current	I_{AVREF} Note 8	AV_{DD} = 3.0 V, ADREFP1 = 0, ADREFP0 = 0 Note 7					14.0	25.0	μA
		AV_{REFP} = 3.0 V, ADREFP1 = 0, ADREFP0 = 1 Note 10					14.0	25.0	
		ADREFP1 = 1, ADREFP0 = 0 Note 1					14.0	25.0	
A/D converter reference voltage current	I_{ADREF} Notes 1, 9	V_{DD} = 3.0 V					75.0		μA
Temperature sensor operating current	I_{TMPS} Note 1						78		μA
D/A converter operating current	I_{DAC} Notes 1, 11	Per D/A converter channel					0.53	1.5	mA
Comparator operating current	I_{CMP} Notes 1, 12	V_{DD} = 3.6 V, Regulator output voltage = 2.1 V	Window mode				12.5		μA
			Comparator high-speed mode				4.5		μA
			Comparator low-speed mode				1.2		μA
LVD operating current	I_{LVI} Notes 1, 13						0.06		μA
Self-programming operating current	I_{FSP} Notes 1, 14						2.50	12.20	mA
BGO operating current	I_{BGO} Notes 1, 15						1.68	12.20	mA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation	The mode is performed Note 16				0.34	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V				0.53	2.04	
		CSI/UART operation					0.70	1.54	mA
LCD operating current	I_{LCD1} Notes 17, 18	External resistance division method	f_{LCD} = f_{SUB} LCD clock = 128 Hz	1/3 bias 4-time slice	V_{DD} = 3.6 V, L_{V4} = 3.6 V		0.14		μA
	I_{LCD2} Note 17	Internal voltage boosting method	f_{LCD} = f_{SUB} LCD clock = 128 Hz	1/3 bias 4-time slice	V_{DD} = 3.0 V, L_{V4} = 3.0 V (VLCD = 04H)		0.61		μA
	I_{LCD3} Note 17	Capacitor split method	f_{LCD} = f_{SUB} LCD clock = 128 Hz	1/3 bias 4-time slice	V_{DD} = 3.0 V, L_{V4} = 3.0 V		0.12		μA
USB current Note 19	I_{USB} Note 20	Operating current during USB communication					4.88		mA
	I_{USB} Note 21	Operating current in the USB suspended state					0.04		mA

(Notes and Remarks are listed on the next page.)

Note 1. Current flowing to V_{DD}.

Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.

Note 3. Current flowing only to the high accuracy real-time clock (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the high accuracy real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the high accuracy real-time clock.

Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{TMKA}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the 12-bit interval timer.

Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates in STOP mode.

Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC}, I_{AVREF}, I_{ADREF} when the A/D converter operates in an operation mode or the HALT mode.

Note 7. Current flowing to the AV_{DD}.

Note 8. Current flowing from the reference voltage source of A/D converter.

Note 9. Operation current flowing to the internal reference voltage.

Note 10. Current flowing to the AV_{REFP}.

Note 11. Current flowing only to the D/A converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{DA} when the D/A converter operates in an operation mode or the HALT mode.

Note 12. Current flowing only to the comparator circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{CMP} when the comparator circuit operates in the Operating, HALT or STOP mode.

Note 13. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVI} when the LVD circuit operates in the Operating, HALT or STOP mode.

Note 14. Current flowing only during self-programming.

Note 15. Current flowing only during data flash rewrite.

Note 16. For shift time to the SNOOZE mode, see **23.3.3 SNOOZE mode in the RL78/L1C User's Manual Hardware**.

Note 17. Current flowing only to the LCD controller/driver (V_{DD} pin). The current value of the RL78 microcontrollers is the sum of the LCD operating current (I_{LCD1}, I_{LCD2} or I_{LCD3}) to the supply current (I_{DD1}, or I_{DD2}) when the LCD controller/driver operates in an operation mode or HALT mode. Not including the current that flows through the LCD panel.

Note 18. Not including the current that flows through the external divider resistor divider resistor.

Note 19. Current flowing to the UV_{BUS}.

Note 20. Including the operating current when f_{PLL} = 48 MHz.

Note 21. Including the current supplied from the pull-up resistor of the UDP pin to the pull-down resistor of the host device, in addition to the current consumed by this MCU during the suspended state.

Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency

Remark 4. Temperature condition of the TYP. value is T_A = 25°C

3.4 AC Characteristics

3.4.1 Basic operation

(T_A = -40 to +105 °C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(1/2)**

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
		Subsystem clock (f_{SUB}) operation		2.4 V ≤ V_{DD} ≤ 3.6 V	28.5	30.5	31.3	μs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
External main system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 3.6 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
	f_{EXT}				32		35	kHz
External main system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 3.6 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10			ns

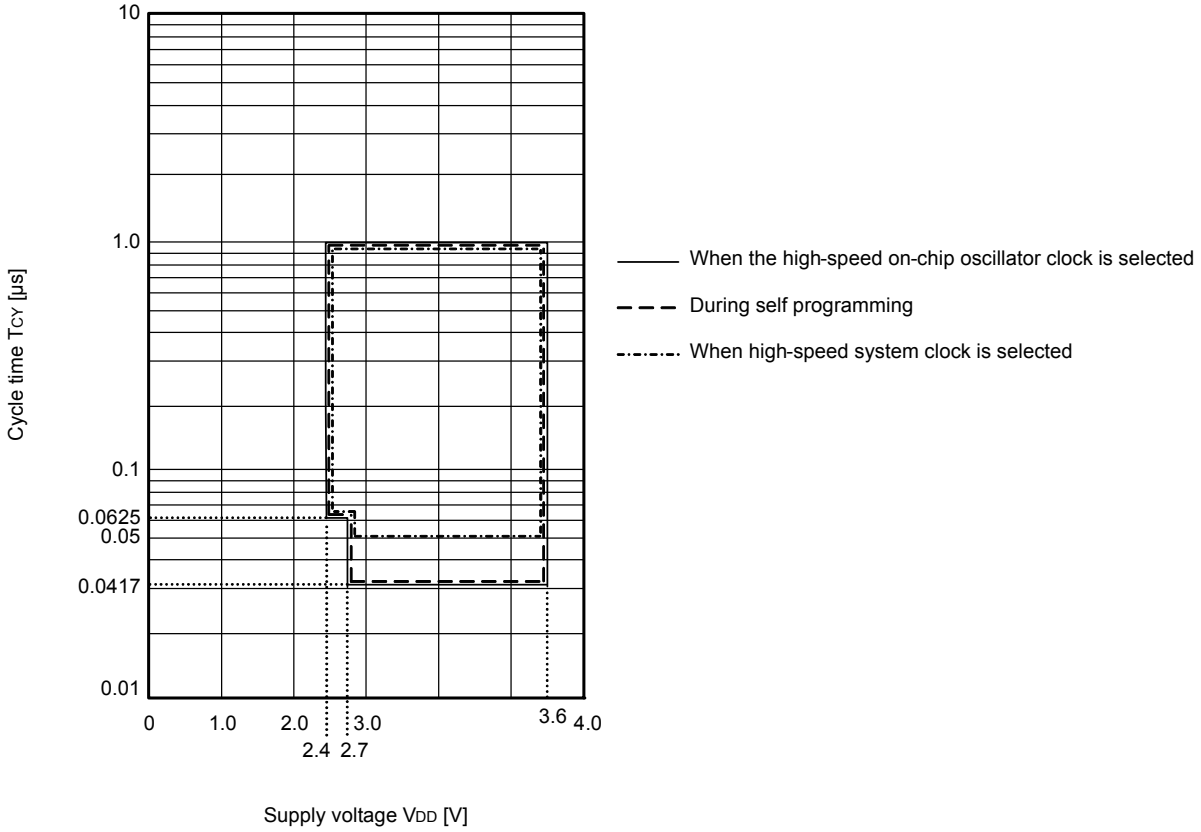
Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 7))

(T_A = -40 to +105 °C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V) **(2/2)**

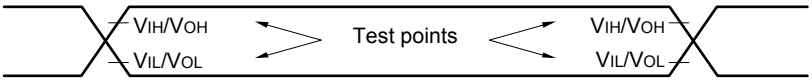
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
TO00 to TO07, TKBO00, TKBO01, TKBO10, TKBO11, TKBO20, TKBO21 output frequency	f_{TO}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			8	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 3.6 V			8	MHz
			2.4 V ≤ V_{DD} < 2.7 V			8	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0 to INTP7	2.4 V ≤ V_{DD} ≤ 3.6 V	1			μs
Key interrupt input low-level width	t_{KR}	2.4 V ≤ V_{DD} ≤ 3.6 V		250			ns
TMKB2 forced output stop input high-level width	t_{IHR}	INTP0 to INTP7	f_{CLK} > 16 MHz	125			ns
			f_{CLK} ≤ 16 MHz	2			f_{CLK}
$\overline{\text{RESET}}$ low-level width	t_{RSL}			10			μs

Minimum Instruction Execution Time during Main System Clock Operation

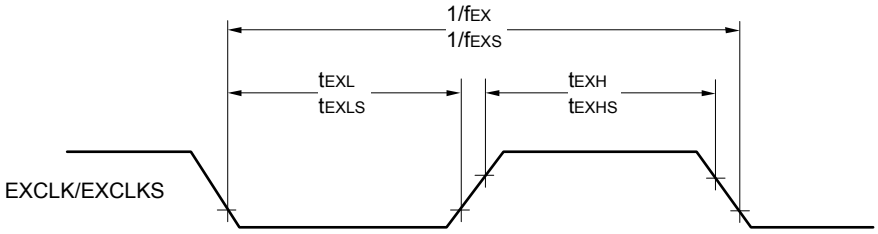
TCY vs VDD (HS (high-speed main) mode)



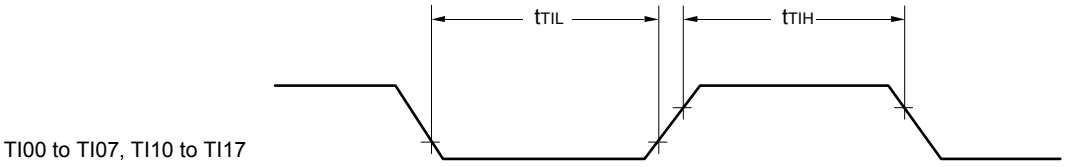
AC Timing Test Points

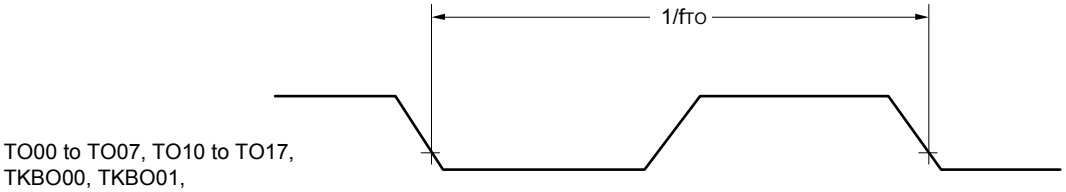


External System Clock Timing

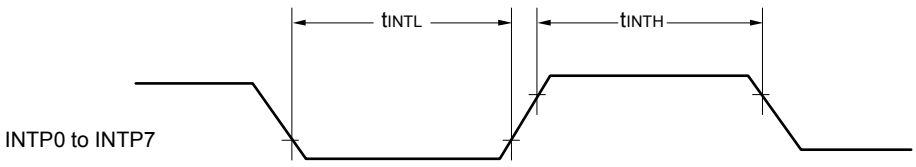


TI/TO Timing

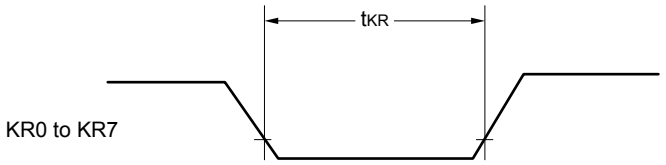




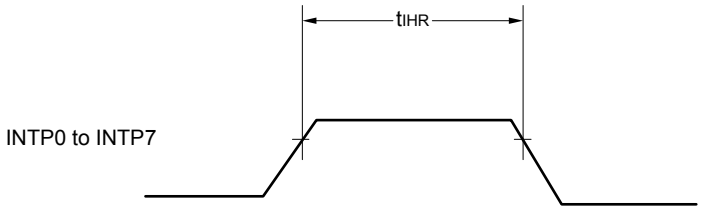
Interrupt Request Input Timing



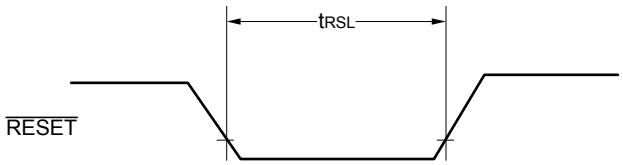
Key Interrupt Input Timing



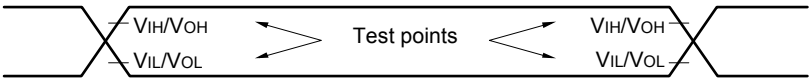
Timer KB2 Input Timing



$\overline{\text{RESET}}$ Input Timing



3.5 Peripheral Functions Characteristics



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +105 °C, 2.4 V ≤ VDD ≤ 3.6 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ VDD ≤ 3.6 V		fMCK/12 Note 2	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.0	Mbps

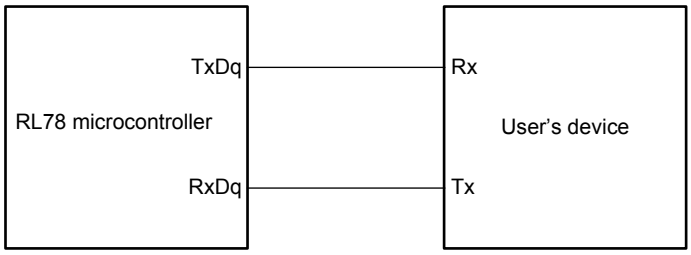
Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The following conditions are required for low voltage interface.
2.4 V ≤ VDD < 2.7 V: MAX. 1.3 Mbps

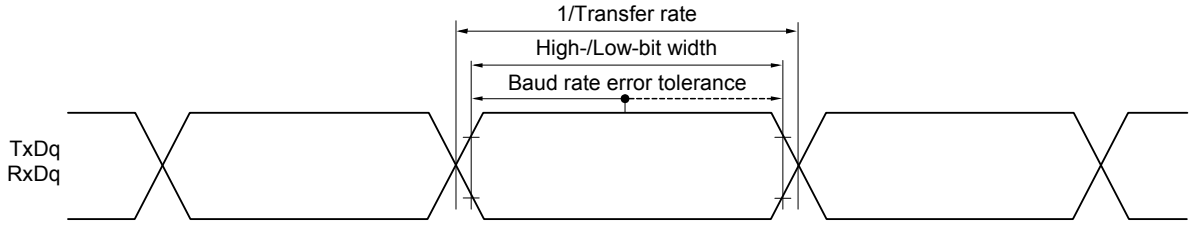
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fCLK) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ VDD ≤ 3.6 V)
16 MHz (2.4 V ≤ VDD ≤ 3.6 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 2. fMCK: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7 V ≤ V_{DD} ≤ 3.6 V	250		ns
			2.4 V ≤ V_{DD} ≤ 3.6 V	500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 36		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		t_{KCY1}/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V		66		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		133		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			38		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note 4			50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)

Remark 2. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 5	t_{KCY2}	2.7 V ≤ V_{DD} < 3.6 V	f_{MCK} > 16 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 16 MHz	12/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 3.6 V		12/f_{MCK} and 1000		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 16		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		t_{KCY2}/2 - 36		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 40		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO2}	C = 30 pF Note 4	2.7 V ≤ V_{DD} ≤ 3.6 V		2/f_{MCK} + 66	ns
			2.4 V ≤ V_{DD} < 3.6 V		2/f_{MCK} + 113	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SOp output lines.

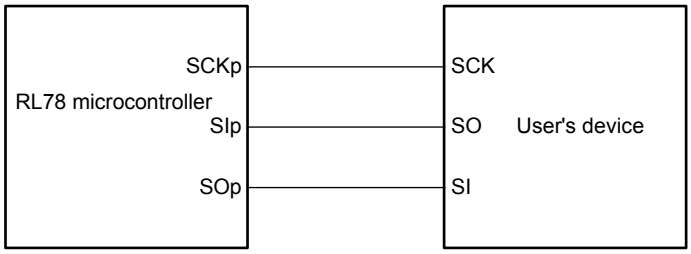
Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0 to 3)

Remark 2. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

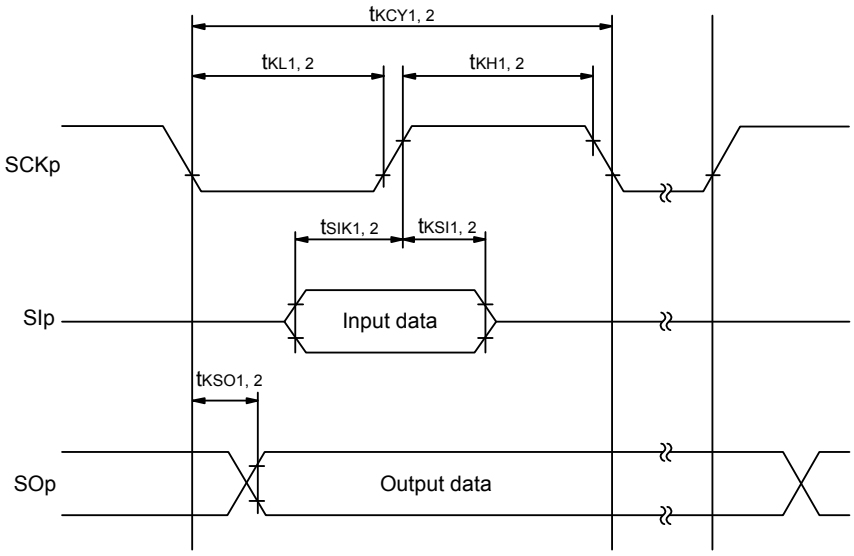
CSI mode connection diagram (during communication at same potential)



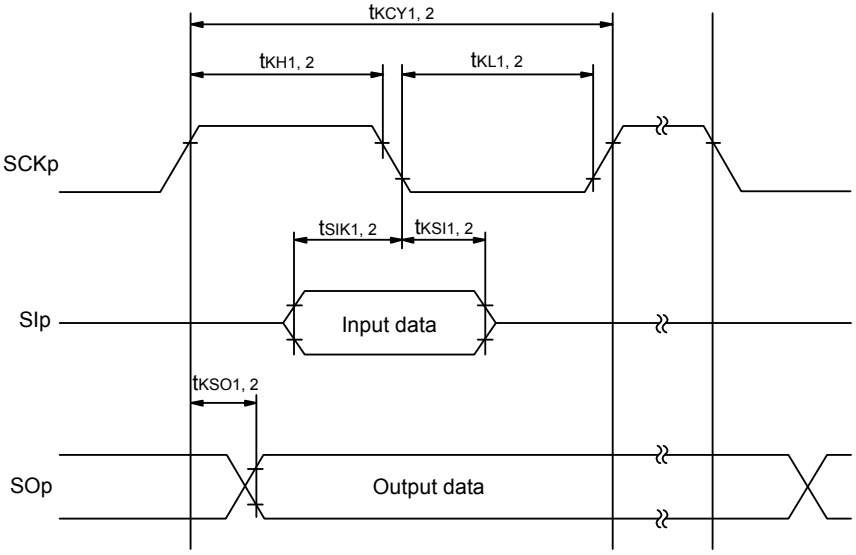
Remark 1. p: CSI number (p = 00, 10, 20, 30)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 10, 20, 30)
Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(4) During communication at same potential (simplified I²C mode)

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

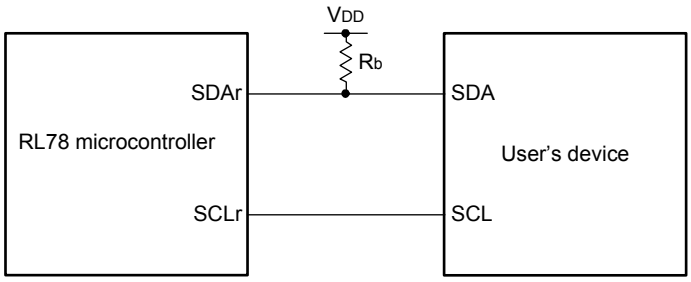
Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ		400 Note 1	kHz
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ		100 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 200 Note 2		ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 580 Note 2		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		2.4 V ≤ V_{DD} ≤ 3.6 V, C_b = 100 pF, R_b = 3 kΩ	0	1420	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

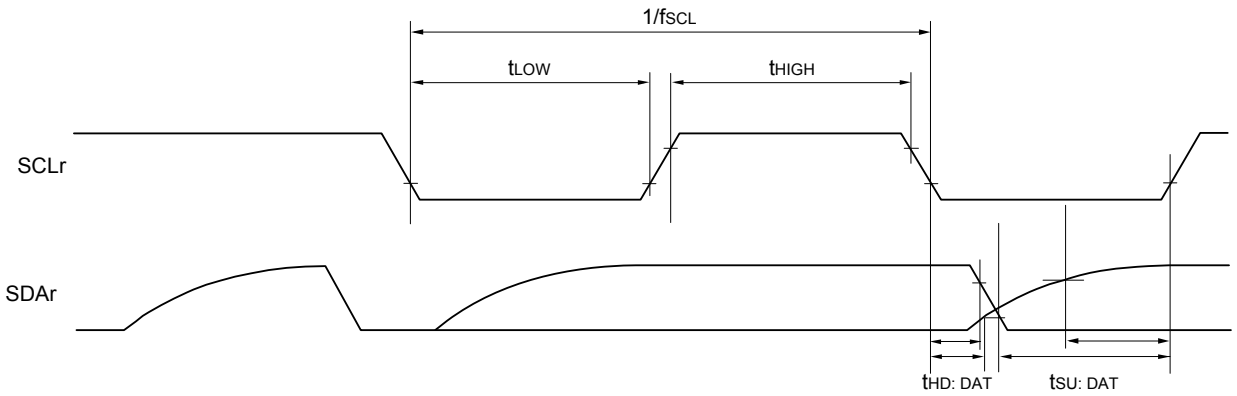
Note 2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I^2C mode serial transfer timing (during communication at same potential)



Remark 1. R_b[Ω]: Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM number (g = 0 to 3),
h: POM number (h = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),
n: Channel number (n = 0, 2), mn = 00 to 03, 10 to 13)

(5) Communication at different potential (1.8 V, 2.5 V) (UART mode) (dedicated baud rate generator output)

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate Notes 1, 2		Reception	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		f_{MCK}/12 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 4		2.0	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		f_{MCK}/12 Notes 1, 2, 3	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 4		1.3	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.

Note 2. Use it with V_{DD} ≥ Vb.

Note 3. The following conditions are required for low voltage interface.
2.4 V ≤ V_{DD} < 2.7 V: MAX. 2.6 Mbps

Note 4. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 3.6 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 3.6 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(5) Communication at different potential (1.8 V, 2.5V) (UART mode) (dedicated baud rate generator output)

(T_A = -40 to +105 °C, 2.4 ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
Transfer rate Note 2		Transmission	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 2	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Notes 3, 4	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 5	Mbps

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} < 3.6 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. Use it with $V_{DD} \geq V_b$.

Note 4. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.4 V ≤ V_{DD} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

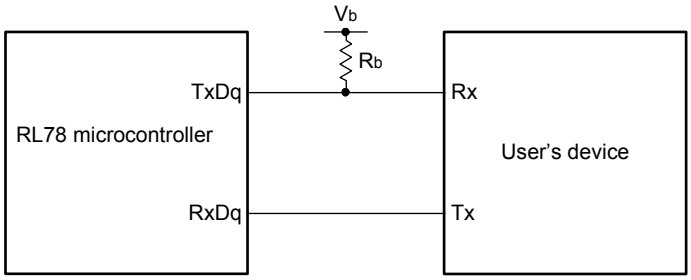
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

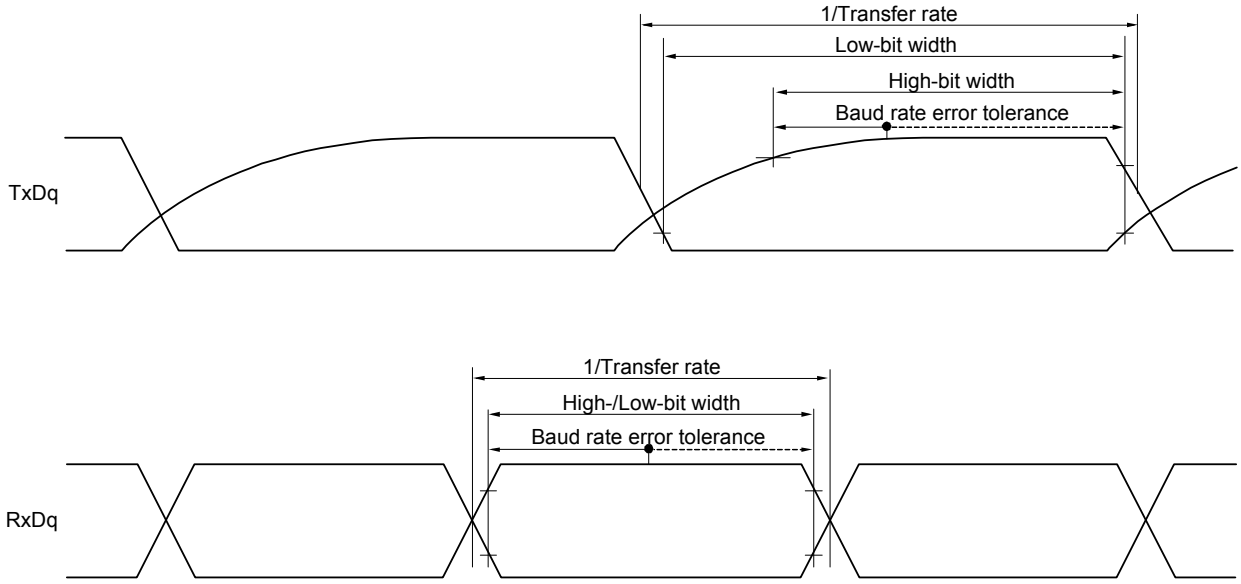
Note 5. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to Note 4 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Remark 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq f_{CLK}/4$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	1000 Note		ns
			2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 1.8 V, C_b = 30 pF, R_b = 5.5 kΩ	2300 Note		ns
SCKp high-level width	t_{KH1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 340		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 916		ns
SCKp low-level width	t_{KL1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 36		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 100		ns

Note Use it with $V_{DD} \geq V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V) (2/2)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	354		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	958		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		390	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		966	ns
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	88		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	220		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		50	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 30 pF, R_b = 5.5 kΩ		50	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

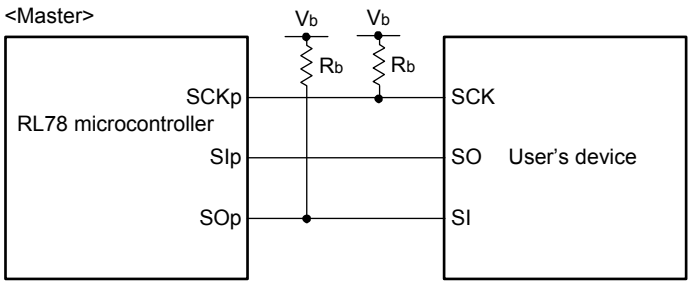
Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. Use it with $V_{DD} \geq V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

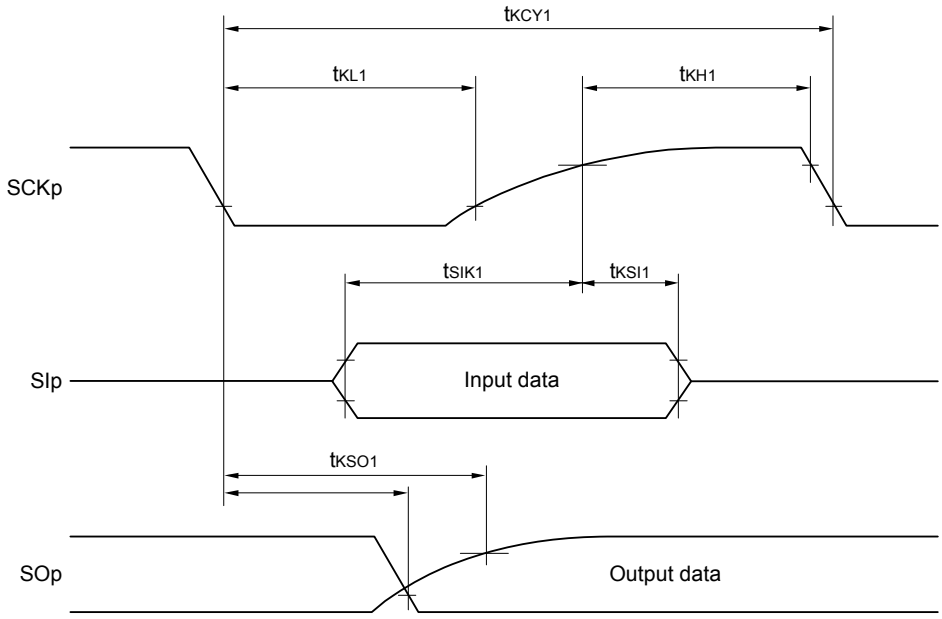


Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

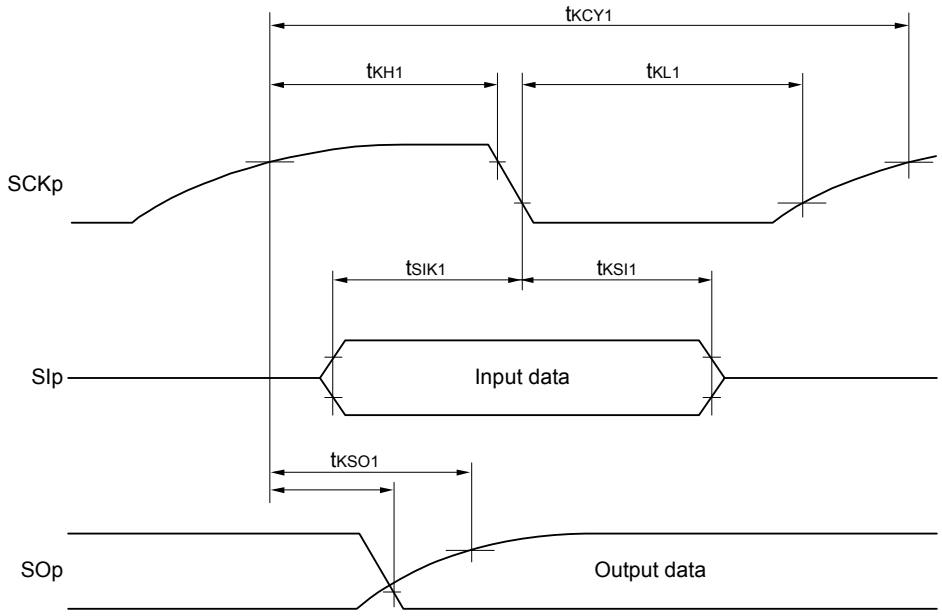
Remark 2. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM number (g = 0 to 3)

(7) Communication at different potential (1.8 V, 2.5 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK} ≤ 24 MHz	32/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	28/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	24/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	12/f_{MCK}		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	20 MHz < f_{MCK} ≤ 24 MHz	72/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	64/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	52/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	32/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	20/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 - 36		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2		t_{KCY2}/2 - 100		ns
SIp setup time (to SCKp↑) Note 3	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 3.6 V		1/f_{MCK} + 40		ns
		2.4 V ≤ V_{DD} < 3.3 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 4	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 5	t_{KSO2}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b ≤ 2.7 V C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 428	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2 C_b = 30 pF, R_b = 5.5 kΩ			2/f_{MCK} + 1146	ns

(Notes and Caution are listed on the next page. Remarks are listed on the page after the next page.)

Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Note 2. Use it with $V_{DD} \geq V_b$.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

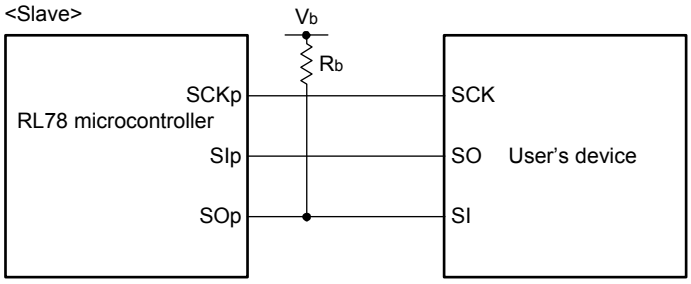
Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

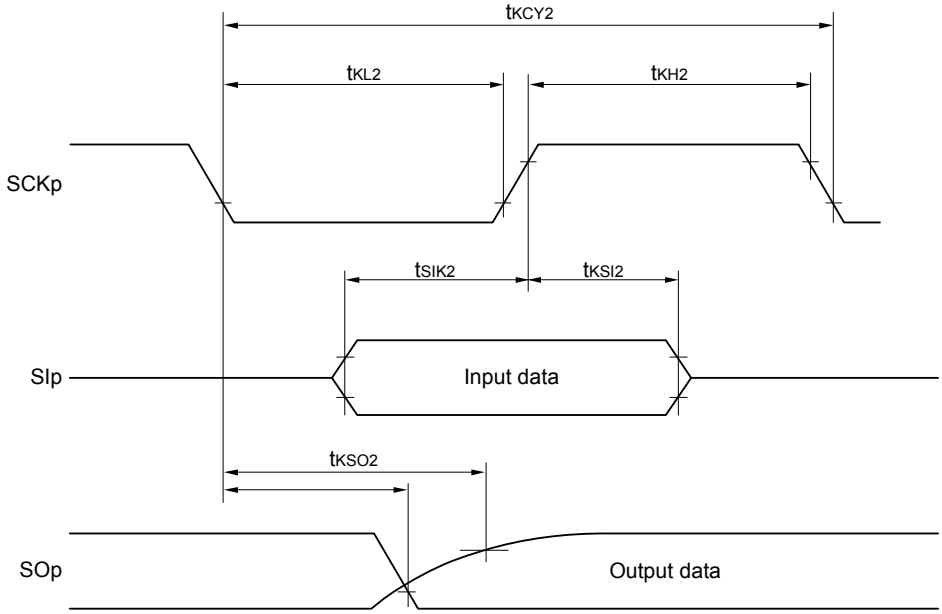


Remark 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

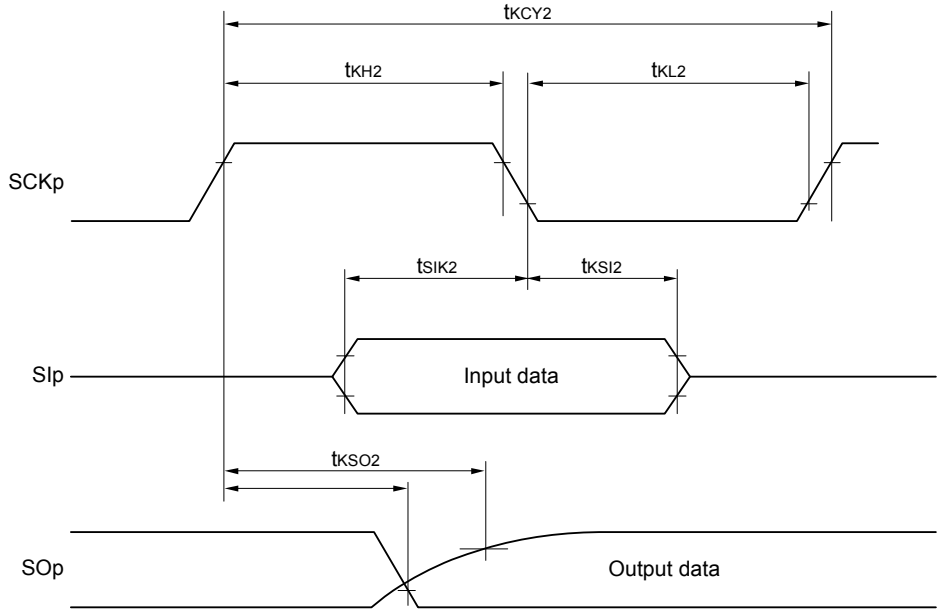
Remark 2. p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02, 10, 12))

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 10, 20, 30), m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0 to 3)

(8) Communication at different potential (1.8 V, 2.5 V) (simplified I²C mode)

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ		400 Note 1	kHz
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		100 Note 1	kHz
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ		100 Note 1	kHz
Hold time when SCLr = “L”	t_{LOW}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b <2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	4600		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	4650		ns
Hold time when SCLr = “H”	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	500		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	2400		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1830		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 340 Note 3		ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 760 Note 3		ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 570 Note 3		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		2.7 V ≤ V_{DD} ≤ 3.6 V, 2.3 V ≤ V_b < 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	1420	ns
		2.4 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	0	1215	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

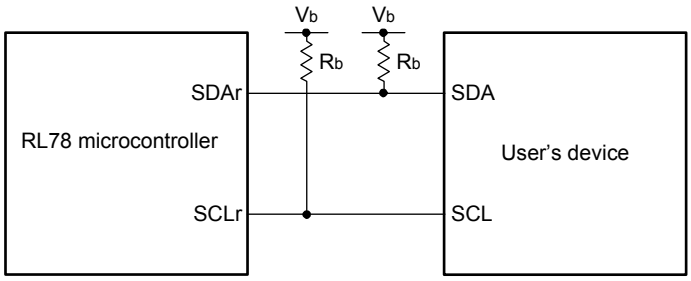
Note 2. Use it with $V_{DD} \geq V_b$.

Note 3. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

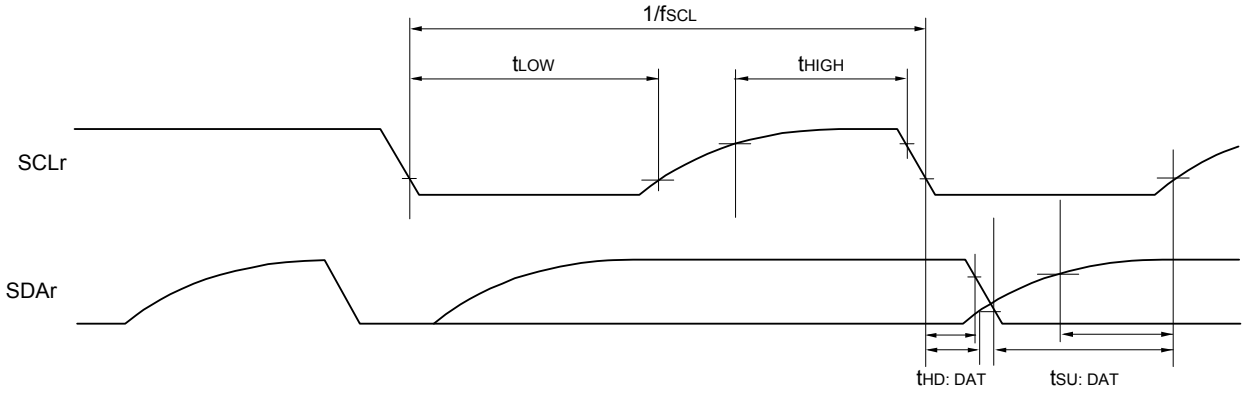
Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 10, 20, 30), g: PIM, POM number (g = 0 to 3)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 02, 10, 12)

3.5.2 Serial interface IICA

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode				Unit
			Standard mode		Fast mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: f_{CLK} ≥ 3.5 MHz	—	—	0	400	kHz
		Standard mode: f_{CLK} ≥ 1 MHz	0	100	—	—	kHz
Setup time of restart condition	$t_{SU: STA}$		4.7		0.6		µs
Hold time Note 1	$t_{HD: STA}$		4.0		0.6		µs
Hold time when SCLA0 = “L”	t_{LOW}		4.7		1.3		µs
Hold time when SCLA0 = “H”	t_{HIGH}		4.0		0.6		µs
Data setup time (reception)	$t_{SU: DAT}$		250		100		ns
Data hold time (transmission) Note 2	$t_{HD: DAT}$		0	3.45	0	0.9	µs
Setup time of stop condition	$t_{SU: STO}$		4.0		0.6		µs
Bus-free time	t_{BUF}		4.7		1.3		µs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

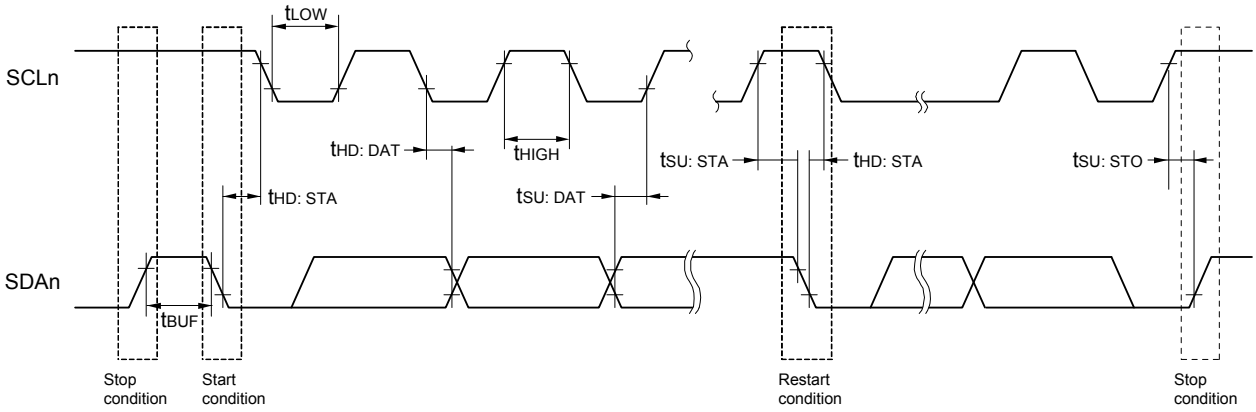
Note 2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 kΩ

Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

IICA serial transfer timing



3.5.3 USB

(1) Electrical specifications

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, HS (High-speed main) mode only)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
U_{REGC}	U_{REGC} output voltage characteristic	U_{REGC}	UV_{BUS} = 4.0 to 5.5 V, PXXCON = VDDUSBE = 1	3.0	3.3	3.6	V
UV_{BUS}	UV_{BUS} input voltage characteristic	UV_{BUS}	Function	4.35 (4.02 Note)	5.00	5.25	V

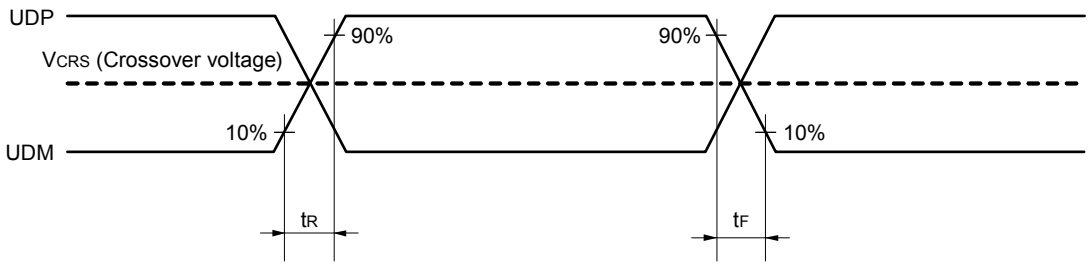
Note Value of instantaneous voltage

(T_A = -40 to +105 °C, 4.35 V ≤ UV_{BUS} ≤ 5.25 V, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V, HS (High-speed main) mode only)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input characteristic (FS/LS receiver)	Input voltage		V_{IH}		2.0			V
			V_{IL}				0.8	V
	Difference input sensitivity		V_{DI}	| UDP voltage - UDM voltage |	0.2			V
	Difference common mode range		V_{CM}		0.8		2.5	V
Output characteristic (FS driver)	Output voltage		V_{OH}	I_{OH} = -200 μA	2.8		3.6	V
			V_{OL}	I_{OL} = 2 mA	0		0.3	V
	Transition time	Rising	t_{FR}	Rising: From 10% to 90% of amplitude, Falling: From 90% to 10% of amplitude, CL = 50 pF	4		20	ns
		Falling	t_{FF}		4		20	ns
	Matching (TFR/TFF)		V_{FRFM}		90		111.1	%
	Crossover voltage		V_{FCRS}		1.3		2.0	V
	Output Impedance		Z_{DRV}	U_{REGC} voltage = 3.3 V, Pin voltage = 1.65 V	28		44	Ω
Output characteristic (LS driver)	Output voltage		V_{OH}		2.8		3.6	V
			V_{OL}		0		0.3	V
	Transition time	Rising	t_{LR}	Rising: From 10% to 90% of amplitude, Falling: From 90% to 10% of amplitude, CL = 250 pF to 750 pF The UDP and UDM pins are individually pulled down via 15 kΩ	75		300	ns
		Falling	t_{LF}		75		300	ns
	Matching (TFR/TFF) Note		V_{LTFM}		80		125	%
	Crossover voltage Note		V_{LCRS}		1.3		2.0	V
Pull-up, Pull-down	Pull-down resistor		R_{PD}		14.25		24.80	kΩ
	Pull-up resistor	Idle	R_{PUI}		0.9		1.575	kΩ
		Reception	R_{PUA}		1.425		3.09	kΩ
UV_{BUS}	UV_{BUS} pull-down resistor		R_{VBUS}	UV_{BUS} voltage = 5.5 V		1000		kΩ
	UV_{BUS} input voltage		V_{IH}		3.20			V
			V_{IL}				0.8	V

Note Excludes the first signal transition from the idle state.

Timing of UDP and UDM



(2) BC standard

(TA = -40 to +105 °C, 4.35 V ≤ UVBUS ≤ 5.25 V, 2.4 V ≤ VDD ≤ 3.6 V, VSS = 0 V, HS (High-speed main) mode only)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
USB standard BC1.2	UDP sink current	IDP_SINK		25	100	175	μA
	UDM sink current	IDM_SINK		25	100	175	μA
	DCD source current	IDP_SRC		7	10	13	μA
	Data detection voltage	VDAT_REF		0.25	0.325	0.4	V
	UDP source voltage	VDP_SRC	Output current 250 μA	0.5	0.6	0.7	V
	UDM source voltage	VDM_SRC	Output current 250 μA	0.5	0.6	0.7	V

(3) BC option standard

(T_A = -40 to +105 °C, 4.35 V ≤ UV_{BUS} ≤ 5.25 V, 2.4 V ≤ V_{DD} ≤ 3.6, V_{SS} = 0 V)

Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
UDP/UDM input reference voltage (UV_{BUS} divider ratio) (Function)	VDSELi [3: 0] (i = 0, 1)	0000	V_{DDET0}		27	32	37	%UVBUS
		0001	V_{DDET1}		29	34	39	%UVBUS
		0010	V_{DDET2}		32	37	42	%UVBUS
		0011	V_{DDET3}		35	40	45	%UVBUS
		0100	V_{DDET4}		38	43	48	%UVBUS
		0101	V_{DDET5}		41	46	51	%UVBUS
		0110	V_{DDET6}		44	49	54	%UVBUS
		0111	V_{DDET7}		47	52	57	%UVBUS
		1000	V_{DDET8}		51	56	61	%UVBUS
		1001	V_{DDET9}		55	60	65	%UVBUS
		1010	V_{DDET10}		59	64	69	%UVBUS
		1011	V_{DDET11}		63	68	73	%UVBUS
		1100	V_{DDET12}		67	72	73	%UVBUS
		1101	V_{DDET13}		71	76	81	%UVBUS
		1110	V_{DDET14}		75	80	85	%UVBUS
		1111	V_{DDET15}		79	84	89	%UVBUS

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage / Input Channel	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = AV_{DD} Reference voltage (-) = AV_{SS}	Reference voltage (+) = Internal reference voltage Reference voltage (-) = AV_{SS}
High-accuracy channel; ANI0 to ANI6 (input buffer power supply: AV_{DD})	Refer to **3.6.1 (1)**.	Refer to **3.6.1 (2)**.	Refer to **3.6.1 (5)**.
Standard channel; ANI16 to ANI21 (input buffer power supply: V_{DD})	Refer to **3.6.1 (3)**.	Refer to **3.6.1 (4)**.	
Internal reference voltage, Temperature sensor output voltage	Refer to **3.6.1 (3)**.	Refer to **3.6.1 (4)**.	—

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), conversion target: ANI2 to ANI6

(T_A = -40 to +105 °C, 2.4 V ≤ AV_{REFP} ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		12	bit
Overall error Note	AINL	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	3.375			µs
Zero-scale error Note	EZS	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
Full-scale error Note	EFS	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±4.5	LSB
Integral linearity error Note	ILE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
Differential linearity error Note	DLE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±1.5	LSB
Analog input voltage	V_{AIN}			0		AV_{REFP}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(2) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AV_{SS} (ADREFM = 0), conversion target: ANI0 to ANI6

(T_A = -40 to +105 °C, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (-) = AV_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
Overall error Note	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±7.5	LSB
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	3.375			µs
Zero-scale error Note	EZS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
Full-scale error Note	EFS	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±6.0	LSB
Integral linearity error Note	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.0	LSB
Differential linearity error Note	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
Analog input voltage	V_{AIN}			0		AV_{DD}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(3) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), conversion target ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, 2.4 V ≤ AV_{REFP} ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}		2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	8		12	bit
Overall error Note 1	AINL	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±7.0	LSB
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V	4.125			μs
Zero-scale error Note 1	E_{ZS}	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±5.0	LSB
Full-scale error Note 1	E_{FS}	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±5.0	LSB
Integral linearity error Note 1	ILE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±3.0	LSB
Differential linearity error Note 1	DLE	12-bit resolution	2.4 V ≤ AV_{REFP} ≤ AV_{DD} ≤ 3.6 V			±2.0	LSB
Analog input voltage	V_{AIN}			0		AV_{REFP}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{BGR} Note 2			
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{TMP25} Note 2			

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. Refer to **3.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(4) When reference voltage (+) = AV_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = AV_{SS} (ADREFM = 0), conversion target: ANI16 to ANI21, internal reference voltage, temperature sensor output voltage

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, 2.4 V ≤ AV_{DD} = V_{DD} ≤ 3.6 V, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = AV_{DD}, Reference voltage (-) = AV_{SS} = 0)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	R_{ES}		2.4 V ≤ AV_{DD} ≤ 3.6 V	8		12	bit
Overall error Note 1	AINL	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.5	LSB
Conversion time	t_{CONV}	ADTYP = 0, 12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V	4.125			μs
Zero-scale error Note 1	E_{ZS}	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
Full-scale error Note 1	E_{FS}	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±8.0	LSB
Integral linearity error Note 1	ILE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±3.5	LSB
Differential linearity error Note 1	DLE	12-bit resolution	2.4 V ≤ AV_{DD} ≤ 3.6 V			±2.5	LSB
Analog input voltage	V_{AIN}			0		AV_{DD}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{BGR} Note 2			
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode)		V_{TMP25} Note 2			

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. Refer to **3.6.2 Temperature sensor, internal reference voltage output characteristics**.

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

(5) When reference voltage (+) = Internal reference voltage (1.45 V) (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVSS (ADREFM = 0), conversion target: ANI0 to ANI6, ANI16 to ANI21

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, 2.4 V ≤ V_{DD}, 2.4 V ≤ AV_{DD} = V_{DD}, V_{SS} = 0 V, AV_{SS} = 0 V, Reference voltage (+) = internal reference voltage, Reference voltage (-) = AV_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tCONV	8-bit resolution	16.0			μs
Zero-scale error Note	EZS	8-bit resolution			±4.0	LSB
Integral linearity error Note	ILE	8-bit resolution			±2.0	LSB
Differential linearity error Note	DLE	8-bit resolution			±2.5	LSB
Reference voltage (+)	$AV_{REF(+)}$	= Internal reference voltage (V_{BGR})	1.38	1.45	1.5	V
Analog input voltage	VAIN		0		V_{BGR}	V

Note Excludes quantization error (±1/2 LSB).

Caution Always use AV_{DD} pin with the same potential as the V_{DD} pin.

3.6.2 Temperature sensor, internal reference voltage output characteristics

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V (HS (high-speed main) mode))

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, T_A = +25°C		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor output voltage that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tAMP		10			μs

3.6.3 D/A converter characteristics

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	2.4 V ≤ V_{DD} ≤ 3.6 V			±2.5	LSB
		Rload = 8 MΩ	2.4 V ≤ V_{DD} ≤ 3.6 V			±2.5	LSB
Settling time	tSET	Cload = 20 pF	2.7 V ≤ V_{DD} ≤ 3.6 V			3	μs
			2.4 V ≤ V_{DD} < 2.7 V			6	μs

3.6.4 Comparator

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		V_{DD} - 1.4	V
	Ivcmp			-0.3		V_{DD} + 0.3	V
Output delay	td	V_{DD} = 3.0 V Input slew rate > 50 mV/μs	High-speed comparator mode, standard mode			1.2	μs
			High-speed comparator mode, window mode			2.0	μs
			Low-speed comparator mode, standard mode		3	5.0	μs
High-electric-potential judgment voltage	VTW+	High-speed comparator mode, window mode			0.76 V_{DD}		V
Low-electric-potential judgment voltage	VTW-	High-speed comparator mode, window mode			0.24 V_{DD}		V
Operation stabilization wait time	t_{CMP}			100			μs
Internal reference voltage Note	V_{BGR}	2.4 V ≤ V_{DD} ≤ 3.6 V, HS (high-speed main) mode		1.38	1.45	1.50	V

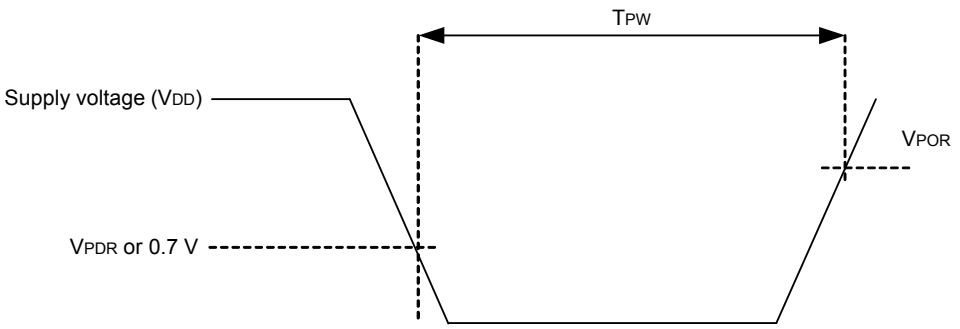
Note Not usable in sub-clock operation or STOP mode.

3.6.5 POR circuit characteristics

(T_A = -40 to +105 °C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.45	1.51	1.57	V
	V_{PDR}	Power supply fall time Note	1.44	1.50	1.56	V
Minimum pulse width	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.6 LVD circuit characteristics

(T_A = -40 to +105 °C, $V_{PDR} \leq V_{DD} \leq 3.6$ V $\leq V_{SS}$ = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD2}	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	V
		V_{LVD3}	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		V_{LVD4}	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		V_{LVD5}	Power supply rise time	2.71	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		V_{LVD6}	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		V_{LVD7}	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum pulse width		t_{LW}		300			μs
Detection delay time						300	μs

Caution Set the detection voltage (V_{LVD}) to be within the operating voltage range. The operating voltage range depends on the setting of the user option byte (000C2H/010C2H). The following shows the operating voltage range.
HS (high-speed main) mode: V_{DD} = 2.7 to 3.6 V at 1 MHz to 24 MHz
V_{DD} = 2.4 to 3.6 V at 1 MHz to 16 MHz

LVD Detection Voltage of Interrupt & Reset Mode

(T_A = -40 to +105 °C, $V_{PDR} \leq V_{DD} \leq$ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDD0}	V_{POC0}, V_{POC1}, V_{POC2} = 0, 1, 1, falling reset voltage: 2.7 V			2.64	2.75	2.86	V
	V_{LVDD1}		LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	V_{LVDD2}		LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V

3.7 Power supply voltage rising slope characteristics

(T_A = -40 to +105 °C, V_{SS} = 0 V)

Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SV_{DD}			54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.8 LCD Characteristics

3.8.1 Resistance division method

(1) Static display mode

(T_A = -40 to +105 °C, V_{L4} (MIN.) ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.0		V_{DD}	V

(2) 1/2 bias method, 1/4 bias method

(T_A = -40 to +105 °C, V_{L4} (MIN.) ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.7		V_{DD}	V

(3) 1/3 bias method

(T_A = -40 to +105 °C, V_{L4} (MIN.) ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.5		V_{DD}	V

3.8.2 Internal voltage boosting method

(1) 1/3 bias method

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V_{L1}	C1 to C4 Note 1 = 0.47 μF Note 2	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	V_{L2}	C1 to C4 Note 1 = 0.47 μF		2 V_{L1} - 0.1	2 V_{L1}	2 V_{L1}	V
Tripler output voltage	V_{L3}	C1 to C4 Note 1 = 0.47 μF		3 V_{L1} - 0.15	3 V_{L1}	3 V_{L1}	V
Reference voltage setup time Note 2	t_{VWAIT1}			5			ms
Voltage boost wait time Note 3	t_{VWAIT2}	C1 to C4 Note 1 = 0.47μF		500			ms

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L3} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

(2) 1/4 bias method

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V_{L1}	C1 to C4 Note 1 = 0.47 μF Note 2	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	V_{L2}	C1 to C4 Note 1 = 0.47 μF		2 V_{L1} - 0.08	2 V_{L1}	2 V_{L1}	V
Tripler output voltage	V_{L3}	C1 to C4 Note 1 = 0.47 μF		3 V_{L1} - 0.12	3 V_{L1}	3 V_{L1}	V
Quadruply output voltage	V_{L4}	C1 to C5 Note 1 = 0.47 μF		4 V_{L1} - 0.16	4 V_{L1}	4 V_{L1}	V
Reference voltage setup time Note 2	t_{VWAIT1}			5			ms
Voltage boost wait time Note 3	t_{VWAIT2}	C1 to C5 Note 1 = 0.47μF		500			ms

Note 1. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L3} and GND
C5: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

Note 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

Note 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

3.8.3 Capacitor split method

(1) 1/3 bias method

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V_{L4} voltage	V_{L4}	C1 to C4 = 0.47 μF Note 2		V_{DD}		V
V_{L2} voltage	V_{L2}	C1 to C4 = 0.47 μF Note 2	2/3 V_{L4} - 0.07	2/3 V_{L4}	2/3 V_{L4} + 0.07	V
V_{L1} voltage	V_{L1}	C1 to C4 = 0.47 μF Note 2	1/3 V_{L4} - 0.08	1/3 V_{L4}	1/3 V_{L4} + 0.08	V
Capacitor split wait time Note 1	t_{VWAIT}		100			ms

Note 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

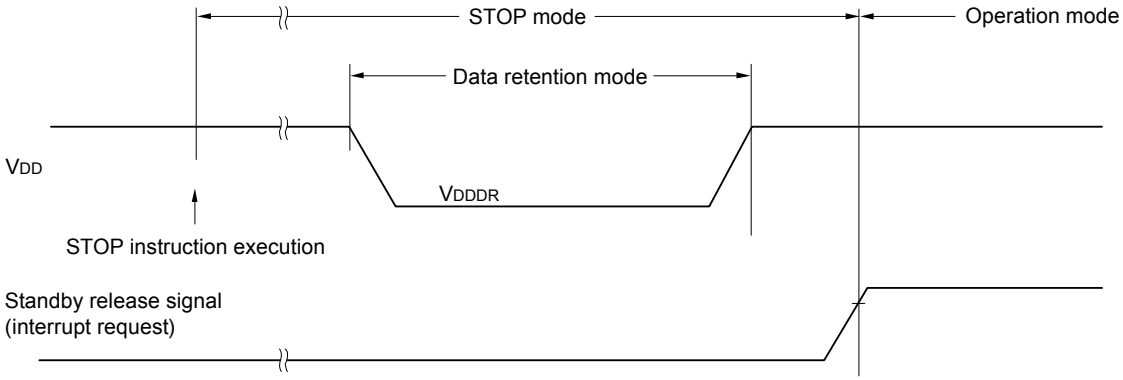
Note 2. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = 0.47 μF±30%

3.9 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

(T_A = -40 to +105 °C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 Note		3.6	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



3.10 Flash Memory Programming Characteristics

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	f_{CLK}	2.4 V ≤ V_{DD} ≤ 3.6 V		1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years	T_A = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year	T_A = 25°C		1,000,000		
		Retained for 5 years	T_A = 85°C	100,000			
		Retained for 20 years	T_A = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

3.11 Dedicated Flash Memory Programmer Communication (UART)

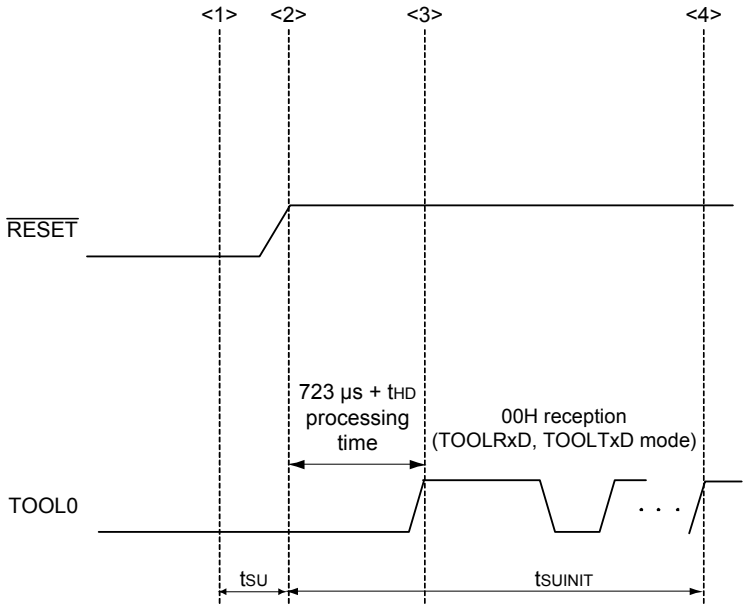
(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.12 Timing Specs for Switching Modes

(T_A = -40 to +105 °C, 2.4 V ≤ V_{DD} ≤ 3.6 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	t_{SUINIT}	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	t_{SU}	POR and LVD reset must end before the external reset ends.	10			μs
Time to hold the TOOL0 pin at the low level after an external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must end before the external reset ends.	1			ms



<1> The low level is input to the TOOL0 pin.
<2> The external reset ends (POR and LVD reset must end before the external reset ends.).
<3> The TOOL0 pin is set to the high level.
<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

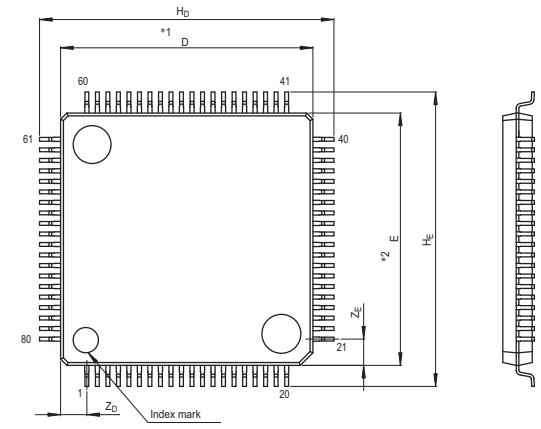
Remark t_{SUINIT}: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the resets end.
t_{SU}: How long from when the TOOL0 pin is placed at the low level until a external reset ends
t_{HD}: How long to keep the TOOL0 pin at the low level from when the external and internal resets end (except soft processing time)

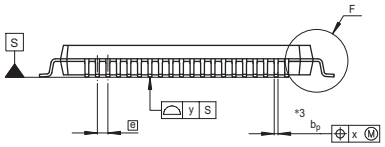
4. PACKAGE DRAWINGS

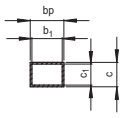
4.1 80-pin products

R5F110MEAFB, R5F110MFAFB, R5F110MGAFB, R5F110MHAFB, R5F110MJAFB
R5F111MEAFB, R5F111MFAFB, R5F111MGAFB, R5F111MHAFB, R5F111MJAFB

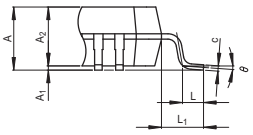
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP80-12x12-0.50	PLQP0080KB-A	80P6Q-A	0.5g







Terminal cross section



Detail F

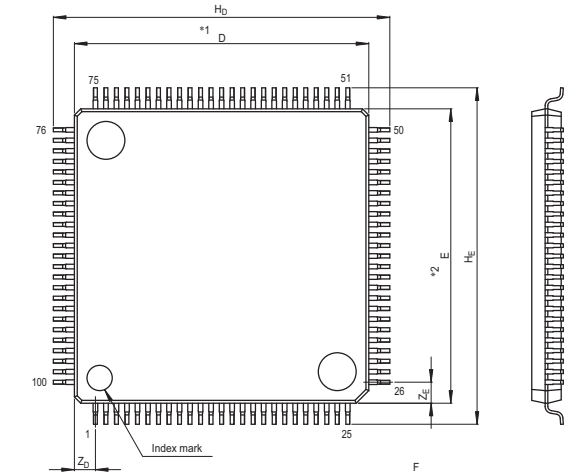
NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

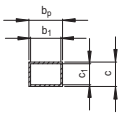
Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	11.9	12.0	12.1
E	11.9	12.0	12.1
A_2	—	1.4	—
H_D	13.8	14.0	14.2
H_E	13.8	14.0	14.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	10°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.25	—
Z_E	—	1.25	—
L	0.3	0.5	0.7
L_1	—	1.0	—

4.2 100-pin products

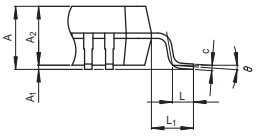
R5F110PEAFB, R5F110PFAFB, R5F110PGAFB, R5F110PHAFB, R5F110PJAFB
R5F111PEAFB, R5F111PFAFB, R5F111PGAFB, R5F111PHAFB, R5F111PJAFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP100-14x14-0.50	PLQP0100KB-A	100P6Q-A / FP-100U / FP-100UV	0.6g





Terminal cross section



Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	13.9	14.0	14.1
E	13.9	14.0	14.1
A_2	—	1.4	—
H_D	15.8	16.0	16.2
H_E	15.8	16.0	16.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.0	—
Z_E	—	1.0	—
L	0.35	0.5	0.65
L_1	—	1.0	—

REVISION HISTORY	RL78/L1C Datasheet

Rev.	Date	Description	
		Page	Summary
0.01	Oct 15, 2012	—	First Edition issued
1.00	Nov 18, 2013	1, 2	Modification of 1.1 Features
		3, 4	Modification of 1.2 Ordering Information
		5 to 8	Modification of package type in 1.3 Pin Configuration (Top View)
		14 to 17	Modification of vectored interrupt sources in 1.6 Outline of Functions
		14 to 17	Modification of operating ambient temperature in 1.6 Outline of Functions
		19 to 21	Modification of description in tables in 2.1 Absolute Maximum Ratings
		22, 23	Modification of description in 2.2 Oscillator Characteristics
		25	Modification of low-level output current in 2.3.1 Pin characteristics
		26	Modification of error of high-level input voltage conditions in 2.3.1 Pin characteristics
		26	Modification of error of low-level input voltage conditions in 2.3.1 Pin characteristics
		27	Modification of low-level output voltage in 2.3.1 Pin characteristics
		28	Modification of error of internal pull-up resistor conditions in 2.3.1 Pin characteristics
		29 to 34	Modification of 2.3.2 Supply current characteristics
		35, 36	Modification of 2.4 AC Characteristics
		37, 38	Addition of minimum instruction execution time during main system clock operation
		41 to 63	Addition of LS mode and LV mode characteristics in 2.5.1 Serial array unit
		64 to 66	Addition of LS mode and LV mode characteristics in 2.5.2 Serial interface IICA
		67, 68	Modification of conditions in 2.5.3 USB
		69	Addition of (3) BC option standard in 2.5.3 USB
		70 to 75	Addition of characteristics about conversion of internal reference voltage and temperature sensor in 2.6.1 A/D converter characteristics
		76	Addition of characteristic in 2.6.4 Comparator
		76	Deletion of detection delay in 2.6.5 POR circuit characteristics
		78	Modification of 2.7 Power supply voltage rising slope characteristics
		79 to 82	Modification of 2.8 LCD Characteristics
		83	Modification of 2.9 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics
		83	Modification of 2.10 Flash Memory Programming Characteristics
		84	Addition of 2.12 Timing Specs for Switching Modes
		85 to 144	Addition of 3. ELECTRICAL SPECIFICATIONS (G: T_A = -40 to +105°C)

NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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